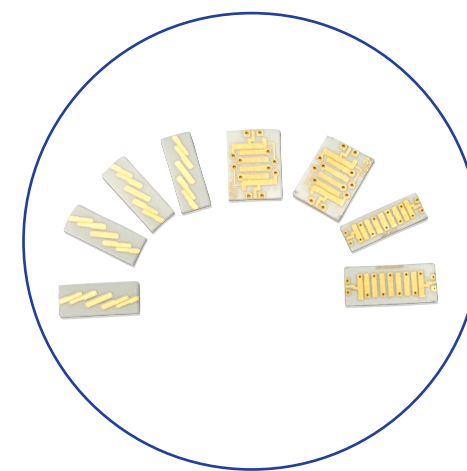


Yun Micro Electronics Ltd. (China) **-----Customizable Microwave RF Filters**



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Film Filter

GOOD NIGHTS

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IYFTB2200-900-10

Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

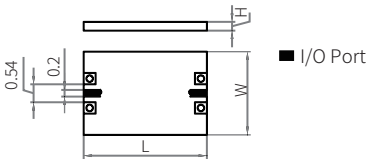
Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

Electrical Specifications

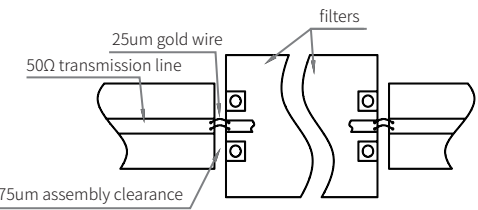
	Min	Typical	Max	
Center Freq	-	2.2	-	GHz
Band Freq	1.75	-	2.65	GHz
Fc IL	-	2.5	-	dB
Passband Ripple	-	-	1.2	dB
VSWR	-	1.8	-	-
Rejection	≥40dB@1.45GHz			
	≥40dB@2.95GHz			

Overall Dimensions

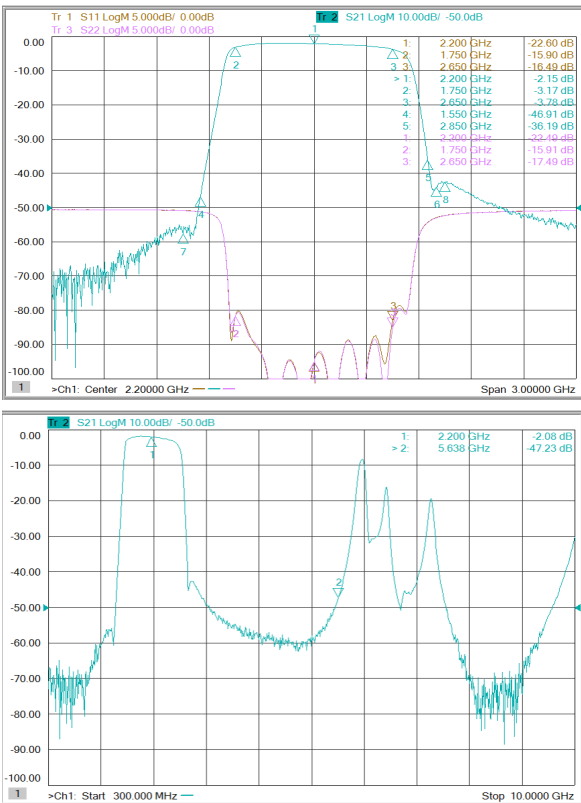


notation	value	unit
L	8.6	mm
W	9.8	mm
H	0.381	mm

Suggested Assembly Drawings

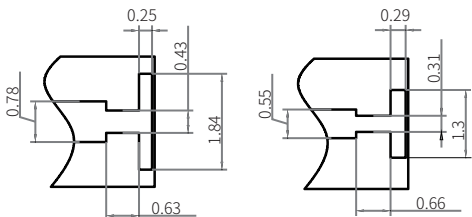


Typical Curve



Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



Rogers5880
Thickness: 0.254mm
Applicable frequency: DC-30GHz
The top of the T-head graphic is 50um from the edge of the substrate, and no matching is required for frequencies below 10GHz.

Rogers4350
Thickness: 0.254mm
Applicable frequency: DC-25GHz

IYFTB3050-200-6

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

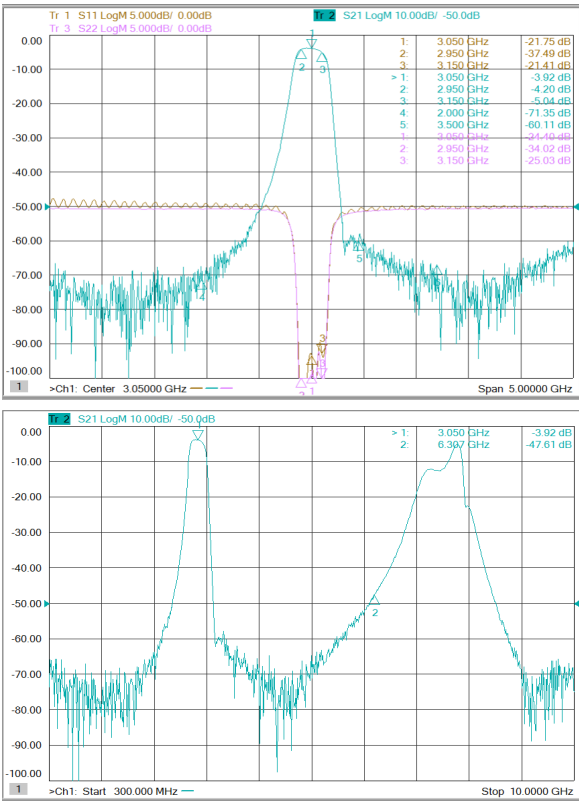
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

► Electrical Specifications

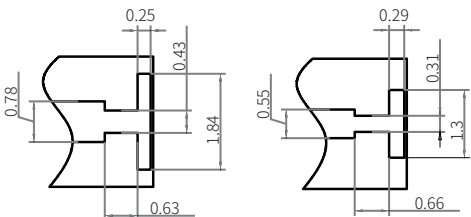
	Min	Typical	Max	
Center Freq	-	3.05	-	GHz
Band Freq	2.95	-	3.15	GHz
Fc IL	-	4.0	-	dB
Passband Ripple	-	-	1.0	dB
VSWR	-	1.8	-	-
Rejection	≥60dB@2 GHz			
	≥40dB@3.5 GHz			

► Typical Curve



► Caveat

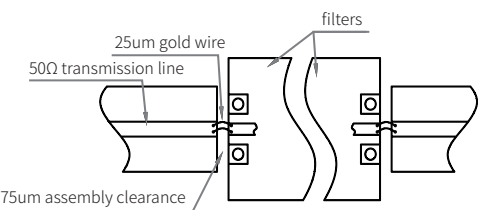
- 1、It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2、The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3、The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4、Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



Rogers5880
Thickness: 0.254mm
Applicable frequency: DC-30GHz
The top of the T-head graphic is 50um from the edge of the substrate, and no matching is required for frequencies below 10GHz.

Rogers4350
Thickness: 0.254mm
Applicable frequency: DC-25GHz
The top of the T-head graphic is 50um from the edge of the substrate, and no matching is required for frequencies below 10GHz.

► Suggested Assembly Drawings



IYFTB3150-800-6

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

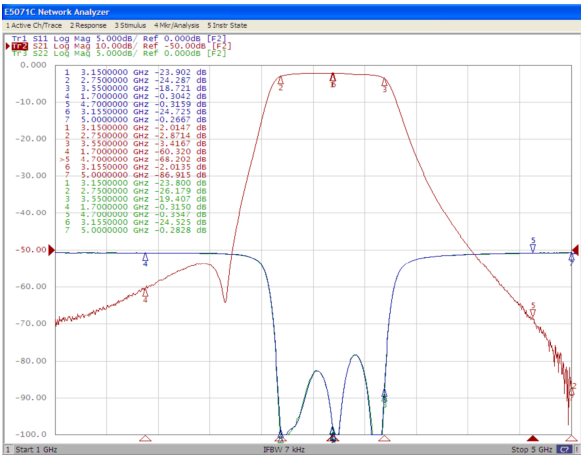
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	3.15	-	GHz
Band Freq	2.75	-	3.55	GHz
Fc IL	-	2.0	-	dB
Passband Ripple	-	-	1.0	dB
VSWR	-	1.8	-	-
Rejection	≥40dB@2.2 GHz			
	≥40dB@4.6 GHz			

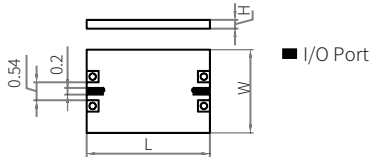
► Typical Curve



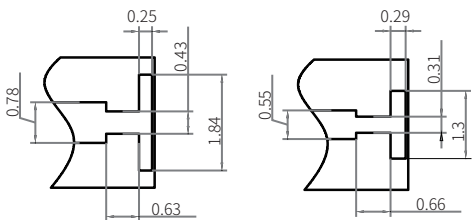
► Caveat

- 1、It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2、The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3、The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4、Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:

► Overall Dimensions



notation	value	unit
L	7.5	mm
W	9.0	mm
H	0.381	mm

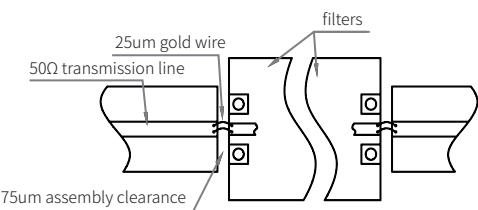


Rogers5880
Thickness: 0.254mm
Applicable frequency: DC-30GHz

Rogers4350
Thickness: 0.254mm
Applicable frequency: DC-25GHz

The top of the T-head graphic is 50um from the edge of the substrate, and no matching is required for frequencies below 10GHz.

► Suggested Assembly Drawings



IYFTB4700-2700-11

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

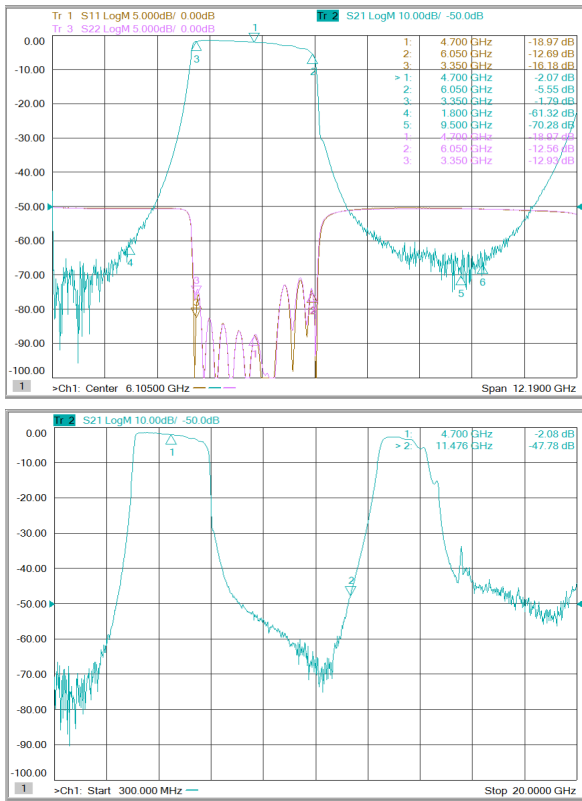
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

► Electrical Specifications

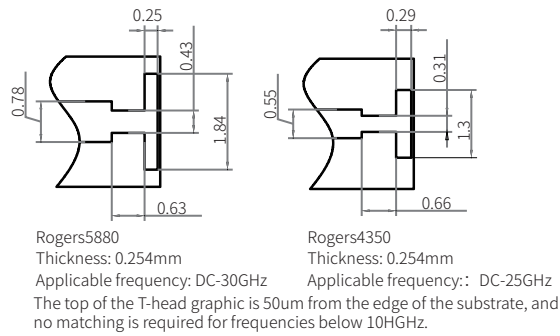
	Min	Typical	Max	
Center Freq	-	4.7	-	GHz
Band Freq	3.35	-	6.05	GHz
Fc IL	-	2.2	-	dB
Passband Ripple	-	-	1	dB
VSWR	-	1.8	-	-
Rejection	≥60dB@1.8 GHz			
	≥60dB@9.5 GHz			

► Typical Curve

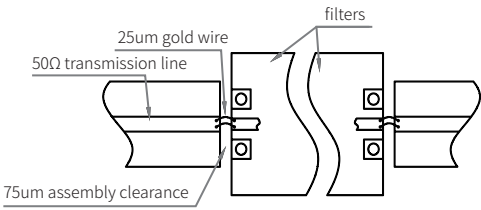


► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



► Suggested Assembly Drawings



IYFTB5100-200-8

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

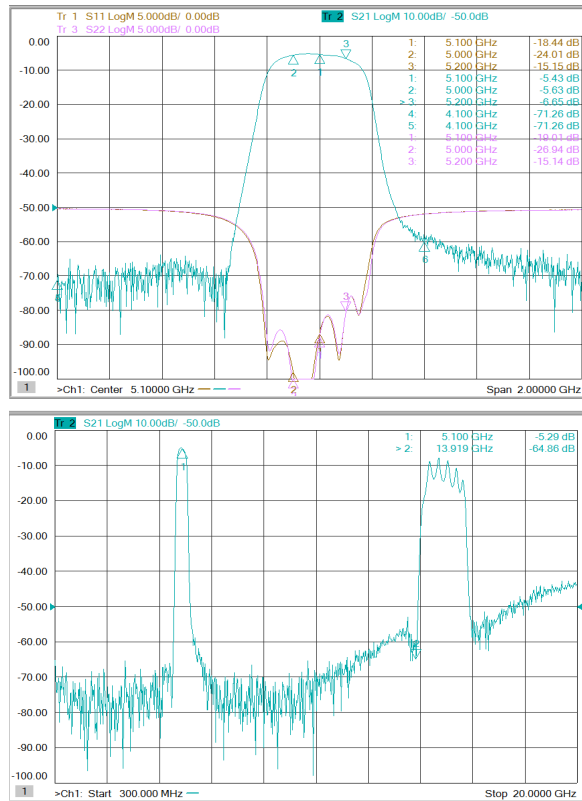
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

► Electrical Specifications

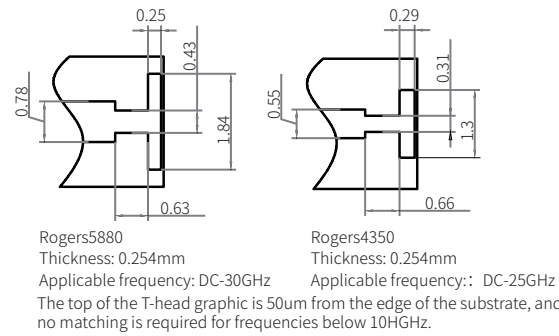
	Min	Typical	Max	
Center Freq	-	5.1	-	GHz
Band Freq	5.0	-	5.2	GHz
Fc IL	-	5.5	-	dB
Passband Ripple	-	-	-	dB
VSWR	-	1.8	-	-
Rejection	≥60dB@4.6GHz			
	≥50dB@5.7 GHz			

► Typical Curve

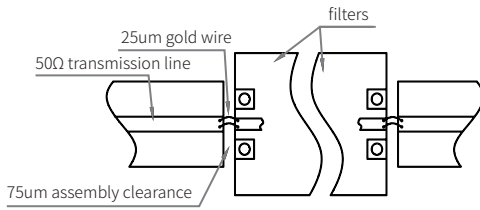


► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



► Suggested Assembly Drawings



IYFTB5195.5-209-4

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

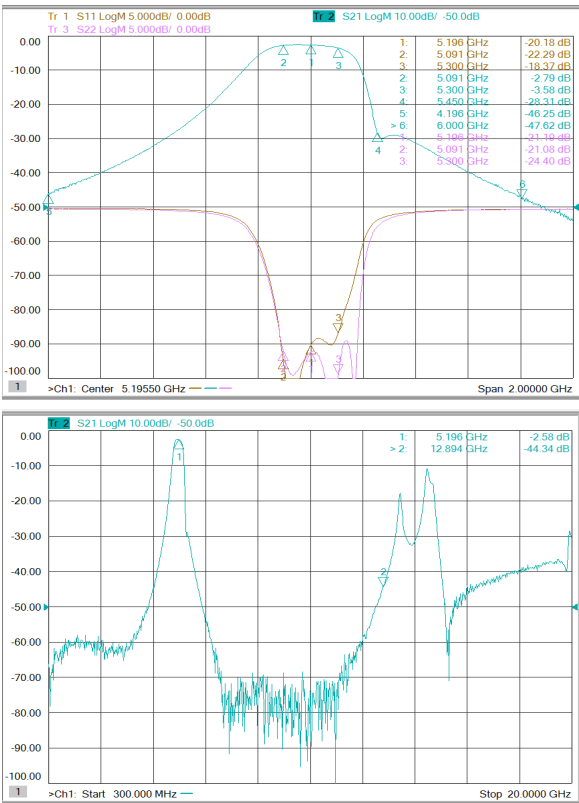
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

► Electrical Specifications

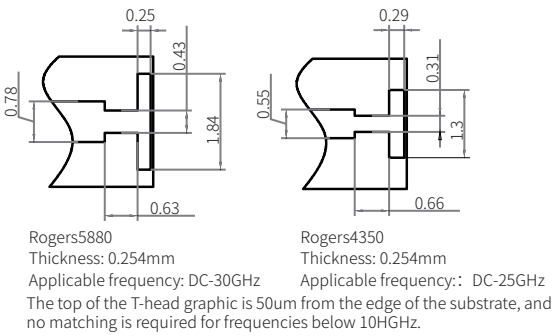
	Min	Typical	Max	
Center Freq	-	5.1955	-	GHz
Band Freq	5.091	-	5.3	GHz
Fc IL	-	2.5	-	dB
Passband Ripple	-	-	1.0	dB
VSWR	-	1.8	-	-
Rejection	≥30dB@4.13 GHz			
	≥20dB@5.45 GHz			

► Typical Curve

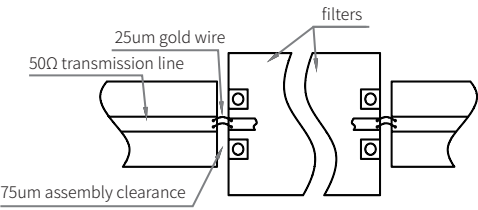


► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



► Suggested Assembly Drawings



IYFTB5575-250-4

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

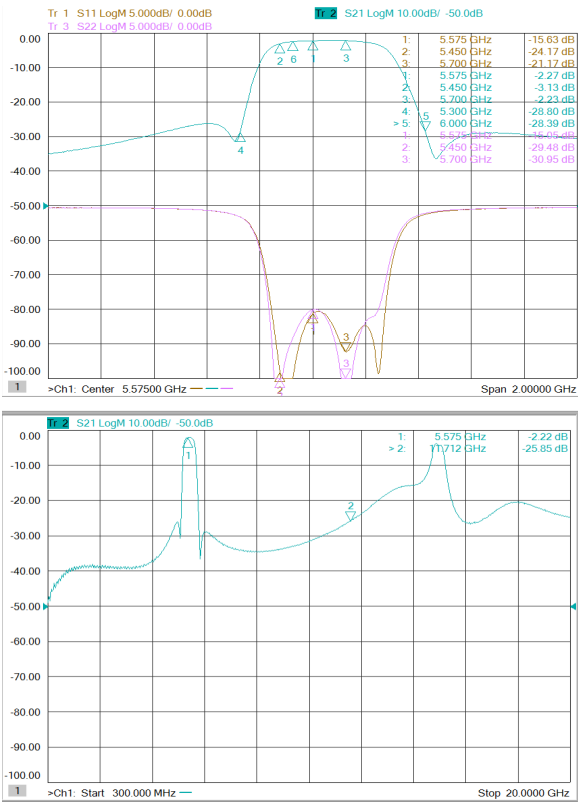
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

► Electrical Specifications

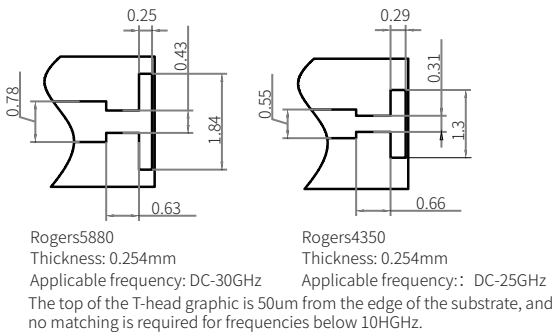
	Min	Typical	Max	
Center Freq	-	5.575	-	GHz
Band Freq	5.45	-	5.7	GHz
Fc IL	-	2.5	-	dB
Passband Ripple	-	-	1.2	dB
VSWR	-	1.8	-	-
Rejection	≥25dB@5.3 GHz			
	≥25dB@6.0 GHz			

► Typical Curve

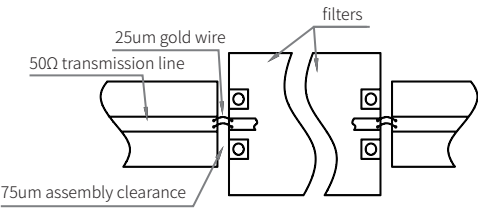


► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



► Suggested Assembly Drawings



IYFTB5750-750-8

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

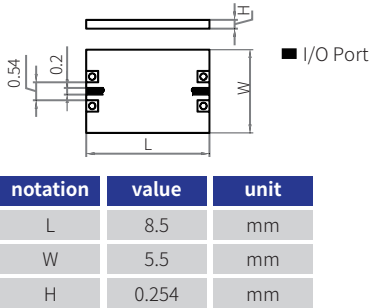
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

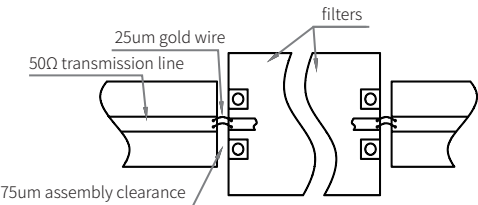
► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	5.75	-	GHz
Band Freq	5.25	-	6.0	GHz
Fc IL	-	2.5	-	dB
Passband Ripple	-	-	1.0	dB
VSWR	-	1.8	-	-
Rejection	≥60dB@4.0 GHz			
	≥60dB@7.0 GHz			

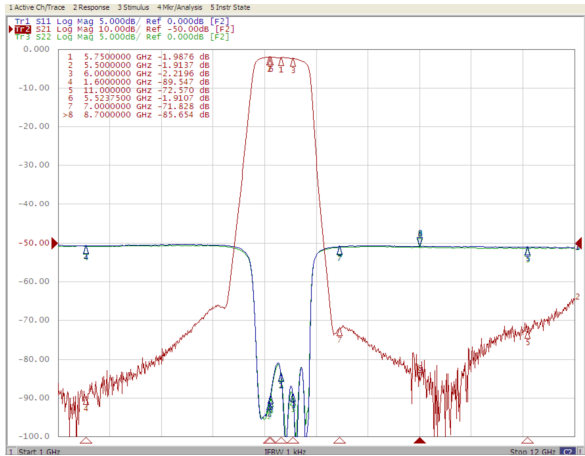
► Overall Dimensions



► Suggested Assembly Drawings

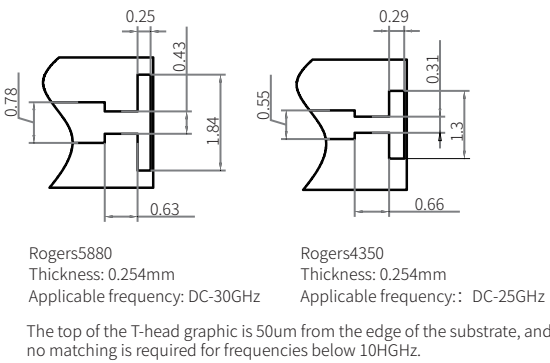


► Typical Curve



► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB6000-4000-10

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

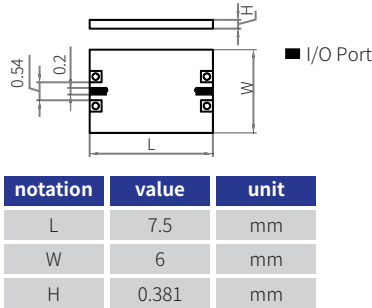
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

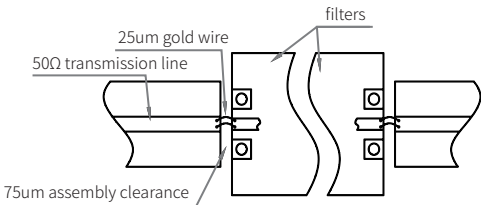
► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	6	-	GHz
Band Freq	4	-	8	GHz
Fc IL	-	1.5	-	dB
Passband Ripple	-	-	1.5	dB
VSWR	-	1.8	-	-
Rejection	≥45dB@3 GHz			
	≥45dB@9 GHz			

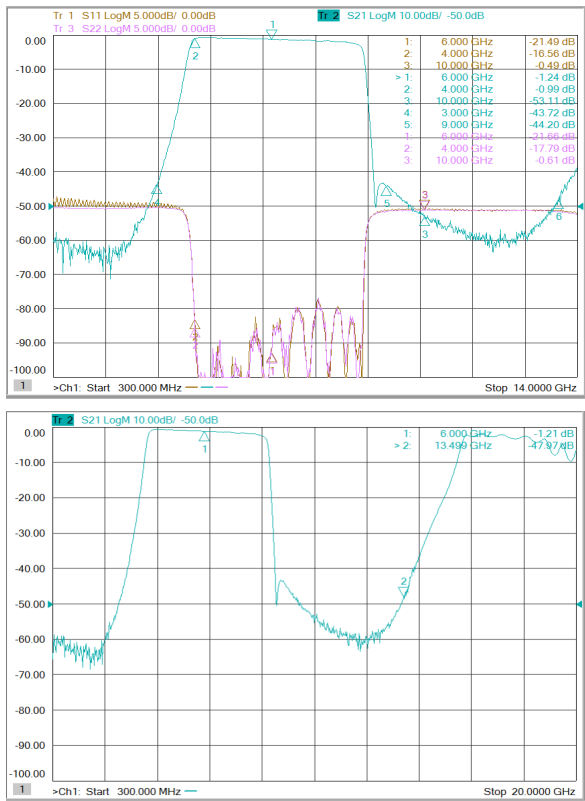
► Overall Dimensions



► Suggested Assembly Drawings

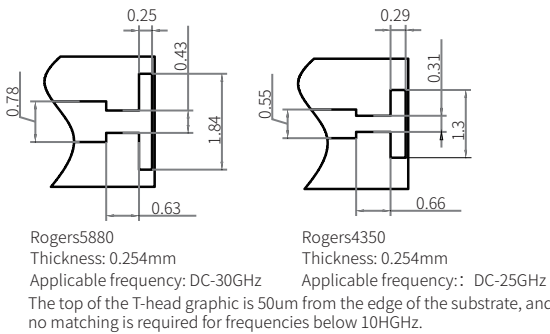


► Typical Curve



► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB6050-300-6

- Performance Characteristics
- 1、High precision micro-nanometer processing technology
 - 2、High performance, low temperature drift, high power
 - 3、Gold wire bonding, suitable for multi-chip integration module applications
 - 4、50Ω coplanar waveguide output

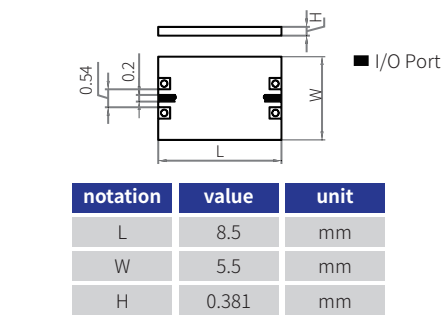
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

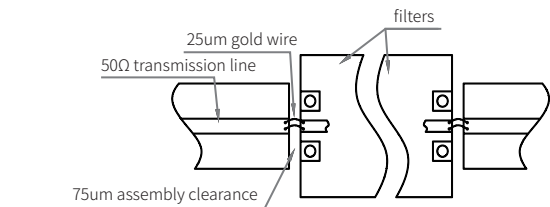
► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	6.05	-	GHz
Band Freq	5.9	-	6.2	GHz
Fc IL	-	2.5	-	dB
Passband Ripple	-	-	1.0	dB
VSWR	-	1.8	-	-
Rejection	≥60dB@5 GHz			
	≥60dB@7.25 GHz			

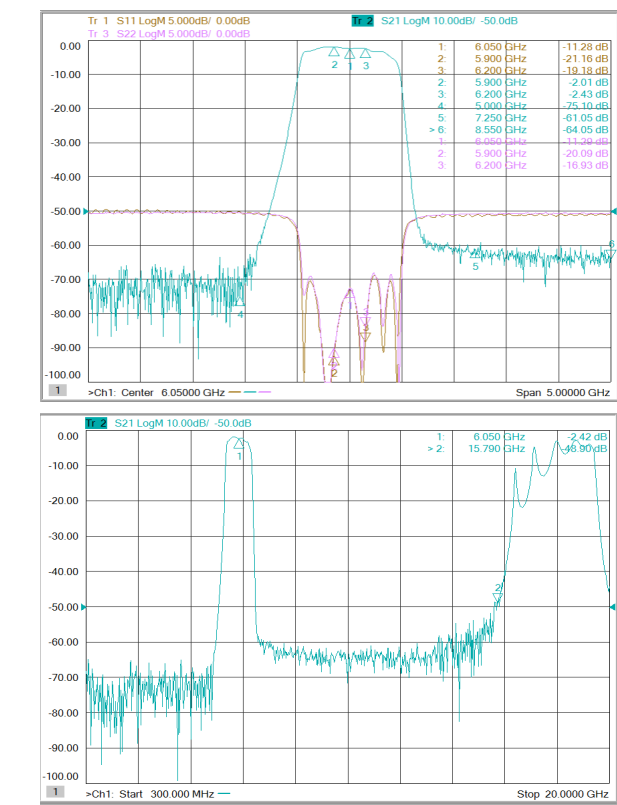
► Overall Dimensions



► Suggested Assembly Drawings

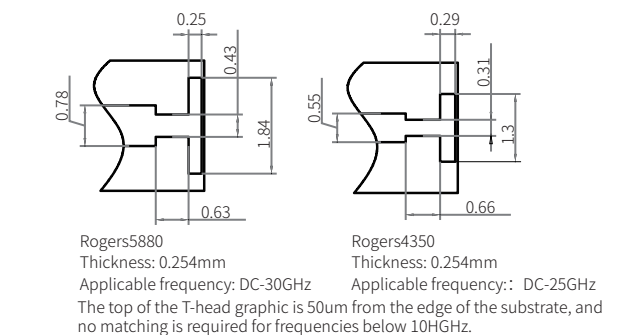


► Typical Curve



► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB6150-300-4

- Performance Characteristics
- 1、High precision micro-nanometer processing technology
 - 2、High performance, low temperature drift, high power
 - 3、Gold wire bonding, suitable for multi-chip integration module applications
 - 4、50Ω coplanar waveguide output

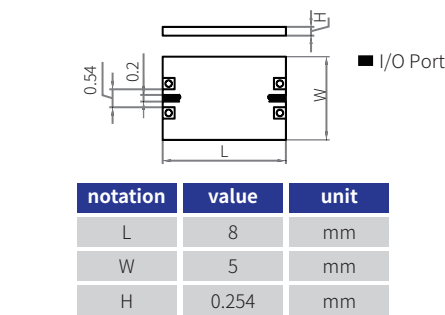
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

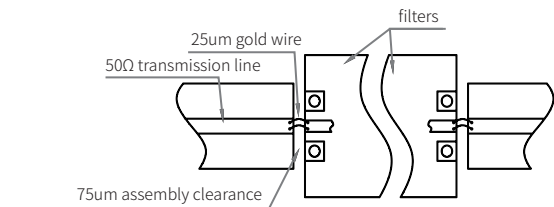
► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	6.15	-	GHz
Band Freq	6.0	-	6.3	GHz
Fc IL	-	2.0	-	dB
Passband Ripple	-	-	1.0	dB
VSWR	-	1.8	-	-
Rejection	≥40dB@3 GHz			
	≥40dB@9 GHz			

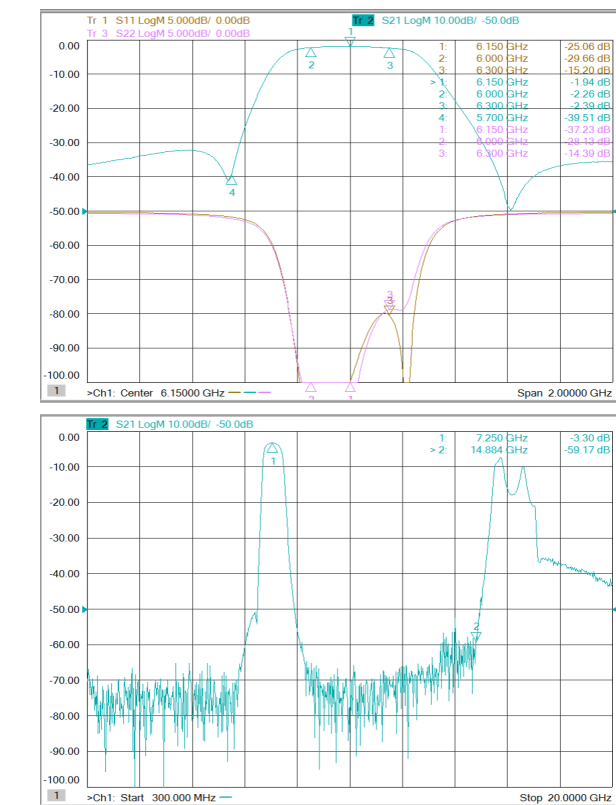
► Overall Dimensions



► Suggested Assembly Drawings

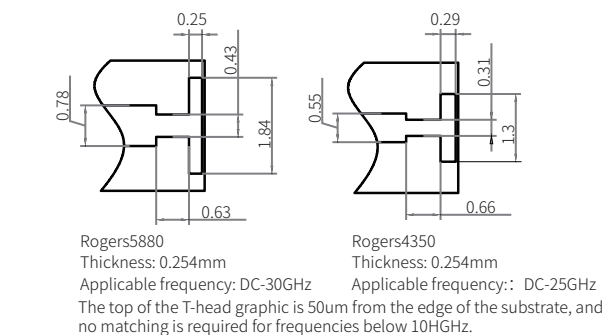


► Typical Curve



► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB6820-1100-10

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

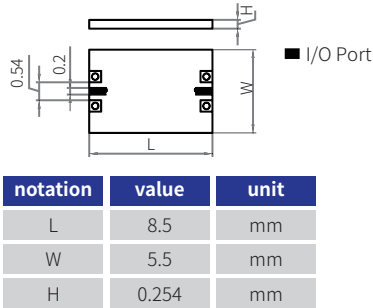
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

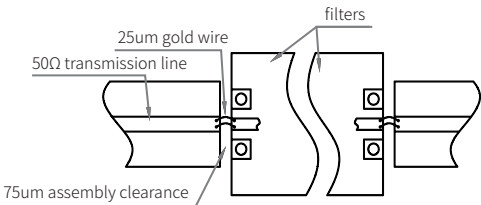
► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	6.82	-	GHz
Band Freq	6.26	-	7.36	GHz
Fc IL	-	2.0	-	dB
Passband Ripple	-	-	0.6	dB
VSWR	-	1.8	-	-
Rejection	≥45dB@5.31 GHz			
	≥45dB@8.59 GHz			

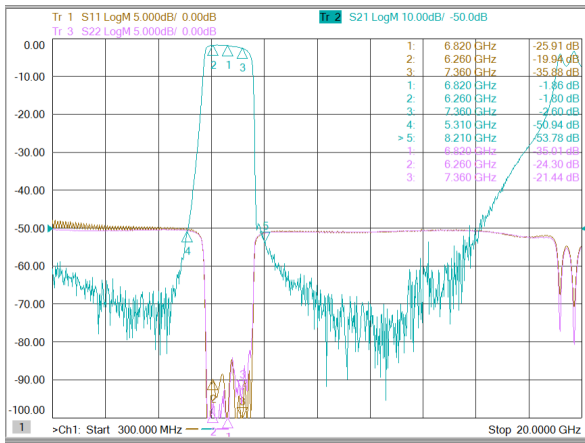
► Overall Dimensions



► Suggested Assembly Drawings

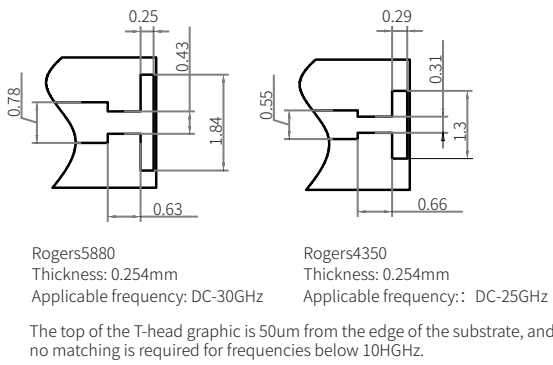


► Typical Curve



► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB7170-1020-9

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

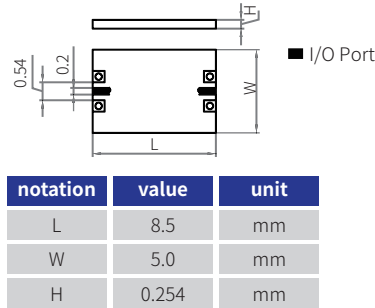
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

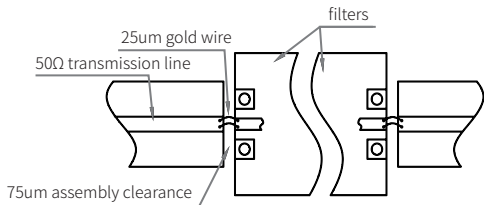
► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	7.17	-	GHz
Band Freq	6.66	-	7.68	GHz
Fc IL	-	3	-	dB
Passband Ripple	-	-	-	dB
VSWR	-	1.8	-	-
Rejection	≥30dB@6.36GHz			
	≥40dB@8.64GHz			

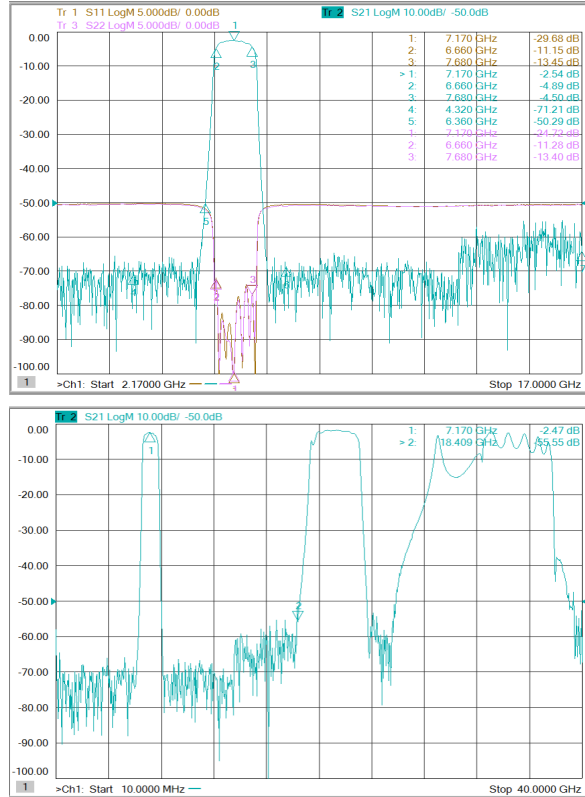
► Overall Dimensions



► Suggested Assembly Drawings

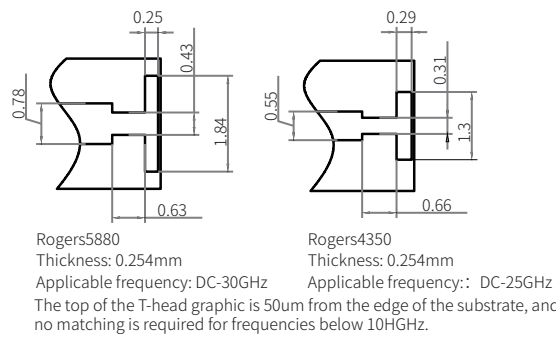


► Typical Curve



► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB7250-500-6

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

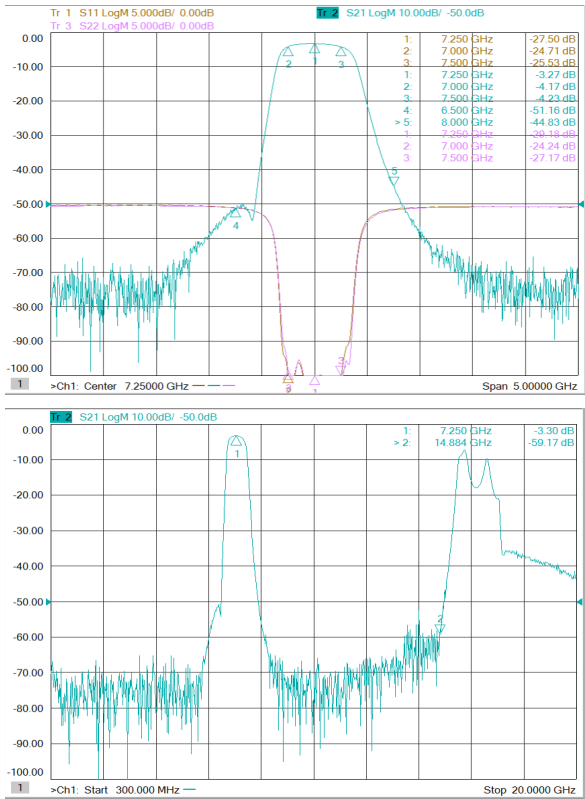
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

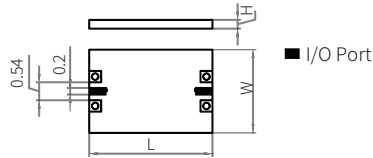
► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	7.25	-	GHz
Band Freq	7	-	7.5	GHz
Fc IL	-	4.5	-	dB
Passband Ripple	-	-	1.5	dB
VSWR	-	1.8	-	-
Rejection	≥40dB@6.5 GHz			
	≥40dB@8 GHz			

► Typical Curve



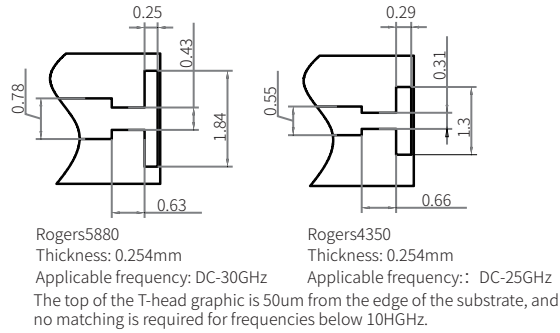
► Overall Dimensions



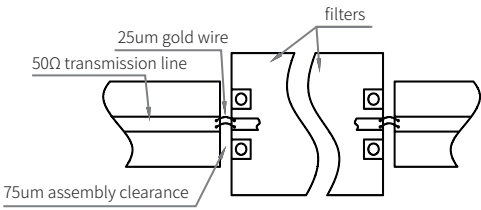
notation	value	unit
L	10	mm
W	4	mm
H	0.254	mm

► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



► Suggested Assembly Drawings



IYFTB7250-2500-7

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

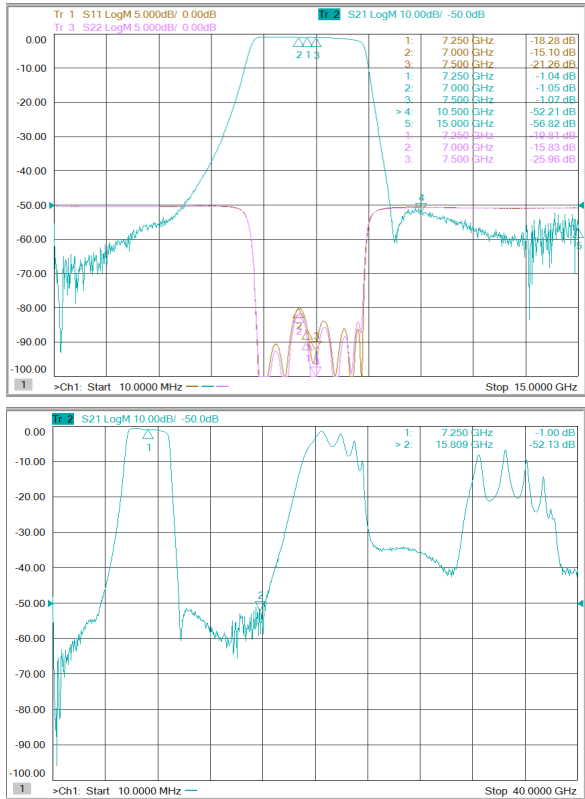
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

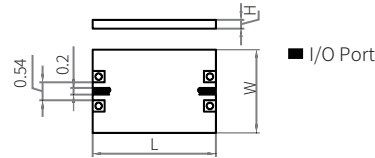
► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	7.25	-	GHz
Band Freq	6	-	8.5	GHz
Fc IL	-	2.0	-	dB
Passband Ripple	-	-	1.2	dB
VSWR	-	1.8	-	-
Rejection	≥40dB@4.0 GHz			
	≥40dB@10.5 GHz			

► Typical Curve



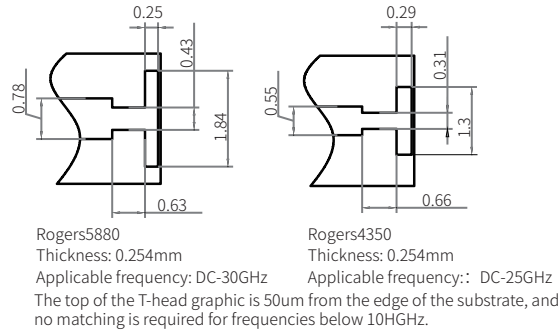
► Overall Dimensions



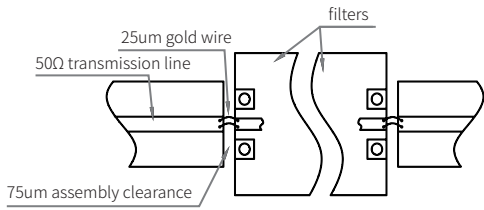
notation	value	unit
L	5.5	mm
W	5.0	mm
H	0.254	mm

► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



► Suggested Assembly Drawings



IYFTB7800-800-8

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

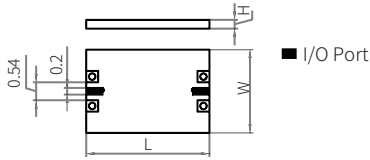
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

► Electrical Specifications

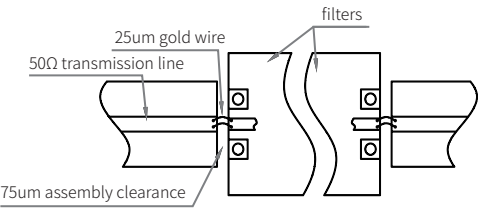
	Min	Typical	Max	
Center Freq	-	7.8	-	GHz
Band Freq	7.4	-	8.2	GHz
Fc IL	-	2.0	-	dB
Passband Ripple	-	-	1.0	dB
VSWR	-	1.8	-	-
Rejection	≥45dB@6.4 GHz			
	≥45dB@9.2 GHz			

► Overall Dimensions

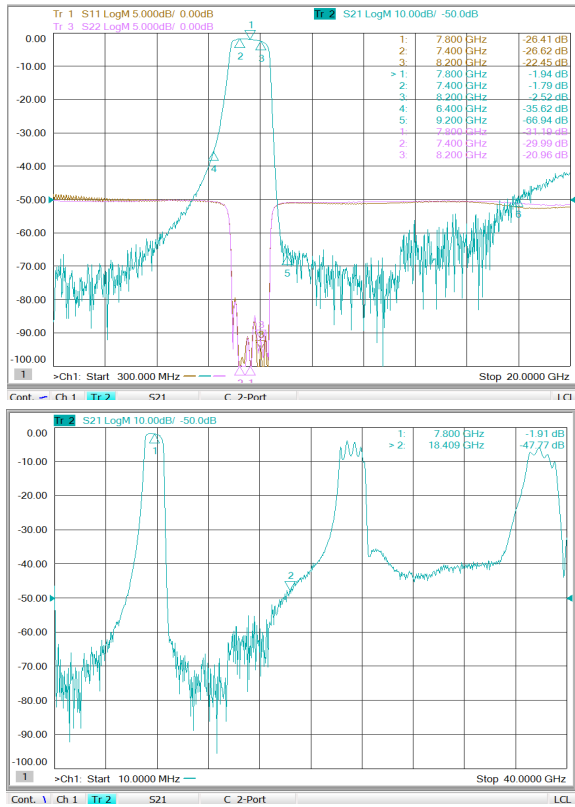


notation	value	unit
L	8.5	mm
W	5	mm
H	0.254	mm

► Suggested Assembly Drawings

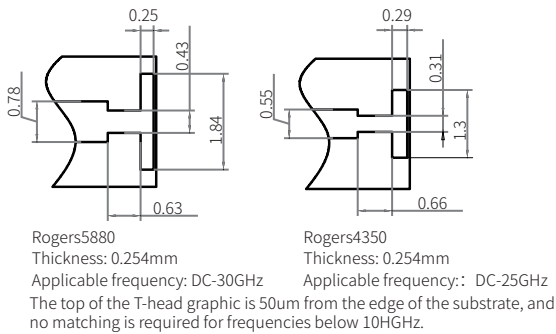


► Typical Curve



► Caveat

- 1、It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2、The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3、The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4、Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB8000-4000-9

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

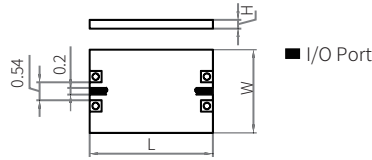
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

► Electrical Specifications

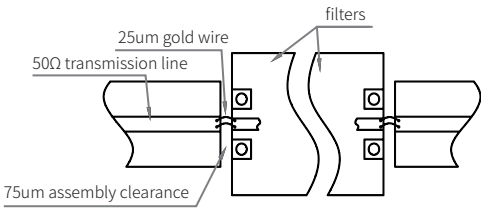
	Min	Typical	Max	
Center Freq	-	8.0	-	GHz
Band Freq	6	-	10	GHz
Fc IL	-	1.8	-	dB
Passband Ripple	-	-	1.0	dB
VSWR	-	1.8	-	-
Rejection	≥40dB@5.15 GHz			
	≥40dB@11.6 GHz			

► Overall Dimensions

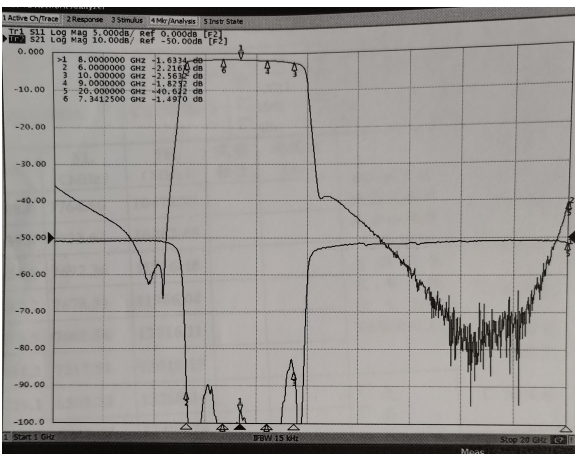


notation	value	unit
L	8.0	mm
W	4.8	mm
H	0.381	mm

► Suggested Assembly Drawings

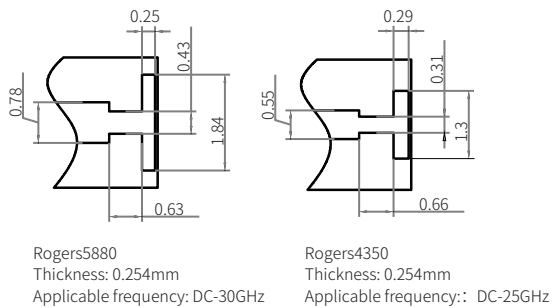


► Typical Curve



► Caveat

- 1、It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2、The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3、The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4、Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



Rogers5880 Thickness: 0.254mm Applicable frequency: DC-30GHz
Rogers4350 Thickness: 0.254mm Applicable frequency: DC-25GHz

The top of the T-head graphic is 50um from the edge of the substrate, and no matching is required for frequencies below 10GHz.

IYFTB8000-4000-10

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

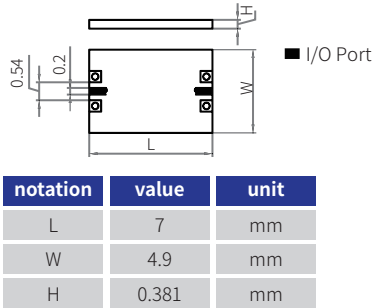
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

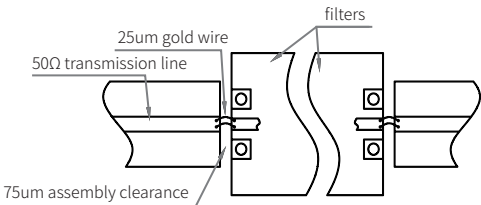
► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	8	-	GHz
Band Freq	6	-	10	GHz
Fc IL	-	1.5	-	dB
Passband Ripple	-	-	1	dB
VSWR	-	1.8	-	
Rejection	≥40dB@4 GHz			
	≥40dB@11.5 GHz			

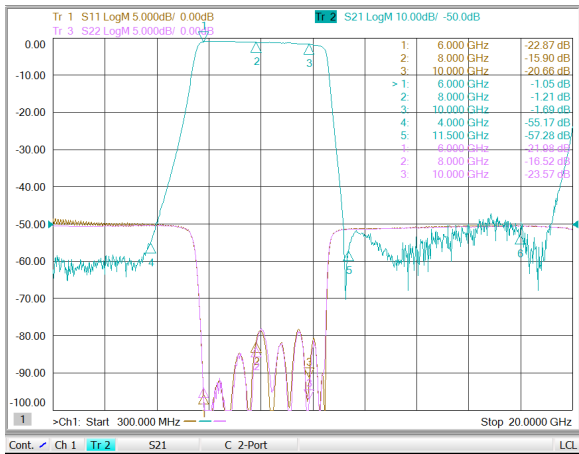
► Overall Dimensions



► Suggested Assembly Drawings

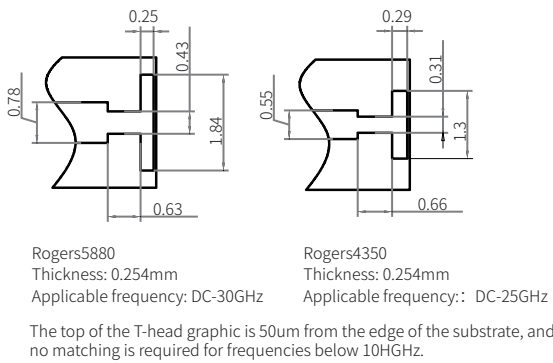


► Typical Curve



► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB8000-4400-11

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

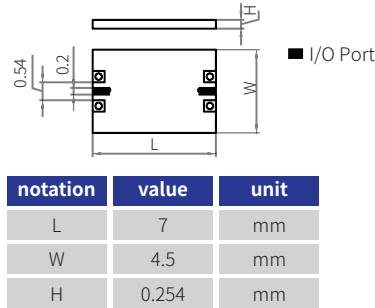
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

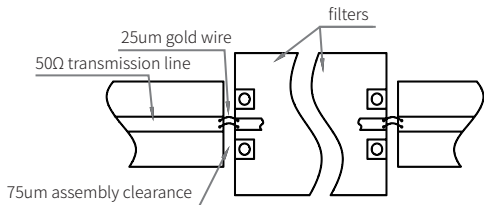
► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	8	-	GHz
Band Freq	5.8	-	10.2	GHz
Fc IL	-	2	-	dB
Passband Ripple	-	-	1	dB
VSWR	-	1.8	-	
Rejection	≥60dB@3.5 GHz			
	≥60dB@15 GHz			

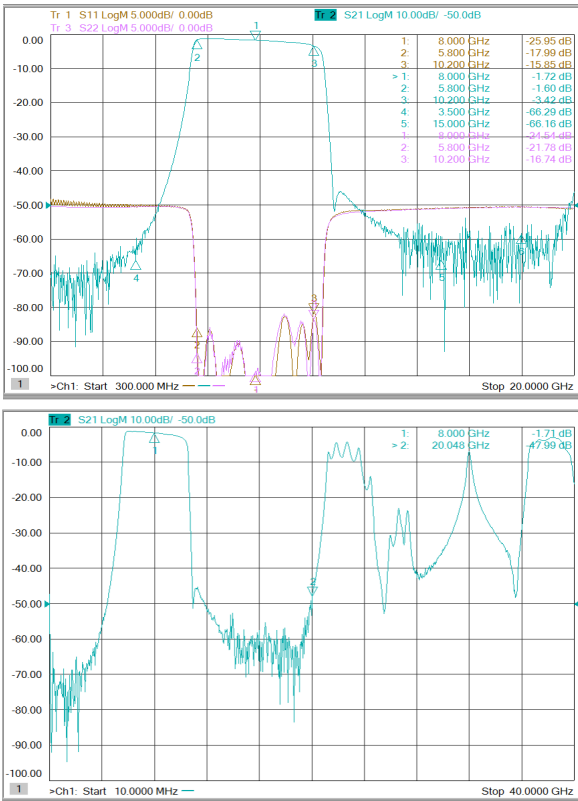
► Overall Dimensions



► Suggested Assembly Drawings

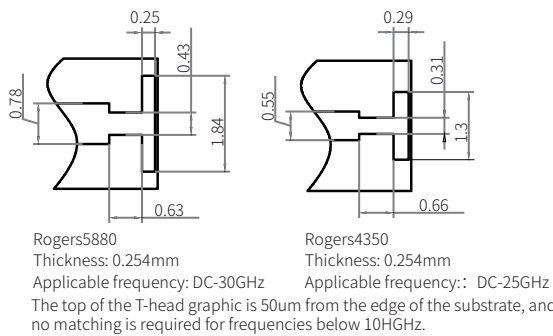


► Typical Curve



► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB8170-1020-9

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

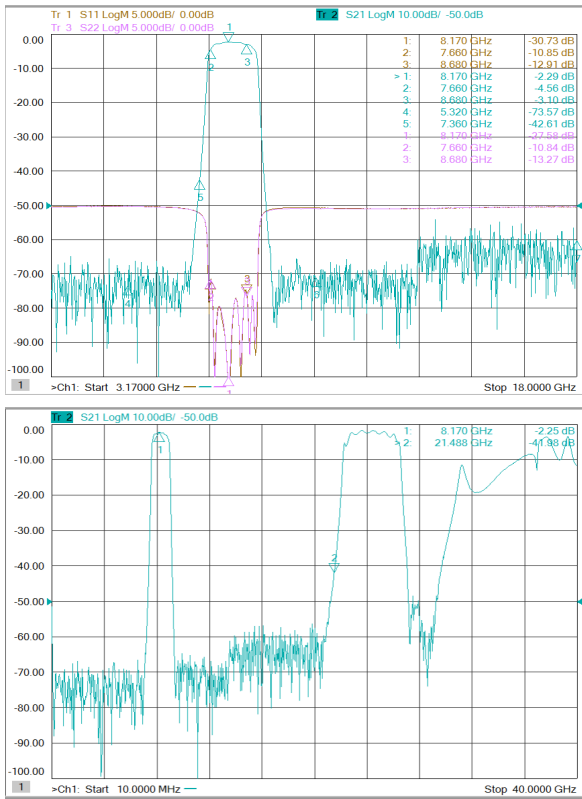
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

► Electrical Specifications

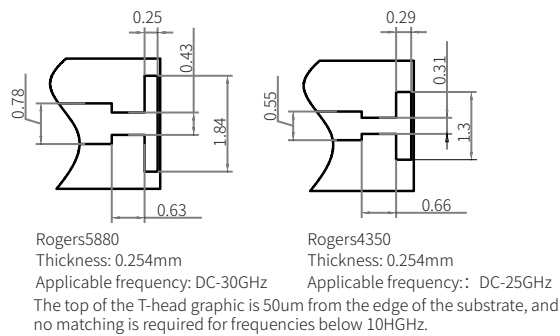
	Min	Typical	Max	
Center Freq	-	8.17	-	GHz
Band Freq	7.66	-	8.68	GHz
Fc IL	-	2.5	-	dB
Passband Ripple	-	-	-	dB
VSWR	-	1.8	-	-
Rejection	≥30dB@7.36 GHz			
	≥40dB@10.64 GHz			

► Typical Curve

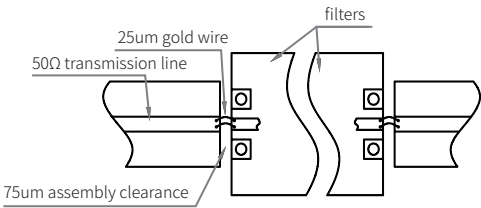


► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



► Suggested Assembly Drawings



IYFTB8250-500-7

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

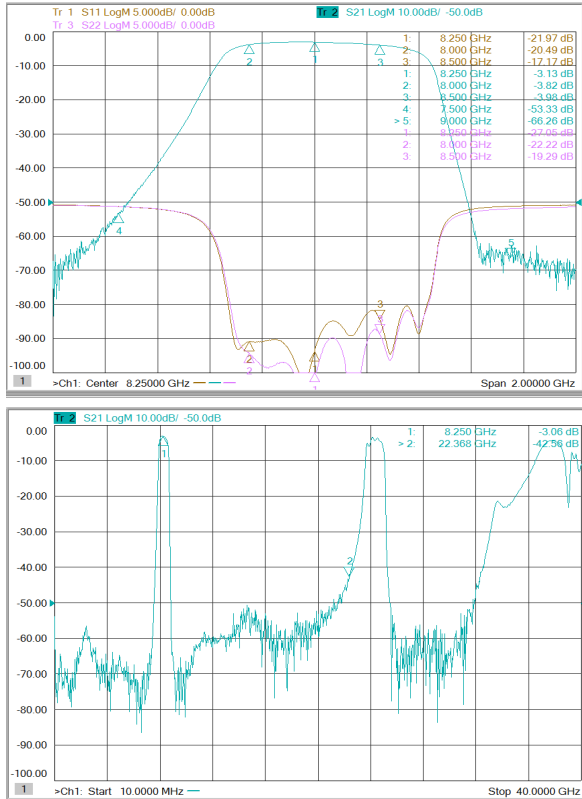
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

► Electrical Specifications

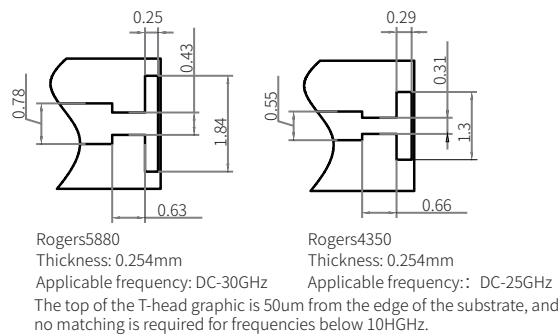
	Min	Typical	Max	
Center Freq	-	8.25	-	GHz
Band Freq	8	-	8.5	GHz
Fc IL	-	3.5	-	dB
Passband Ripple	-	-	-	dB
VSWR	-	1.8	-	-
Rejection	≥40dB@7.5 GHz			
	≥40dB@9.0 GHz			

► Typical Curve

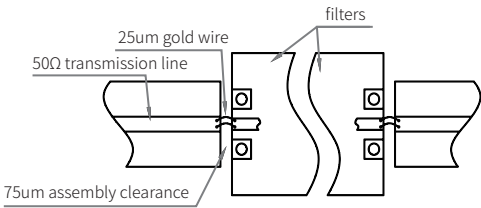


► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



► Suggested Assembly Drawings



IYFTB8750-2100-7

- Performance Characteristics
- 1、High precision micro-nanometer processing technology

2、High performance, low temperature drift, high power

3、Gold wire bonding, suitable for multi-chip integration module applications

4、50Ω coplanar waveguide output

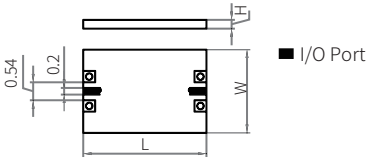
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

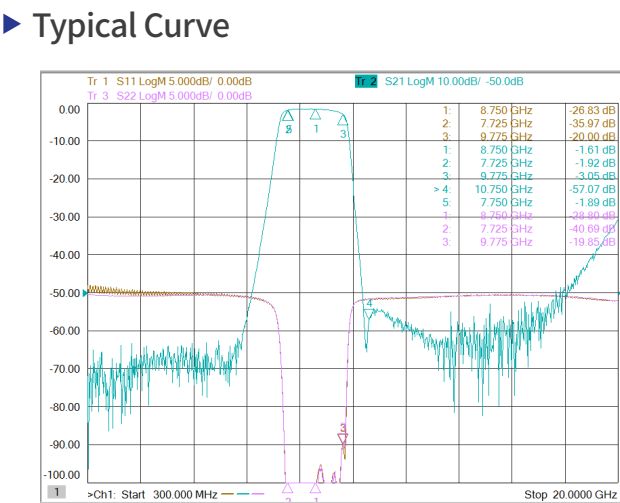
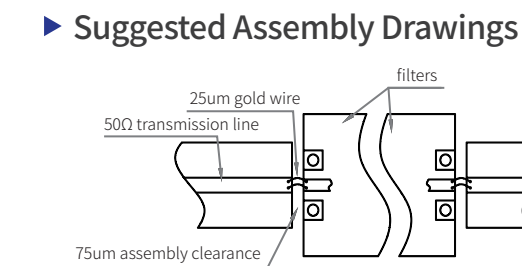
► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	8.75	-	GHz
Band Freq	7.7	-	9.8	GHz
Fc IL	-	1.8	-	dB
Passband Ripple	-	-	1.0	dB
VSWR	-	1.8	-	-
Rejection	≥45dB@6.2 GHz			
	≥45dB@11.25 GHz			

► Overall Dimensions



notation	value	unit
L	5.5	mm
W	4.2	mm
H	0.254	mm

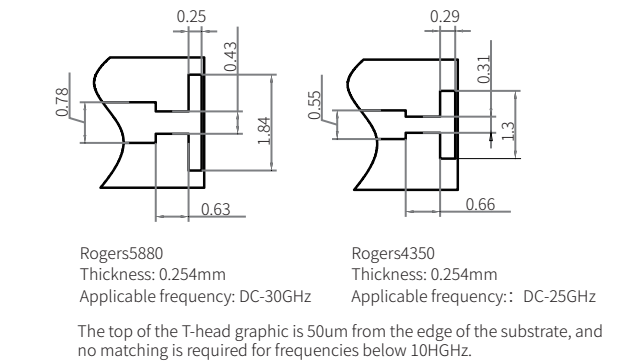


- Caveat
- 1、It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;

2、The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);

3、The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;

4、Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB9170A-1020-9

- Performance Characteristics
- 1、High precision micro-nanometer processing technology

2、High performance, low temperature drift, high power

3、Gold wire bonding, suitable for multi-chip integration module applications

4、50Ω coplanar waveguide output

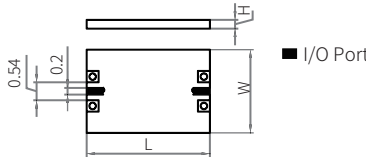
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

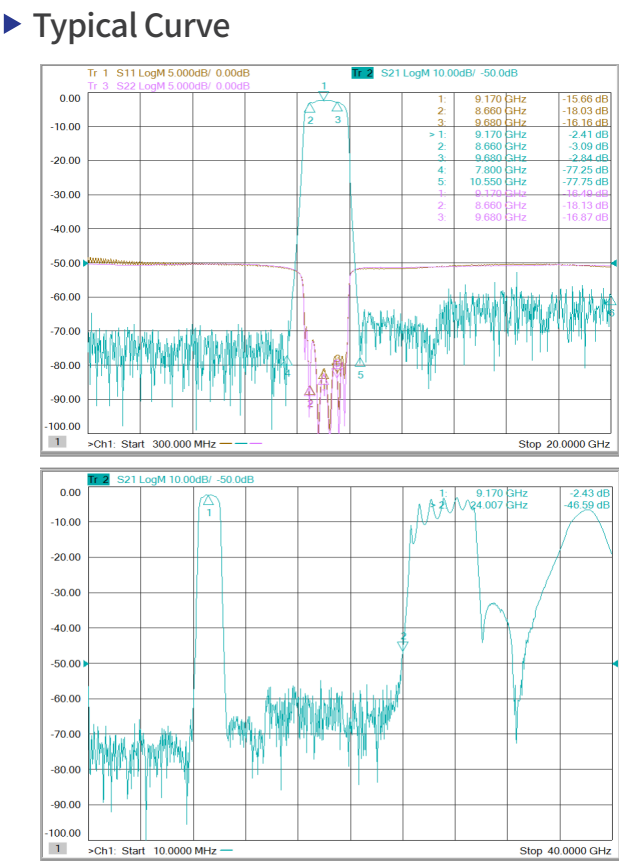
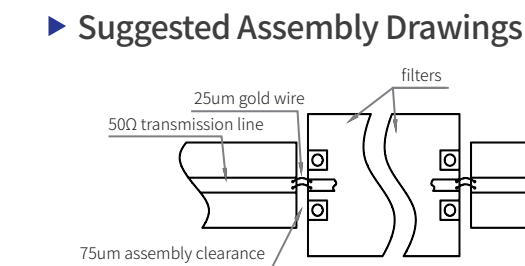
► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	9.17	-	GHz
Band Freq	8.66	-	9.68	GHz
Fc IL	-	3	-	dB
Passband Ripple	-	-	1.2	dB
VSWR	-	1.8	-	-
Rejection	≥40dB@7.8 GHz			
	≥40dB@10.55 GHz			

► Overall Dimensions



notation	value	unit
L	9	mm
W	4	mm
H	0.254	mm

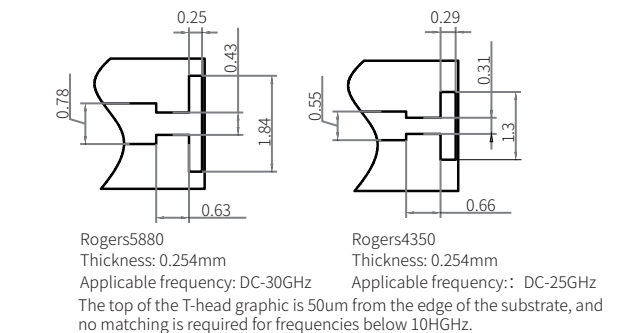


- Caveat
- 1、It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;

2、The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);

3、The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;

4、Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB9185-2370-7

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

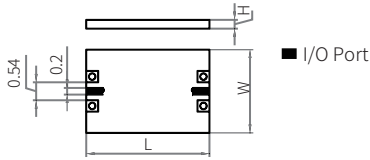
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

► Electrical Specifications

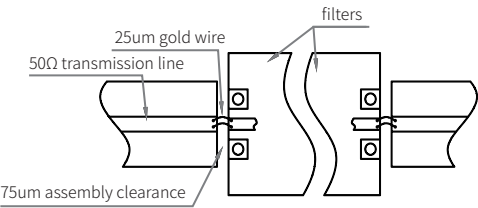
	Min	Typical	Max	
Center Freq	-	9.185	-	GHz
Band Freq	8	-	10.37	GHz
Fc IL	-	1.5	-	dB
Passband Ripple	-	-	1.2	dB
VSWR	-	1.8	-	-
Rejection	≥40dB@6.2 GHz			
	≥40dB@12.2 GHz			

► Overall Dimensions

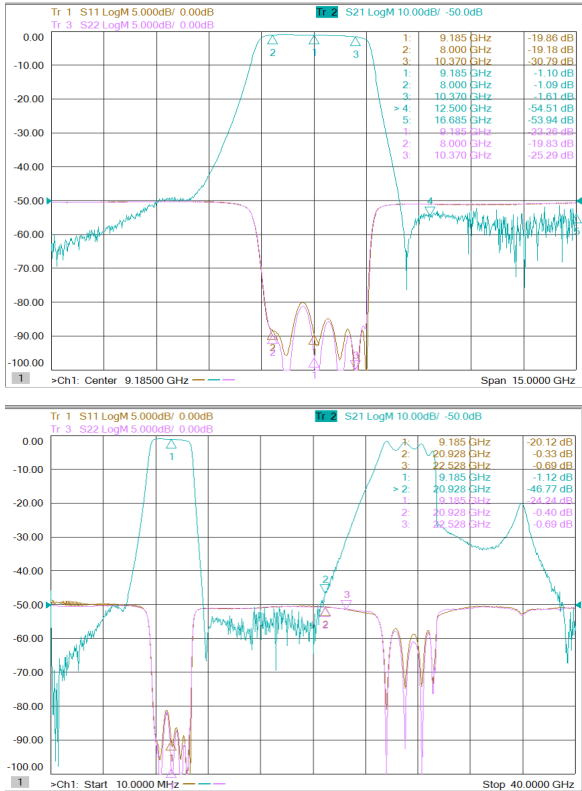


notation	value	unit
L	5.5	mm
W	4.0	mm
H	0.254	mm

► Suggested Assembly Drawings

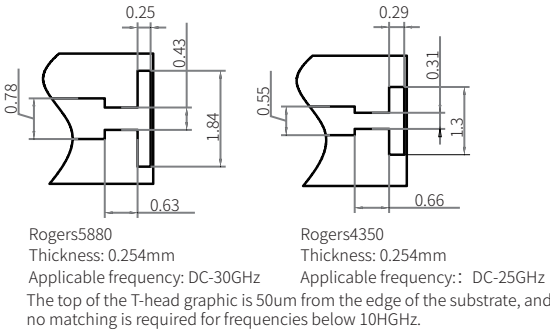


► Typical Curve



► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB9200-200-4

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

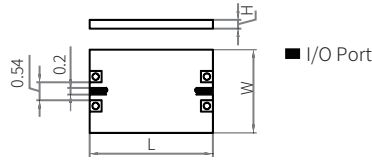
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

► Electrical Specifications

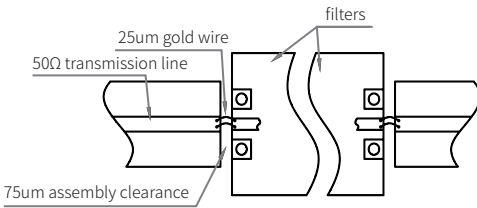
	Min	Typical	Max	
Center Freq	-	9.2	-	GHz
Band Freq	9.1	-	9.3	GHz
Fc IL	-	3.0	-	dB
Passband Ripple	-	-	-	dB
VSWR	-	1.8	-	-
Rejection	≥50dB@8.26 GHz			
	≥50dB@10.14 GHz			

► Overall Dimensions

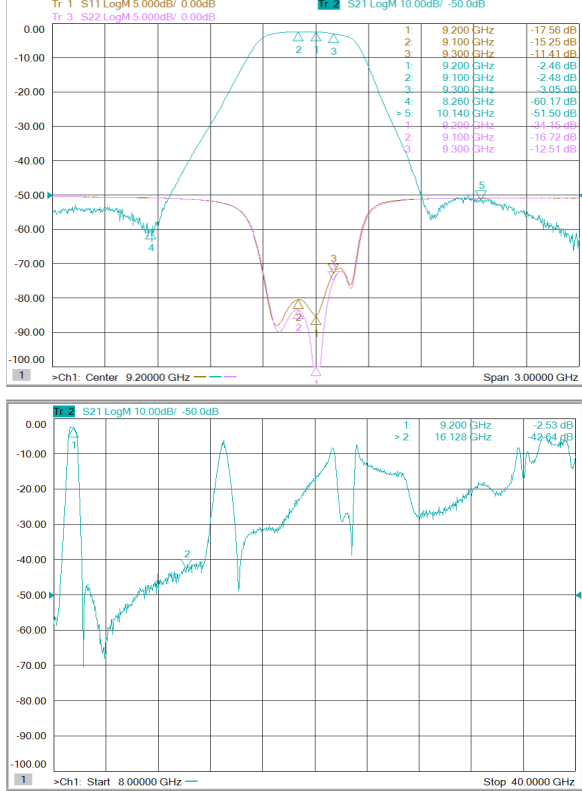


notation	value	unit
L	7.5	mm
W	5.3	mm
H	0.381	mm

► Suggested Assembly Drawings

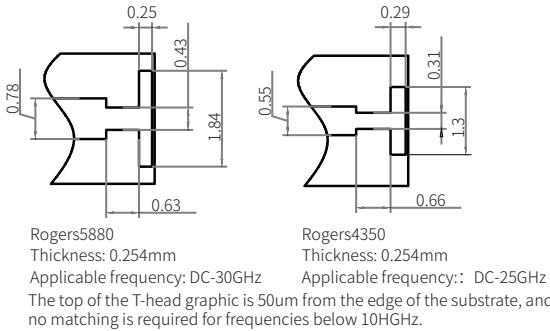


► Typical Curve



► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB9497.5-1835-6

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

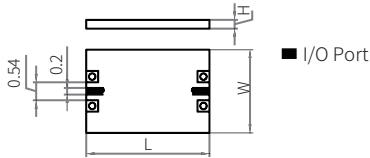
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

► Electrical Specifications

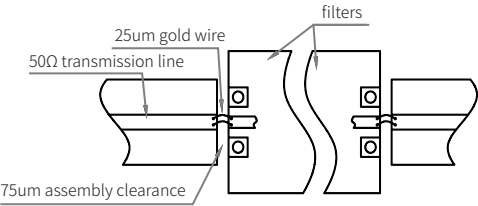
	Min	Typical	Max	
Center Freq	-	9.4975	-	GHz
Band Freq	8.58	-	10.415	GHz
Fc IL	-	1.5	-	dB
Passband Ripple	-	-	1.0	dB
VSWR	-	1.8	-	-
Rejection	≥40dB@5.25 GHz			
	≥50dB@12.8 GHz			

► Overall Dimensions

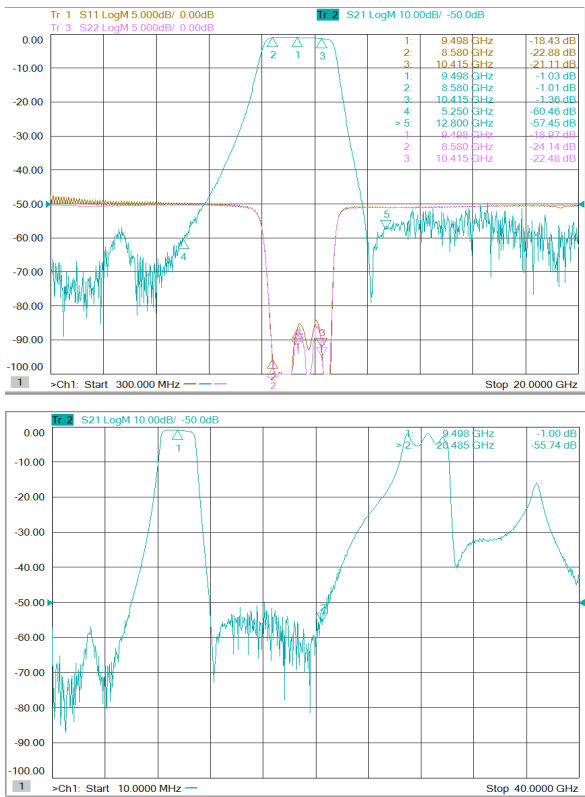


notation	value	unit
L	5.5	mm
W	3.8	mm
H	0.254	mm

► Suggested Assembly Drawings

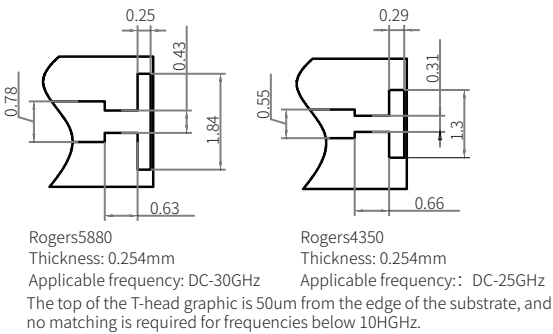


► Typical Curve



► Caveat

- 1、It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2、The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3、The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4、Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB9500-3500-10

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

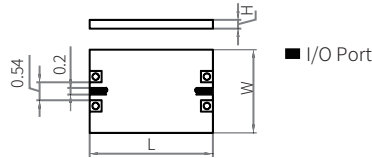
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

► Electrical Specifications

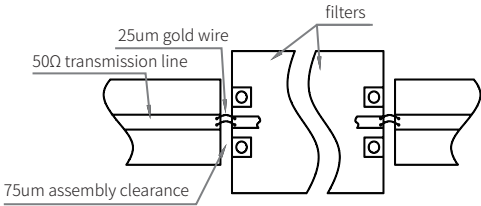
	Min	Typical	Max	
Center Freq	-	9.5	-	GHz
Band Freq	7.75	-	11.25	GHz
Fc IL	-	2.0	-	dB
Passband Ripple	-	-	1.0	dB
VSWR	-	1.8	-	-
Rejection	≥45dB@DC~6 GHz			
	≥45dB@12.5~20 GHz			

► Overall Dimensions

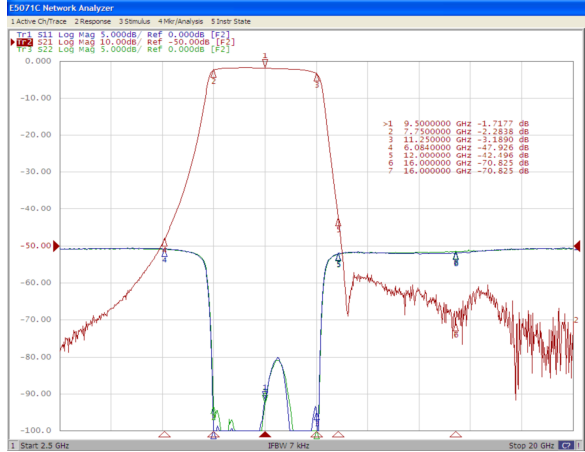


notation	value	unit
L	7.0	mm
W	4.0	mm
H	0.254	mm

► Suggested Assembly Drawings

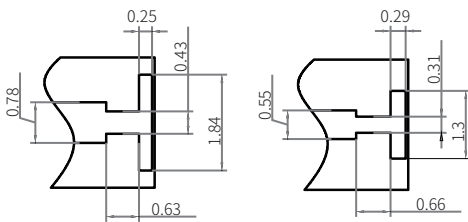


► Typical Curve



► Caveat

- 1、It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2、The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3、The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4、Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



Rogers5880 Thickness: 0.254mm Applicable frequency: DC-30GHz
Rogers4350 Thickness: 0.254mm Applicable frequency: DC-25GHz

The top of the T-head graphic is 50um from the edge of the substrate, and no matching is required for frequencies below 10GHz.

IYFTB9500-1000-9

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

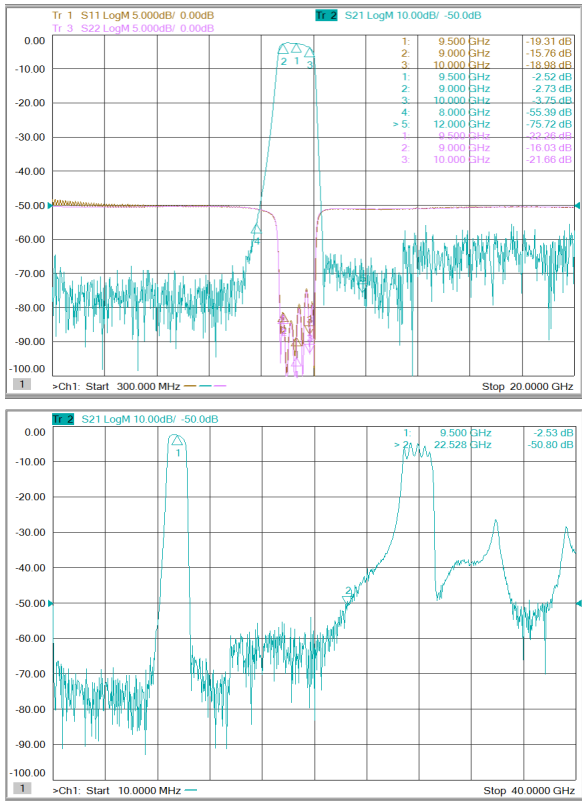
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

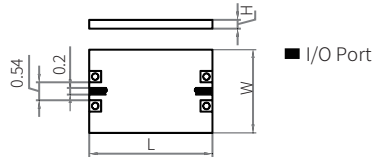
► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	9.5	-	GHz
Band Freq	9.0	-	10	GHz
Fc IL	-	2.5	-	dB
Passband Ripple	-	-	1	dB
VSWR	-	1.8	-	-
Rejection	≥30dB@8 GHz			
	≥60dB@12 GHz			

► Typical Curve



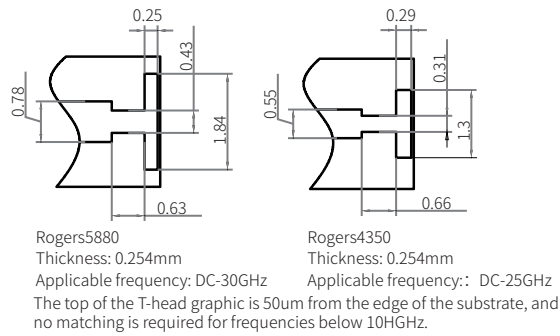
► Overall Dimensions



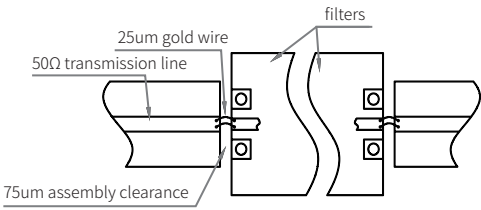
notation	value	unit
L	9.0	mm
W	4.0	mm
H	0.254	mm

► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



► Suggested Assembly Drawings



IYFTB9500-1800-9

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

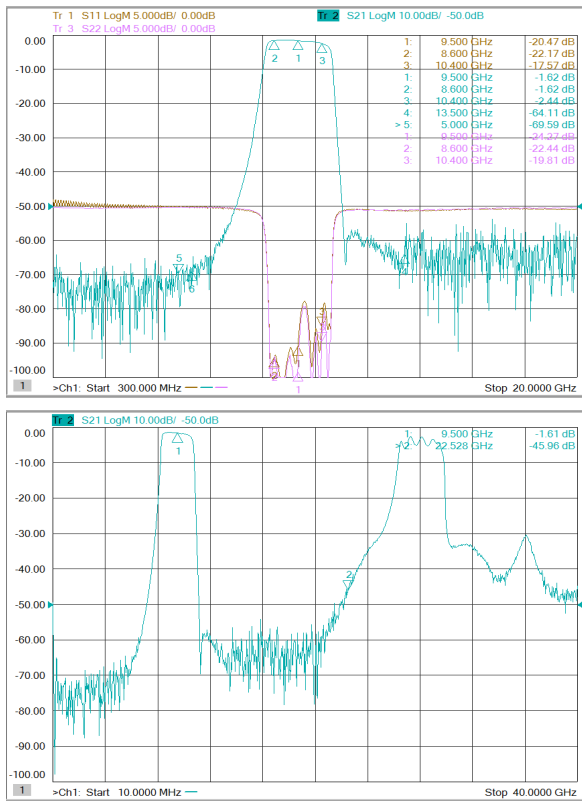
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

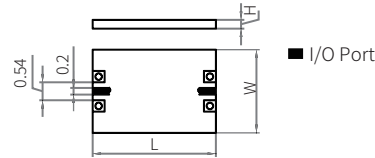
► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	9.5	-	GHz
Band Freq	8.6	-	10.4	GHz
Fc IL	-	2.0	-	dB
Passband Ripple	-	-	1.0	dB
VSWR	-	1.8	-	-
Rejection	≥60dB@5 GHz			
	≥60dB@12 GHz			

► Typical Curve



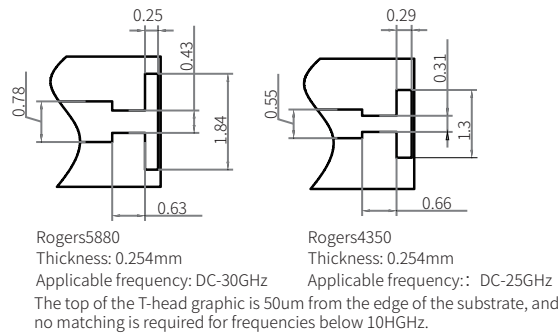
► Overall Dimensions



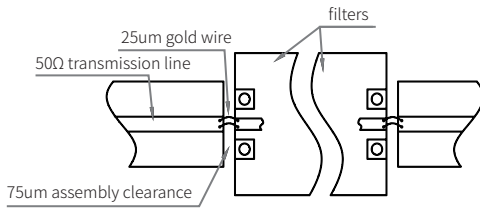
notation	value	unit
L	7.5	mm
W	4.0	mm
H	0.254	mm

► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



► Suggested Assembly Drawings



IYFTB9650-3900-7

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

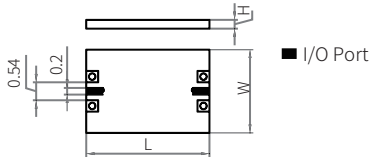
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

► Electrical Specifications

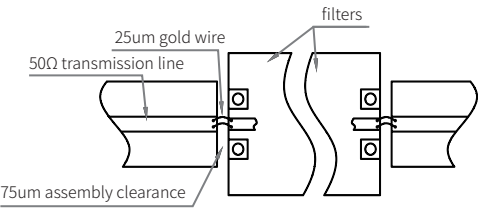
	Min	Typical	Max	
Center Freq	-	9.65	-	GHz
Band Freq	7.7	-	11.6	GHz
Fc IL	-	2.0	-	dB
Passband Ripple	-	-	1.0	dB
VSWR	-	1.8	-	-
Rejection	≥45dB@4 GHz			
	≥50dB@16 GHz			

► Overall Dimensions

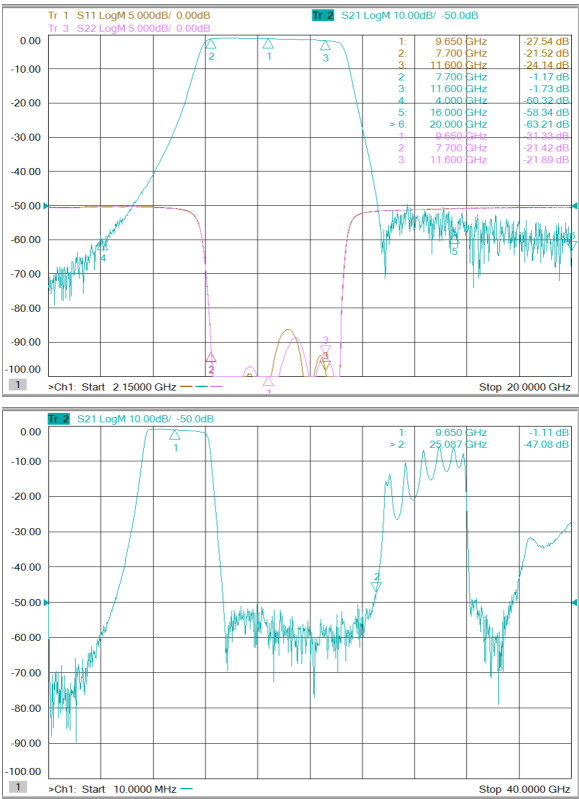


notation	value	unit
L	6.5	mm
W	3.7	mm
H	0.254	mm

► Suggested Assembly Drawings

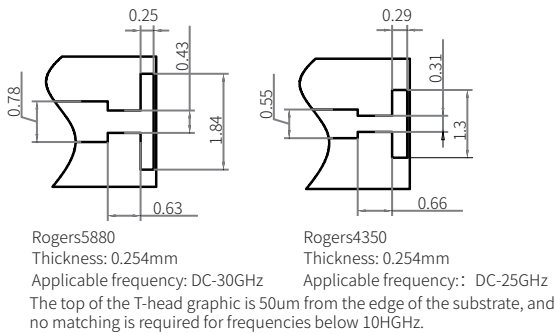


► Typical Curve



► Caveat

- 1、It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2、The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3、The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4、Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB9750-100-5

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

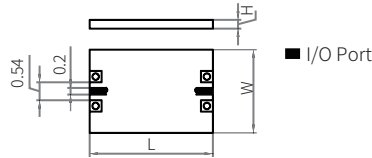
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

► Electrical Specifications

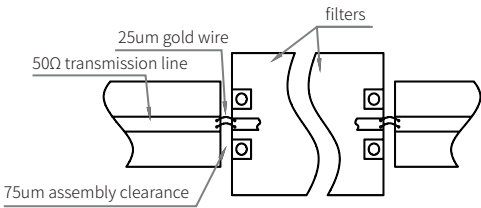
	Min	Typical	Max	
Center Freq	-	9.75	-	GHz
Band Freq	9.7	-	9.8	GHz
Fc IL	-	4.0	-	dB
Passband Ripple	-	-	1.0	dB
VSWR	-	1.8	-	-
Rejection	≥40dB@9 GHz			
	≥40dB@10.5 GHz			

► Overall Dimensions

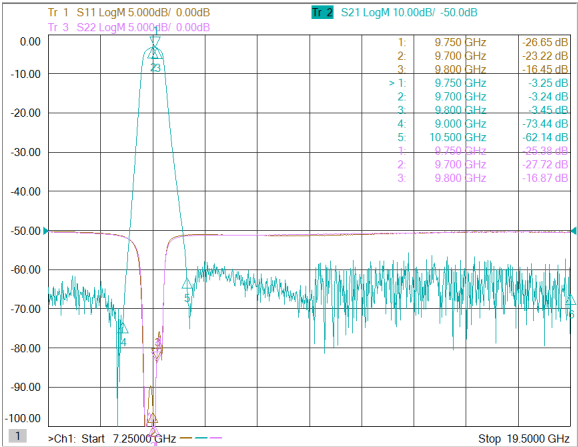


notation	value	unit
L	5.5	mm
W	4.0	mm
H	0.254	mm

► Suggested Assembly Drawings

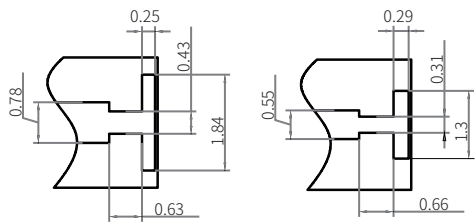


► Typical Curve



► Caveat

- 1、It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2、The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3、The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4、Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



Rogers5880 Thickness: 0.254mm Applicable frequency: DC-30GHz
Rogers4350 Thickness: 0.254mm Applicable frequency: DC-25GHz

The top of the T-head graphic is 50um from the edge of the substrate, and no matching is required for frequencies below 10GHz.

IYFTB10000-2000-8

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

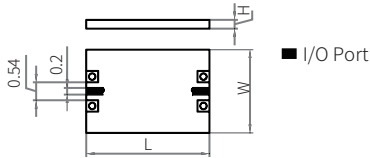
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

► Electrical Specifications

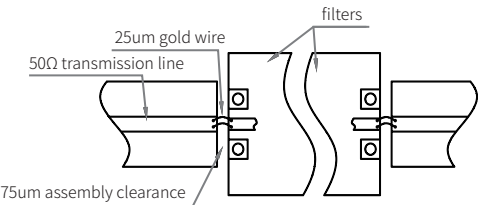
	Min	Typical	Max	
Center Freq	-	10	-	GHz
Band Freq	9	-	11	GHz
Fc IL	-	2	-	dB
Passband Ripple	-	-	1.0	dB
VSWR	-	1.8	-	-
Rejection	≥45dB@7.5 GHz			
	≥45dB@12.45 GHz			

► Overall Dimensions

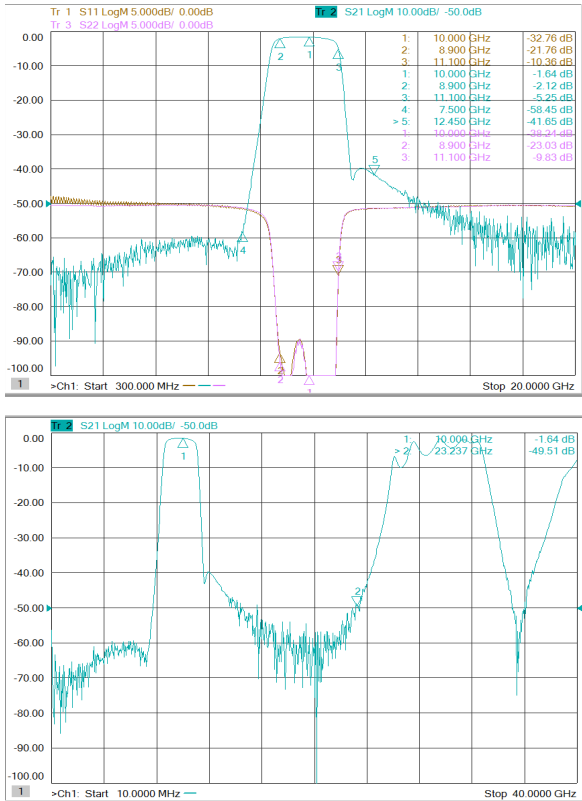


notation	value	unit
L	5.5	mm
W	3.8	mm
H	0.254	mm

► Suggested Assembly Drawings

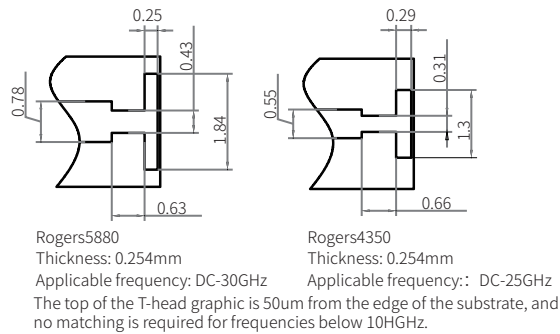


► Typical Curve



► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB10000-4500-10

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

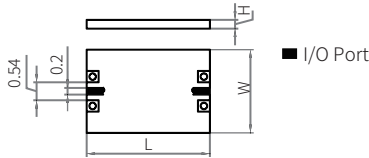
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

► Electrical Specifications

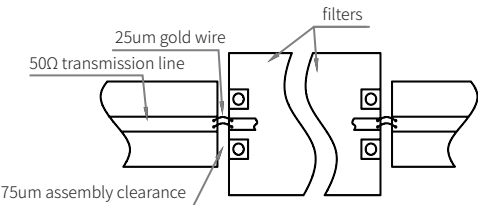
	Min	Typical	Max	
Center Freq	-	10	-	GHz
Band Freq	7.75	-	12.25	GHz
Fc IL	-	2.0	-	dB
Passband Ripple	-	-	1.0	dB
VSWR	-	1.8	-	-
Rejection	≥45dB@DC~6 GHz			
	≥45dB@14~24 GHz			

► Overall Dimensions

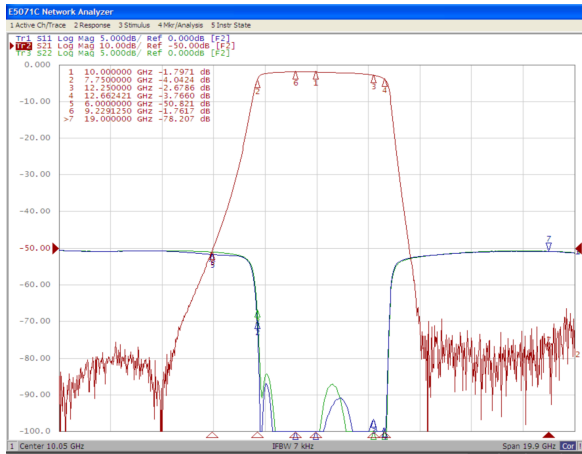


notation	value	unit
L	7.5	mm
W	3.8	mm
H	0.254	mm

► Suggested Assembly Drawings

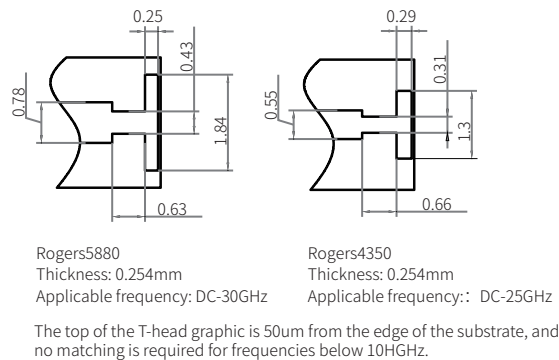


► Typical Curve



► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



Rogers5880
Thickness: 0.254mm
Applicable frequency: DC-30GHz

Rogers4350
Thickness: 0.254mm
Applicable frequency: DC-25GHz

The top of the T-head graphic is 50um from the edge of the substrate, and no matching is required for frequencies below 10GHz.

IYFTB10000-6000-9

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

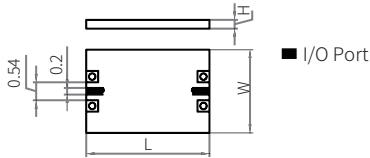
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

► Electrical Specifications

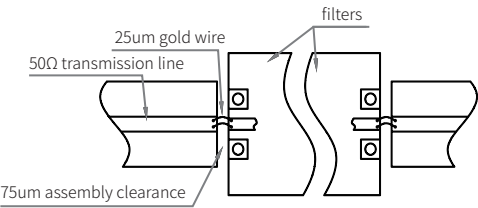
	Min	Typical	Max	
Center Freq	-	10	-	GHz
Band Freq	7	-	13	GHz
Fc IL	-	1.5	-	dB
Passband Ripple	-	-	0.8	dB
VSWR	-	1.8	-	-
Rejection	≥30dB@5GHz			
	≥35dB@16 GHz			

► Overall Dimensions

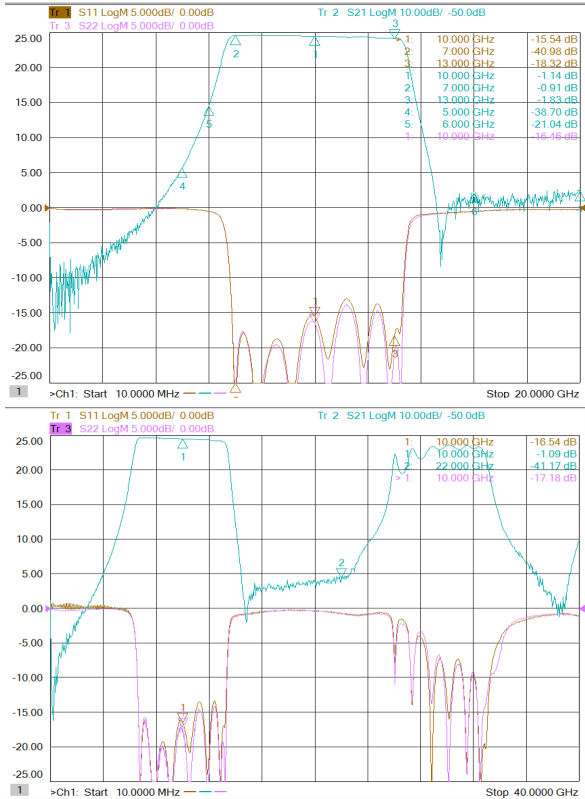


notation	value	unit
L	7.5	mm
W	3.5	mm
H	0.381	mm

► Suggested Assembly Drawings

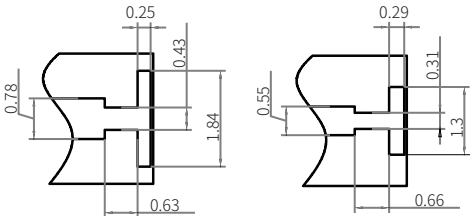


► Typical Curve



► Caveat

- 1、It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2、The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3、The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4、Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



Rogers5880
Thickness: 0.254mm
Applicable frequency: DC-30GHz
The top of the T-head graphic is 50um from the edge of the substrate, and no matching is required for frequencies below 10HGHz.

Rogers4350
Thickness: 0.254mm
Applicable frequency: DC-25GHz

IYFTB10150-4900-8

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

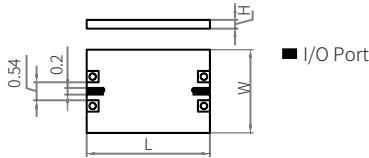
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

► Electrical Specifications

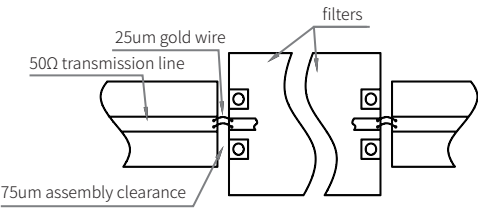
	Min	Typical	Max	
Center Freq	-	10.15	-	GHz
Band Freq	7.7	-	12.6	GHz
Fc IL	-	1.8	-	dB
Passband Ripple	-	-	1.0	dB
VSWR	-	1.8	-	-
Rejection	≥45dB@4.8 GHz			
	≥45dB@15.6 GHz			

► Overall Dimensions

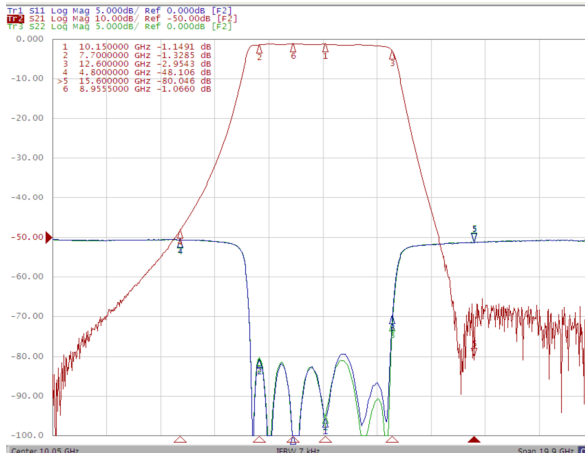


notation	value	unit
L	7.0	mm
W	4.0	mm
H	0.381	mm

► Suggested Assembly Drawings

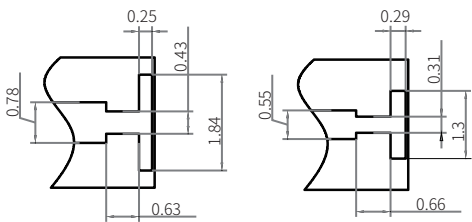


► Typical Curve



► Caveat

- 1、It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2、The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3、The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4、Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



Rogers5880
Thickness: 0.254mm
Applicable frequency: DC-30GHz

Rogers4350
Thickness: 0.254mm
Applicable frequency: DC-25GHz

The top of the T-head graphic is 50um from the edge of the substrate, and no matching is required for frequencies below 10HGHz.

IYFTB10170-1020-9

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

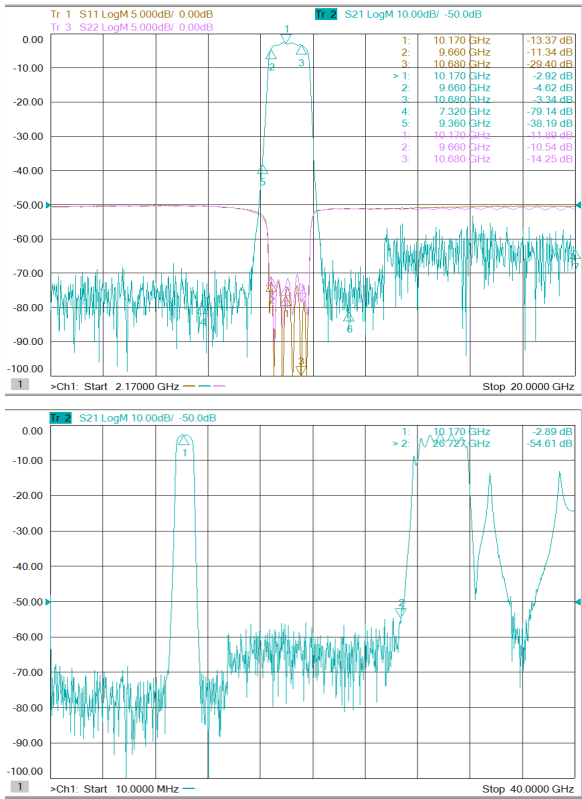
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

► Electrical Specifications

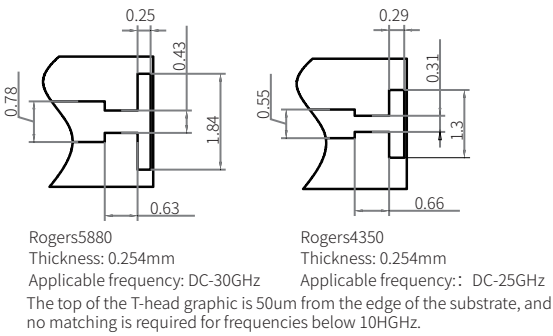
	Min	Typical	Max	
Center Freq	-	10.17	-	GHz
Band Freq	9.66	-	10.68	GHz
Fc IL	-	3.0	-	dB
Passband Ripple	-	-	-	dB
VSWR	-	1.8	-	-
Rejection	≥30dB@9.36 GHz			
	≥40dB@12.3 GHz			

► Typical Curve

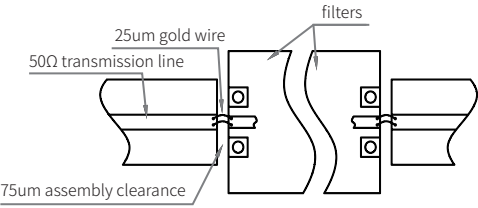


► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



► Suggested Assembly Drawings



IYFTB10170A-1020-9

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

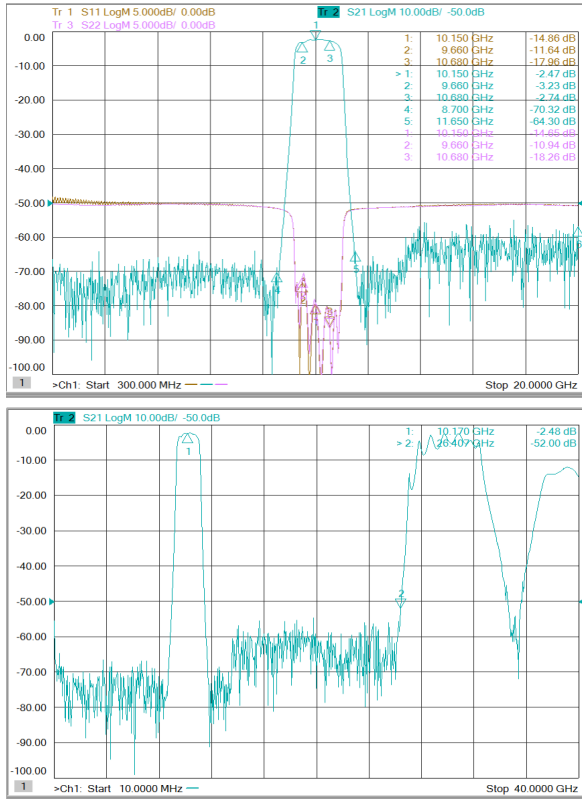
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

► Electrical Specifications

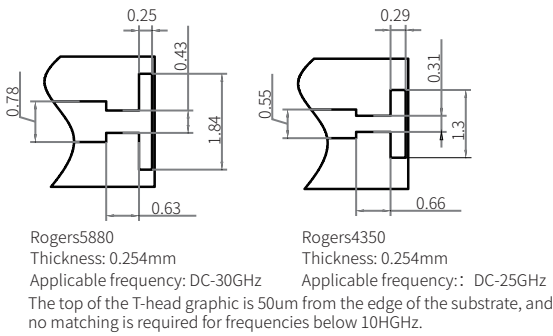
	Min	Typical	Max	
Center Freq	-	10.17	-	GHz
Band Freq	9.66	-	10.68	GHz
Fc IL	-	3	-	dB
Passband Ripple	-	-	1.2	dB
VSWR	-	1.8	-	-
Rejection	≥40dB@8.7 GHz			
	≥40dB@11.65 GHz			

► Typical Curve

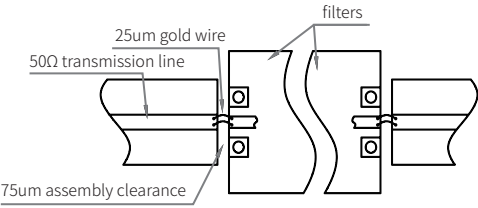


► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



► Suggested Assembly Drawings



IYFTB10200-1920-4

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

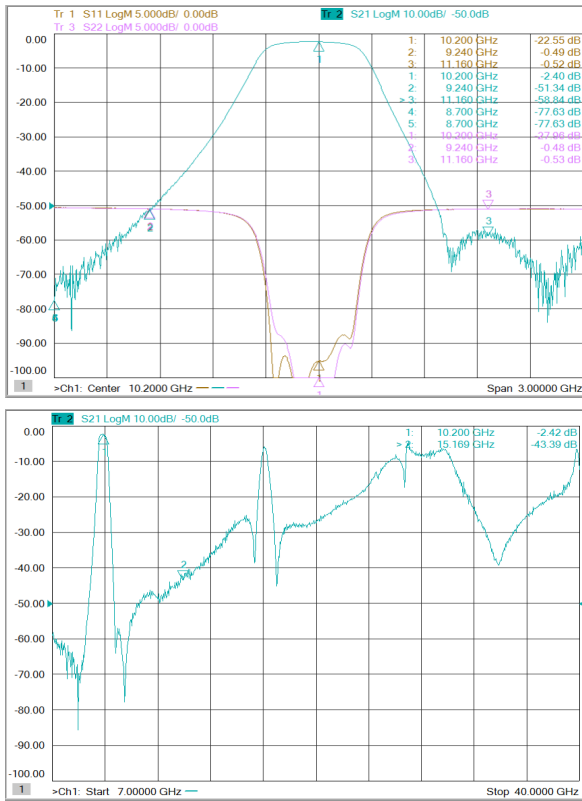
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

► Electrical Specifications

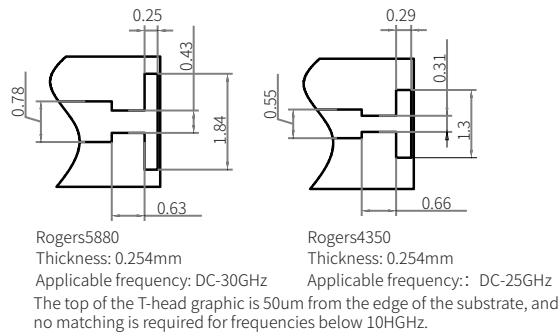
	Min	Typical	Max	
Center Freq	-	10.2	-	GHz
Band Freq	-	-	-	GHz
Fc IL	-	3	-	dB
Passband Ripple	-	-	1.0	dB
VSWR	-	1.8	-	-
Rejection	≥50dB@9.24 GHz			
	≥50dB@11.16 GHz			

► Typical Curve

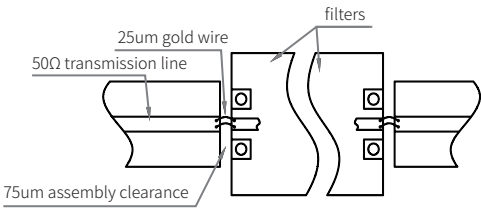


► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



► Suggested Assembly Drawings



IYFTB10200-5000-9

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

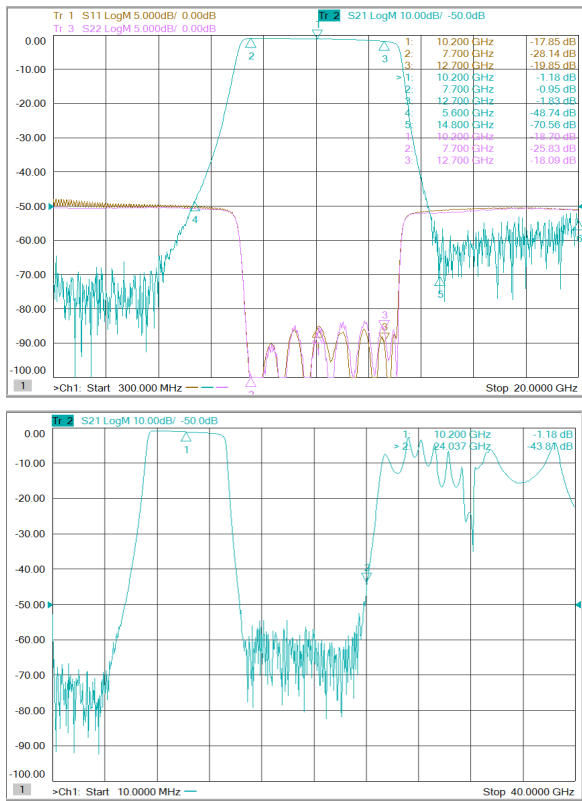
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

► Electrical Specifications

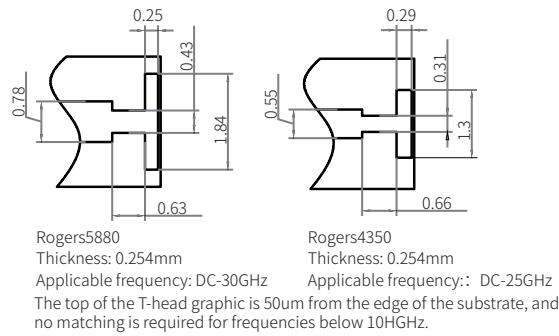
	Min	Typical	Max	
Center Freq	-	10.2	-	GHz
Band Freq	7.7	-	12.7	GHz
Fc IL	-	1.5	-	dB
Passband Ripple	-	-	1.0	dB
VSWR	-	1.8	-	-
Rejection	≥40dB@5.6 GHz			
	≥40dB@14.8 GHz			

► Typical Curve

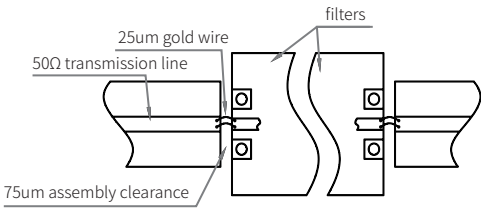


► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



► Suggested Assembly Drawings



IYFTB10920-1920-4

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

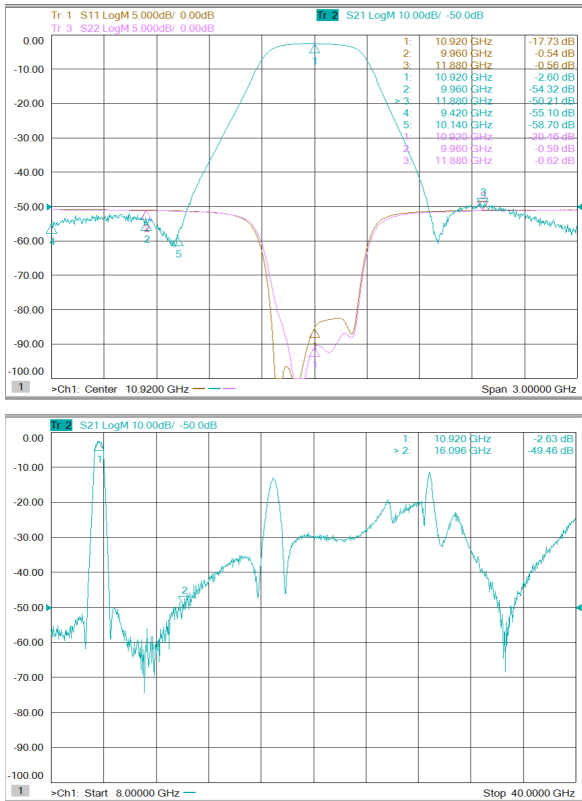
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

► Electrical Specifications

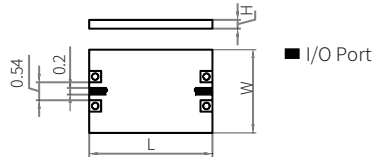
	Min	Typical	Max	
Center Freq	-	10.92	-	GHz
Band Freq	-	-	-	GHz
Fc IL	-	3.0	-	dB
Passband Ripple	-	-	-	dB
VSWR	-	1.8	-	-
Rejection	≥40dB@9.94 GHz			
	≥40dB@11.88 GHz			

► Typical Curve



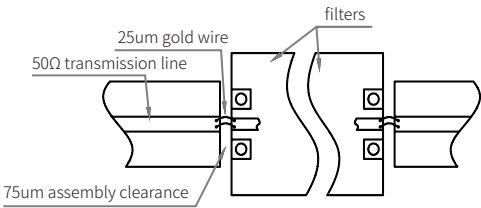
► Caveat

► Overall Dimensions

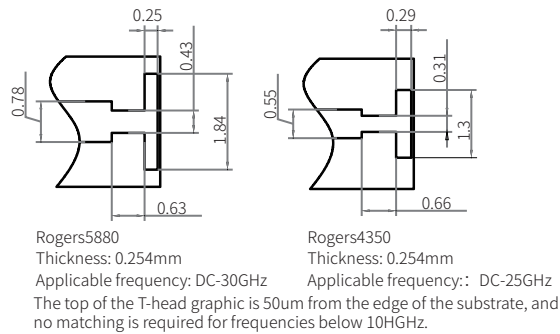


notation	value	unit
L	7.5	mm
W	5	mm
H	0.381	mm

► Suggested Assembly Drawings



- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB11000-2500-7

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

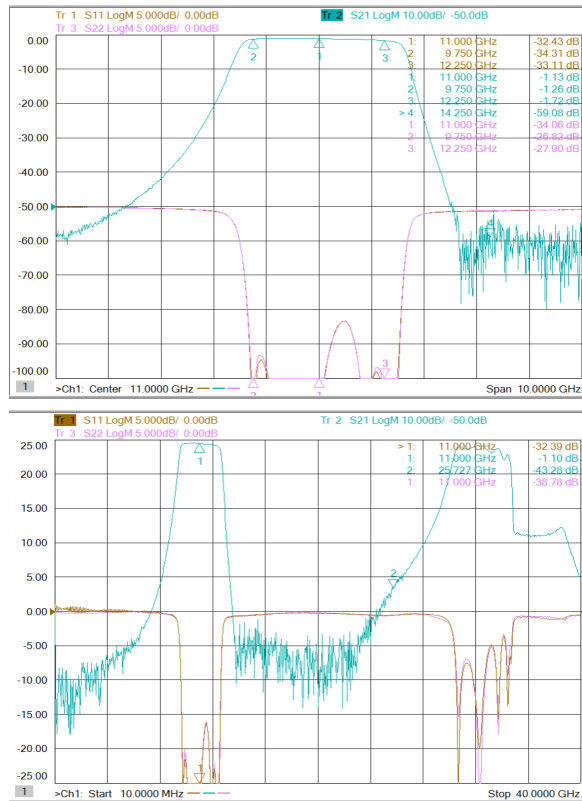
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

► Electrical Specifications

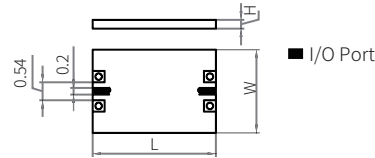
	Min	Typical	Max	
Center Freq	-	11	-	GHz
Band Freq	9.75	-	12.25	GHz
Fc IL	-	2.0	-	dB
Passband Ripple	-	-	1.2	dB
VSWR	-	1.8	-	-
Rejection	≥40dB@7.8 GHz			
	≥40dB@14.2 GHz			

► Typical Curve



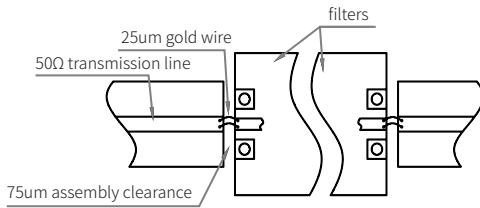
► Caveat

► Overall Dimensions

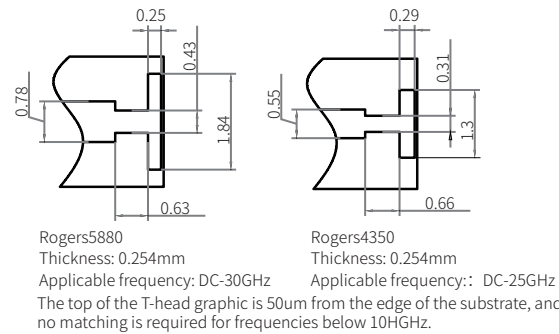


notation	value	unit
L	6.0	mm
W	3.5	mm
H	0.254	mm

► Suggested Assembly Drawings



- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB11000-6200-10

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

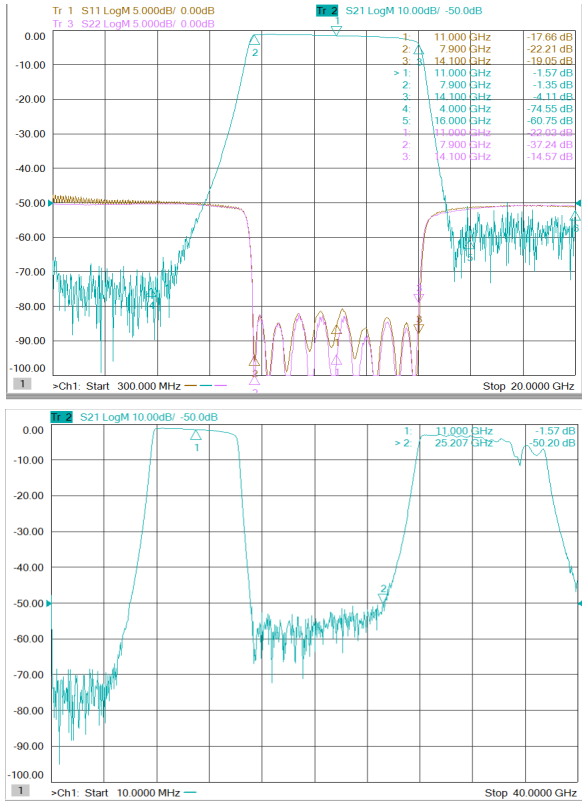
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

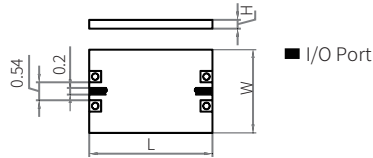
► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	11	-	GHz
Band Freq	7.9	-	14.1	GHz
Fc IL	-	2.0	-	dB
Passband Ripple	-	-	1.0	dB
VSWR	-	1.8	-	-
Rejection	≥60dB@4 GHz			
	≥40dB@16 GHz			

► Typical Curve



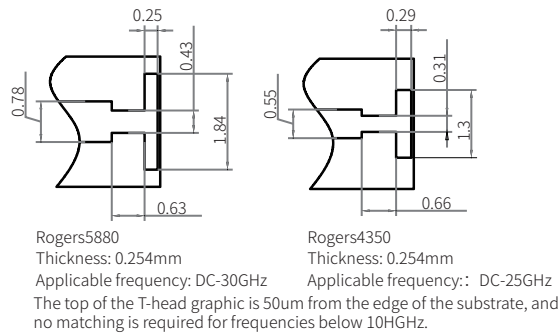
► Overall Dimensions



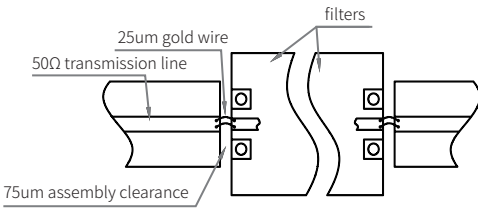
notation	value	unit
L	9.0	mm
W	4.0	mm
H	0.381	mm

► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



► Suggested Assembly Drawings



IYFTB11200-600-7

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

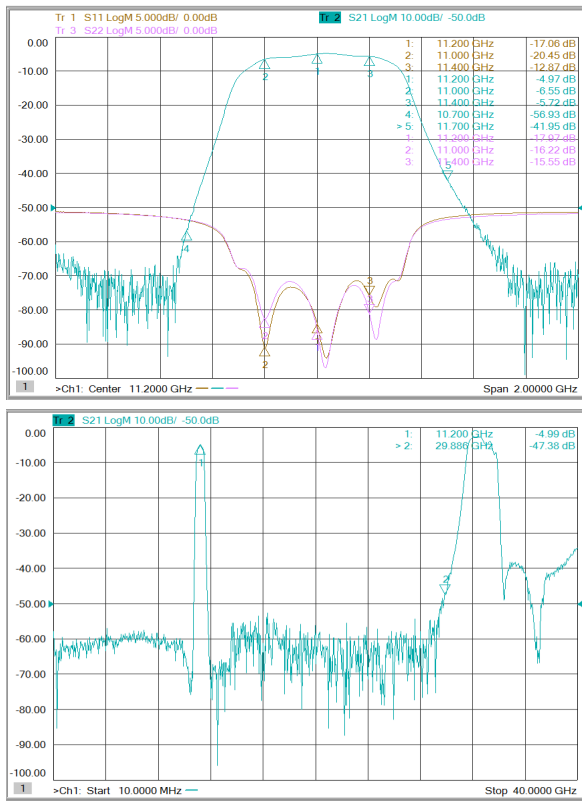
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

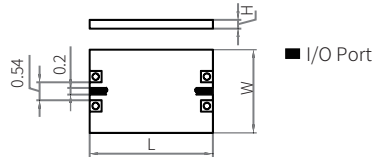
► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	11.2	-	GHz
Band Freq	10.9	-	11.5	GHz
Fc IL	-	5.0	-	dB
Passband Ripple	-	-	1.0	dB
VSWR	-	1.8	-	-
Rejection	≥50dB@9.6 GHz			
	≥50dB@12.1 GHz			

► Typical Curve



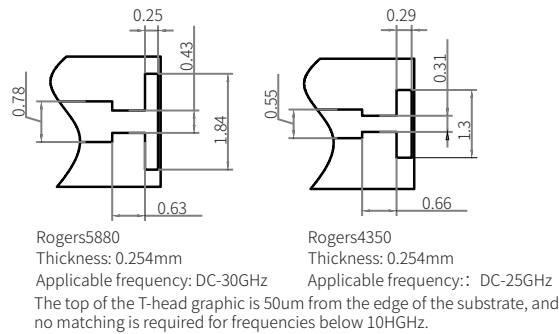
► Overall Dimensions



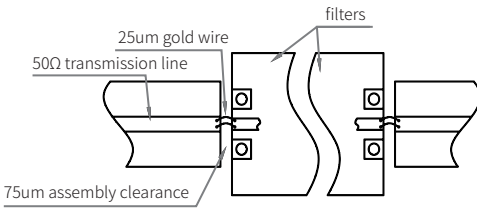
notation	value	unit
L	7.5	mm
W	3.5	mm
H	0.254	mm

► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



► Suggested Assembly Drawings



IYFTB11300-1800-8

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

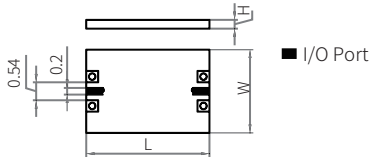
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

► Electrical Specifications

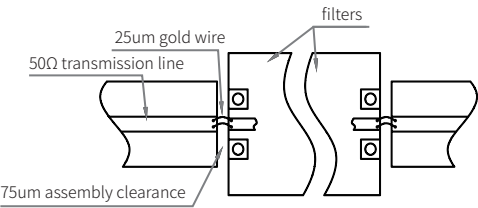
	Min	Typical	Max	
Center Freq	-	11.3	-	GHz
Band Freq	10.4	-	12.2	GHz
Fc IL	-	2.0	-	dB
Passband Ripple	-	-	1.7	dB
VSWR	-	1.8	-	-
Rejection	≥20dB@9.8GHz			
	≥20dB@12.8 GHz			

► Overall Dimensions

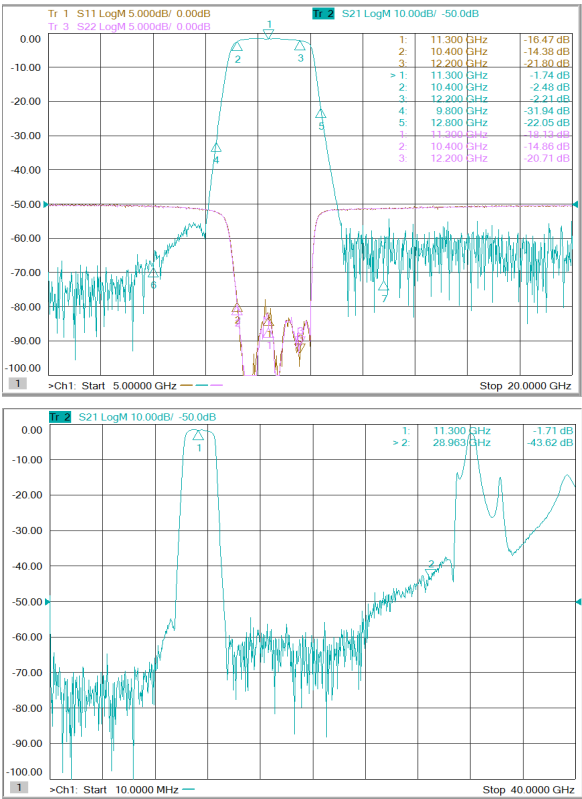


notation	value	unit
L	7.5	mm
W	3	mm
H	0.381	mm

► Suggested Assembly Drawings

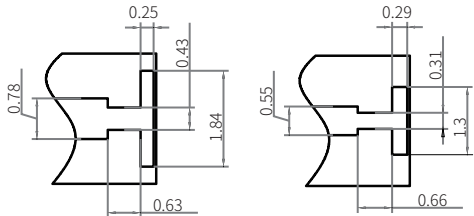


► Typical Curve



► Caveat

- 1、It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2、The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3、The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4、Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



Rogers5880
Thickness: 0.254mm
Applicable frequency: DC-30GHz
The top of the T-head graphic is 50um from the edge of the substrate, and no matching is required for frequencies below 10HGHz.

Rogers4350
Thickness: 0.254mm
Applicable frequency: DC-25GHz

IYFTB11400-2400-7

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

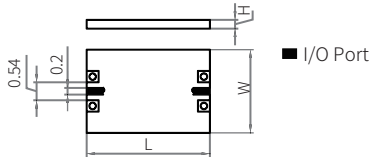
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

► Electrical Specifications

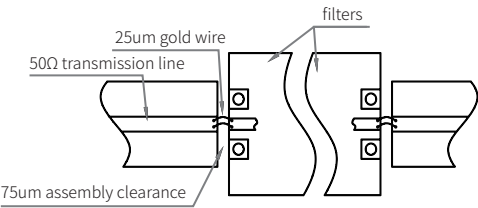
	Min	Typical	Max	
Center Freq	-	11.4	-	GHz
Band Freq	10.2	-	12.6	GHz
Fc IL	-	2.0	-	dB
Passband Ripple	-	-	1.0	dB
VSWR	-	1.8	-	-
Rejection	≥45dB@8.8 GHz			
	≥40dB@13.85 GHz			

► Overall Dimensions

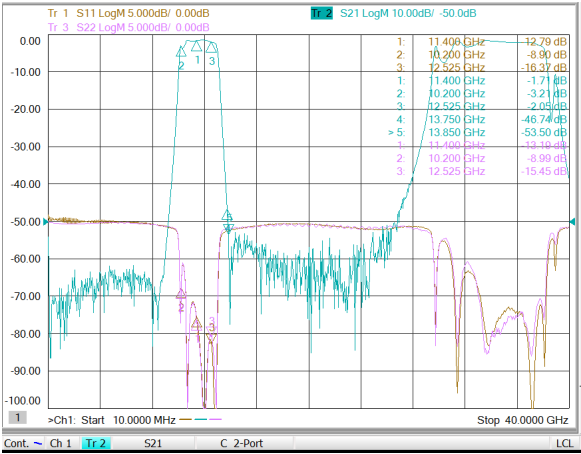


notation	value	unit
L	5.5	mm
W	3.5	mm
H	0.254	mm

► Suggested Assembly Drawings

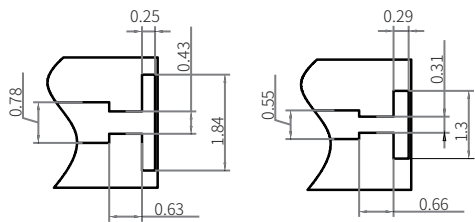


► Typical Curve



► Caveat

- 1、It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2、The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3、The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4、Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



Rogers5880
Thickness: 0.254mm
Applicable frequency: DC-30GHz

Rogers4350
Thickness: 0.254mm
Applicable frequency: DC-25GHz

The top of the T-head graphic is 50um from the edge of the substrate, and no matching is required for frequencies below 10HGHz.

IYFTB11600-100-5

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

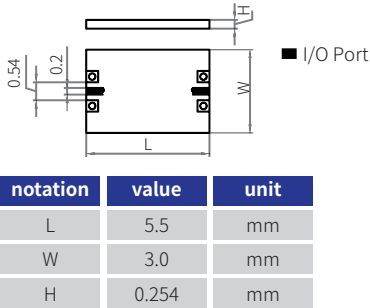
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

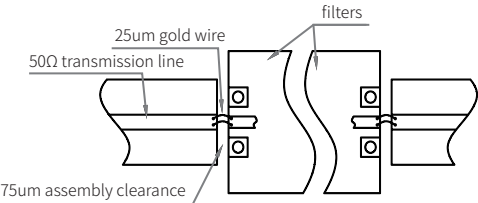
► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	11.6	-	GHz
Band Freq	11.55	-	11.6	GHz
Fc IL	-	5.5	5	dB
Passband Ripple	-	-	-	dB
VSWR	-	1.8	1.0	-
Rejection	≥35dB@11 GHz			
	≥35dB@12.1 GHz			

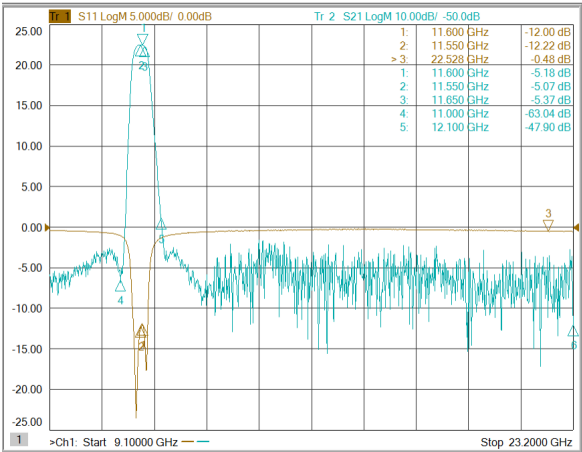
► Overall Dimensions



► Suggested Assembly Drawings

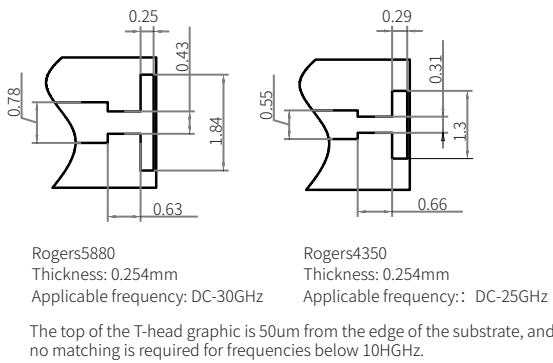


► Typical Curve



► Caveat

- 1、It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2、The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3、The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4、Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB11860-200-4

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

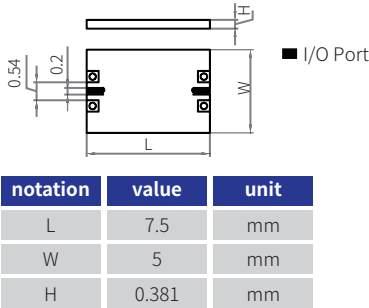
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

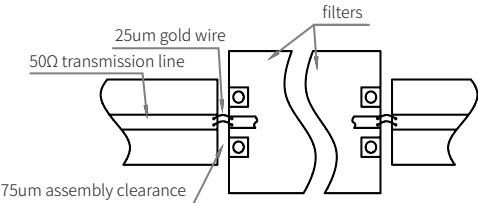
► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	11.86	-	GHz
Band Freq	11.76	-	11.96	GHz
Fc IL	-	3.0	-	dB
Passband Ripple	-	-	-	dB
VSWR	-	1.8	-	-
Rejection	≥50dB@10.92 GHz			
	≥50dB@12.8 GHz			

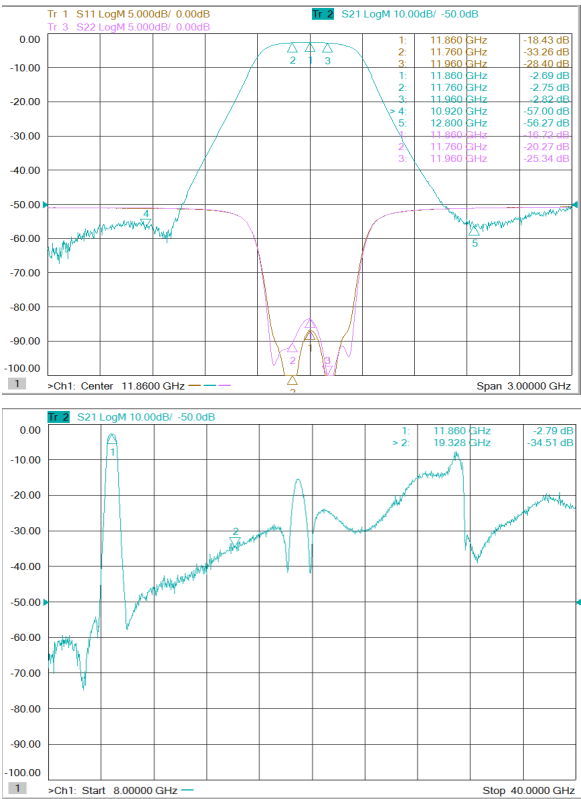
► Overall Dimensions



► Suggested Assembly Drawings

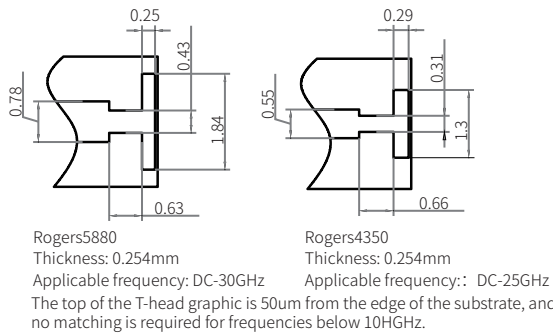


► Typical Curve



► Caveat

- 1、It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2、The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3、The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4、Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB12000-3000-8

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

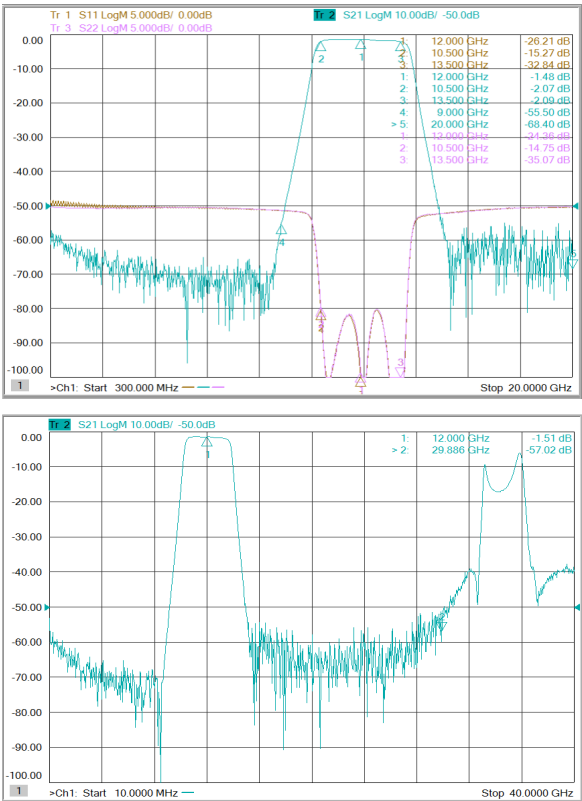
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

► Electrical Specifications

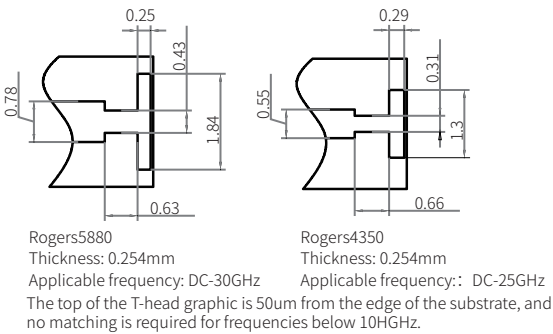
	Min	Typical	Max	
Center Freq	-	12	-	GHz
Band Freq	10.5	-	13.5	GHz
Fc IL	-	2.0	-	dB
Passband Ripple	-	-	1.0	dB
VSWR	-	1.5	-	-
Rejection	≥35dB@9 GHz			
	≥40dB@15 GHz			

► Typical Curve

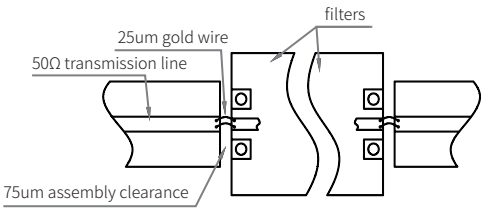


► Caveat

- 1、It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2、The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3、The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4、Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



► Suggested Assembly Drawings



IYFTB12000-4400-10

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

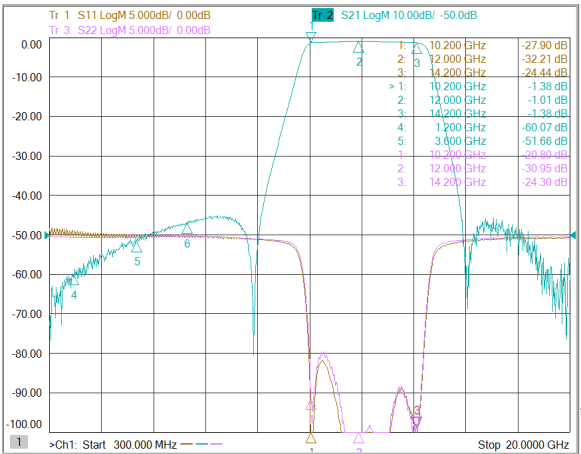
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	12	-	GHz
Band Freq	9.8	-	14.2	GHz
Fc IL	-	1.5	-	dB
Passband Ripple	-	-	1.0	dB
VSWR	-	1.8	-	-
Rejection	≥60dB@5 GHz			
	≥60dB@20 GHz			

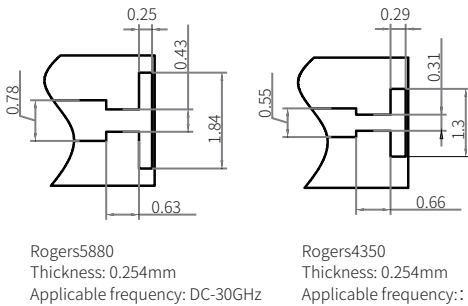
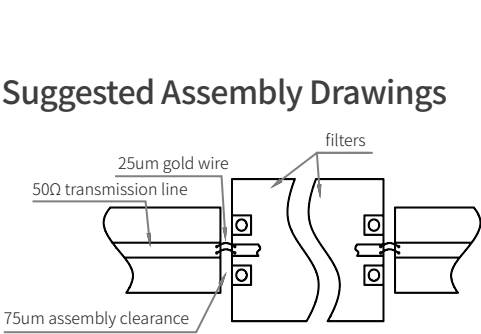
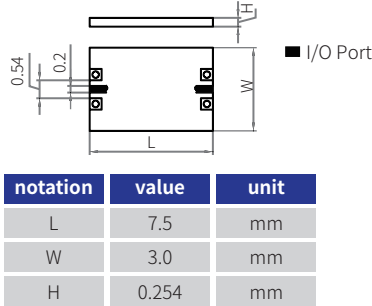
► Typical Curve



► Caveat

- 1、It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2、The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3、The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4、Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:

► Overall Dimensions



Rogers5880 Thickness: 0.254mm Applicable frequency: DC-30GHz
Rogers4350 Thickness: 0.254mm Applicable frequency: DC-25GHz

The top of the T-head graphic is 50um from the edge of the substrate, and no matching is required for frequencies below 10GHz.

IYFTB12500-2200-8

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

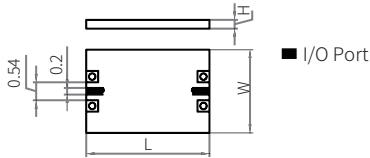
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

► Electrical Specifications

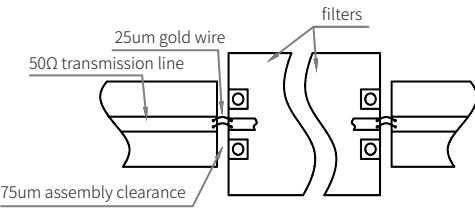
	Min	Typical	Max	
Center Freq	-	12.5	-	GHz
Band Freq	11.3	-	13.5	GHz
Fc IL	-	2.0	-	dB
Passband Ripple	-	-	1.0	dB
VSWR	-	1.8	-	-
Rejection	≥35dB@DC~10 GHz			
	≥40dB@15~26.5 GHz			

► Overall Dimensions

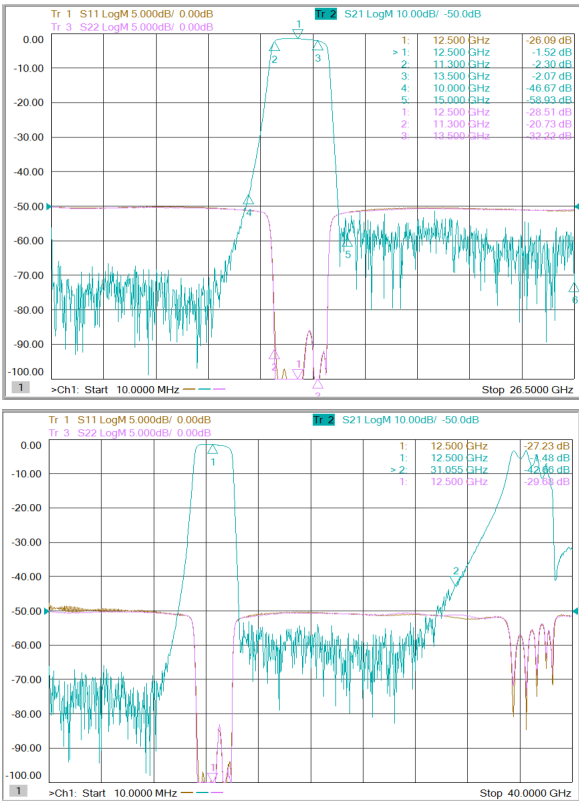


notation	value	unit
L	8.0	mm
W	3.2	mm
H	0.254	mm

► Suggested Assembly Drawings

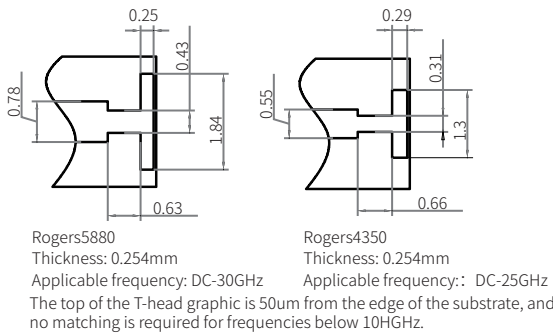


► Typical Curve



► Caveat

- 1、It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2、The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3、The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4、Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB12500-3500-10

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

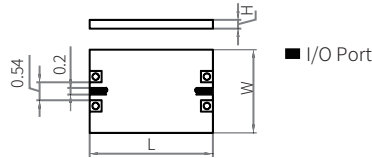
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

► Electrical Specifications

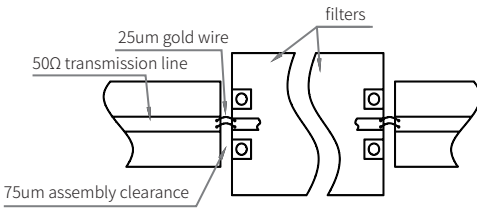
	Min	Typical	Max	
Center Freq	-	12.5	-	GHz
Band Freq	10.75	-	14.25	GHz
Fc IL	-	2.0	-	dB
Passband Ripple	-	-	1.3	dB
VSWR	-	1.8	-	-
Rejection	≥47dB@9.458 GHz			
	≥46dB@15.9 GHz			

► Overall Dimensions

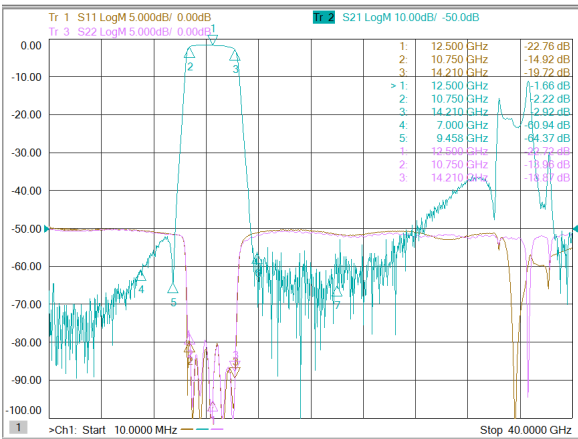


notation	value	unit
L	7	mm
W	3.4	mm
H	0.254	mm

► Suggested Assembly Drawings

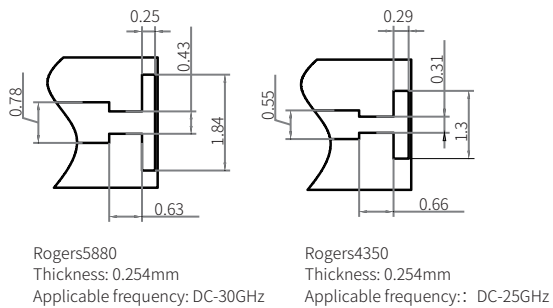


► Typical Curve



► Caveat

- 1、It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2、The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3、The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4、Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



Rogers5880 Thickness: 0.254mm Applicable frequency: DC-30GHz
Rogers4350 Thickness: 0.254mm Applicable frequency: DC-25GHz

The top of the T-head graphic is 50um from the edge of the substrate, and no matching is required for frequencies below 10GHz.

IYFTB13000-1800-8

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

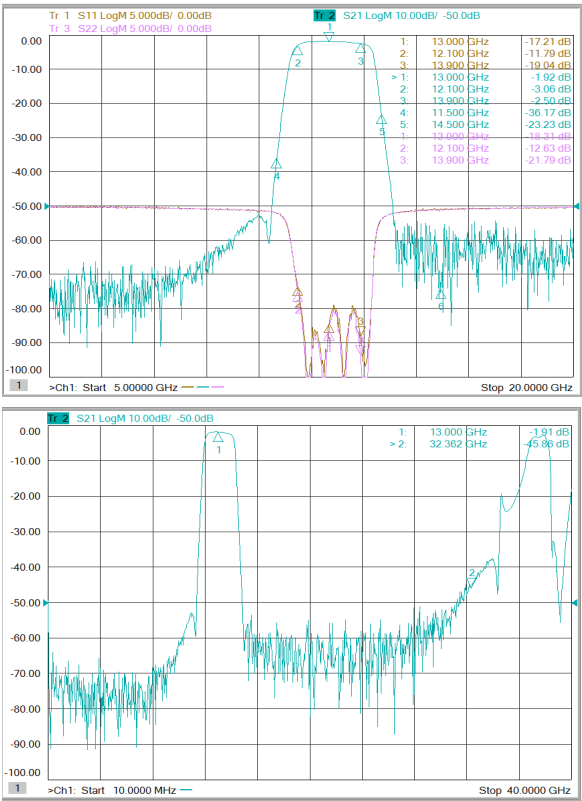
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

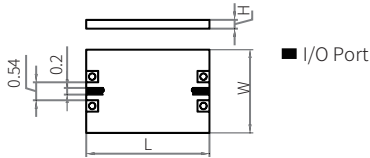
► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	13	-	GHz
Band Freq	12.1	-	13.9	GHz
Fc IL	-	2.5	-	dB
Passband Ripple	-	-	1.7	dB
VSWR	-	1.8	-	-
Rejection	≥20dB@11.5GHz			
	≥20dB@14.5GHz			

► Typical Curve

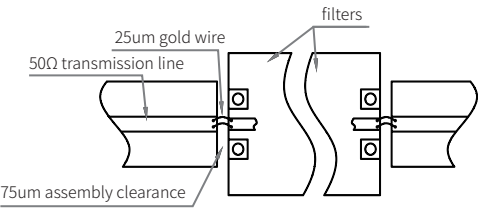


► Overall Dimensions



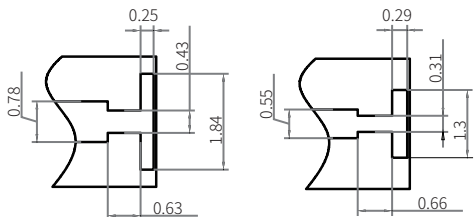
notation	value	unit
L	7.5	mm
W	3	mm
H	0.381	mm

► Suggested Assembly Drawings



► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



Rogers5880
Thickness: 0.254mm
Applicable frequency: DC-30GHz
The top of the T-head graphic is 50um from the edge of the substrate, and no matching is required for frequencies below 10HGHz.

Rogers4350
Thickness: 0.254mm
Applicable frequency: DC-25GHz
The top of the T-head graphic is 50um from the edge of the substrate, and no matching is required for frequencies below 10HGHz.

IYFTB13000-2500-7

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

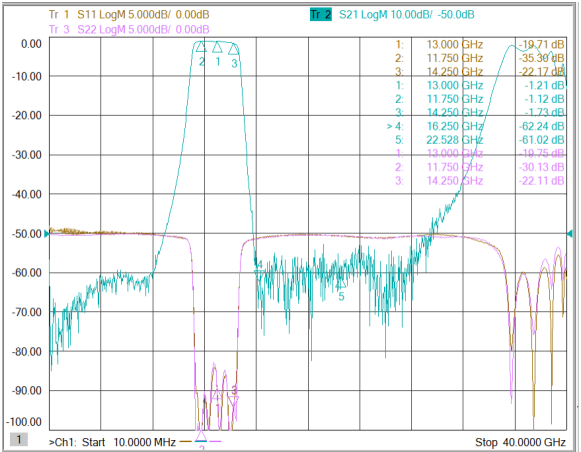
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	13	-	GHz
Band Freq	11.75	-	14.2	GHz
Fc IL	-	2.0	5	dB
Passband Ripple	-	-	-	dB
VSWR	-	1.8	1.2	-
Rejection	≥40dB@9.8 GHz			
	≥40dB@16.2 GHz			

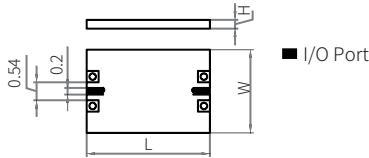
► Typical Curve



► Caveat

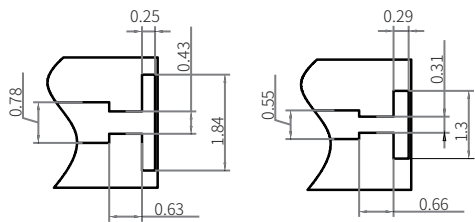
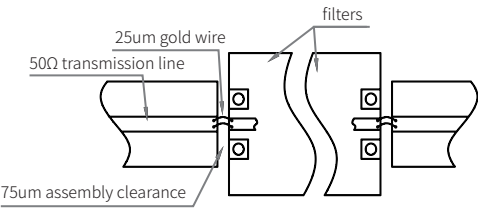
- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:

► Overall Dimensions



notation	value	unit
L	6.0	mm
W	3.0	mm
H	0.254	mm

► Suggested Assembly Drawings



Rogers5880
Thickness: 0.254mm
Applicable frequency: DC-30GHz

Rogers4350
Thickness: 0.254mm
Applicable frequency: DC-25GHz

The top of the T-head graphic is 50um from the edge of the substrate, and no matching is required for frequencies below 10HGHz.

IYFTB13000-4000-9

- Performance Characteristics
- 1、High precision micro-nanometer processing technology

2、High performance, low temperature drift, high power

3、Gold wire bonding, suitable for multi-chip integration module applications

4、50Ω coplanar waveguide output

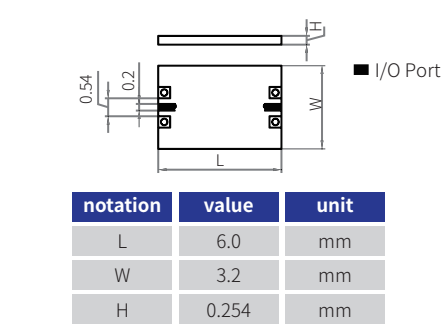
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

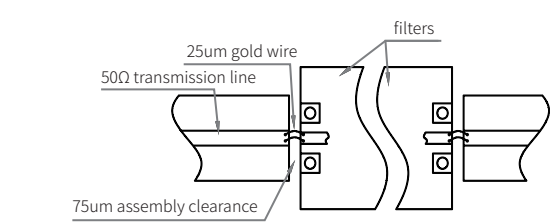
► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	13	-	GHz
Band Freq	11	-	15	GHz
Fc IL	-	2.0	-	dB
Passband Ripple	-	-	1	dB
VSWR	-	1.8	-	-
Rejection	≥40dB@8.5 GHz			
	≥50dB@16.8 GHz			

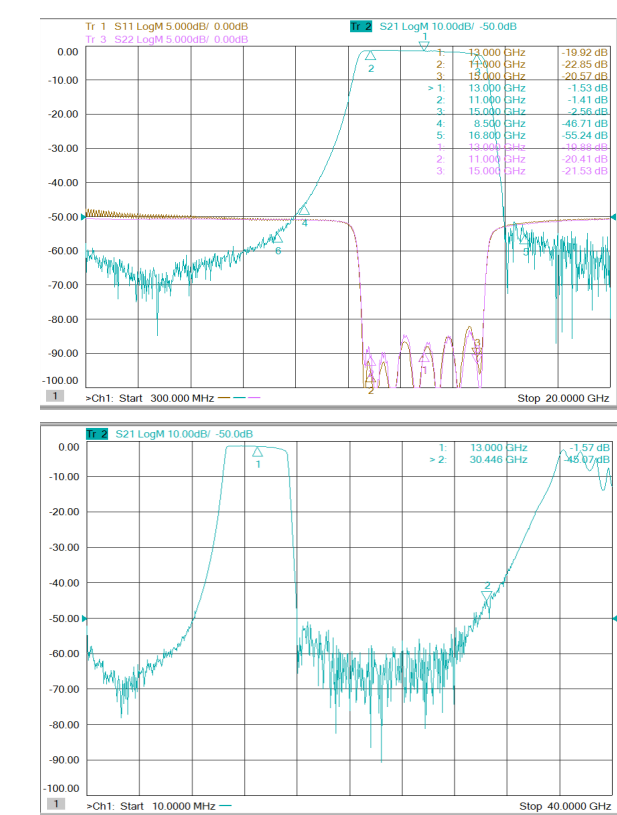
► Overall Dimensions



► Suggested Assembly Drawings

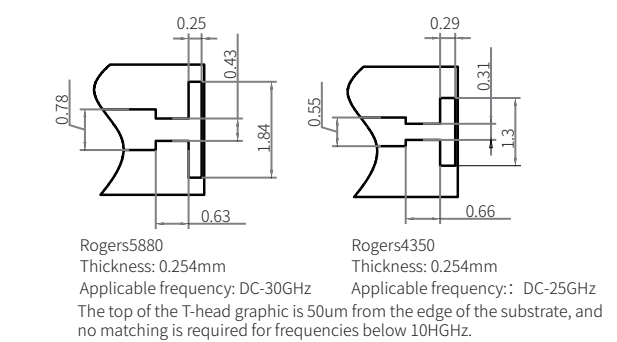


► Typical Curve



► Caveat

- 1、It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2、The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3、The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4、Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB13325-200-7

- Performance Characteristics
- 1、High precision micro-nanometer processing technology

2、High performance, low temperature drift, high power

3、Gold wire bonding, suitable for multi-chip integration module applications

4、50Ω coplanar waveguide output

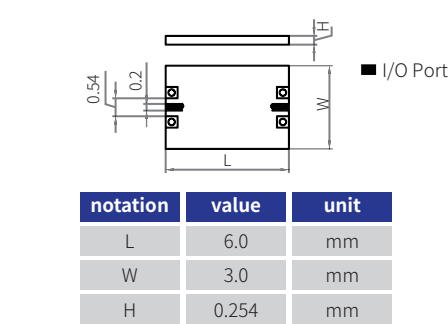
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

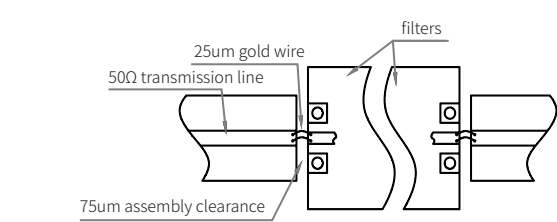
► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	13.325	-	GHz
Band Freq	13.225	-	13.425	GHz
Fc IL	-	6.0	-	dB
Passband Ripple	-	-	1.0	dB
VSWR	-	1.8	-	-
Rejection	≥50dB@12.225 GHz			
	≥50dB@14.425 GHz			

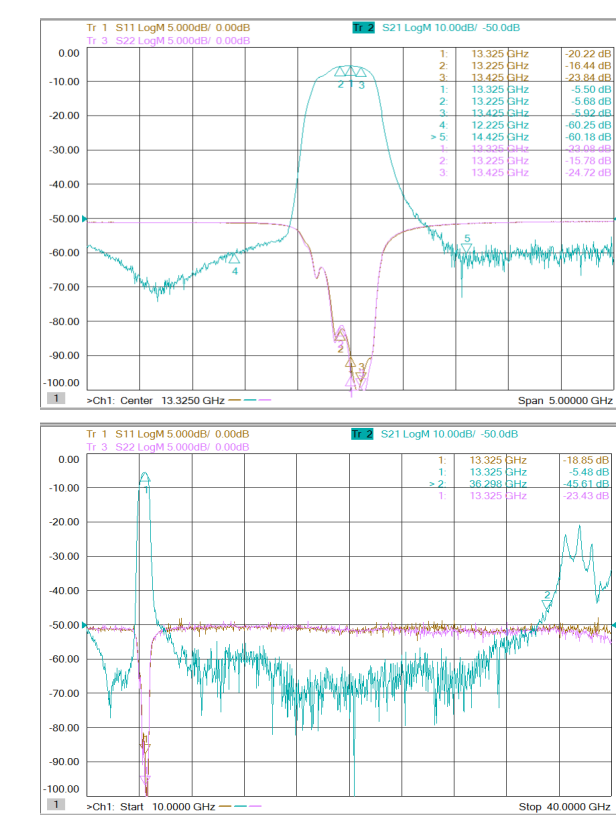
► Overall Dimensions



► Suggested Assembly Drawings

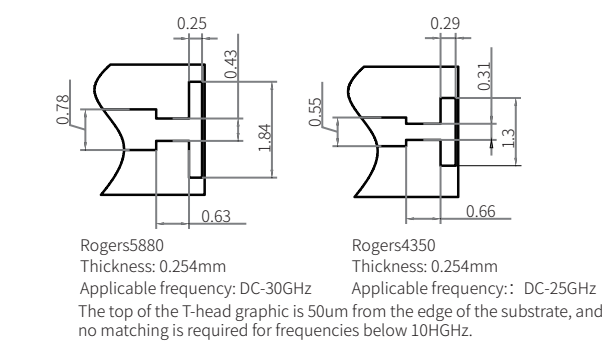


► Typical Curve



► Caveat

- 1、It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2、The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3、The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4、Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB13000-600-7

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

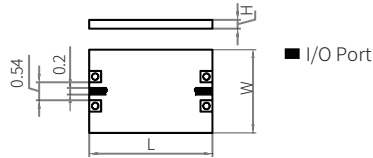
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

► Electrical Specifications

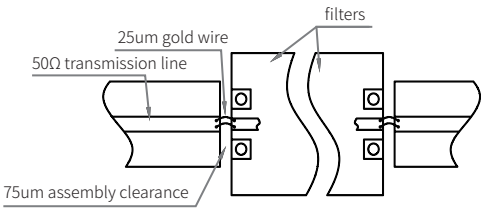
	Min	Typical	Max	
Center Freq	-	13	-	GHz
Band Freq	13.1	-	13.7	GHz
Fc IL	-	6.0	-	dB
Passband Ripple	-	-	-	dB
VSWR	-	1.8	-	-
Rejection	≥35dB@13 GHz			
	≥35dB@14 GHz			

► Overall Dimensions

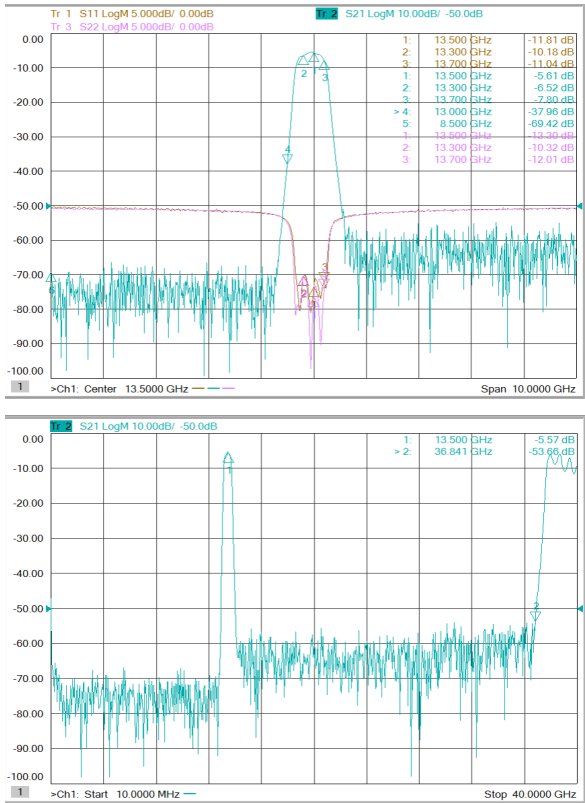


notation	value	unit
L	7.0	mm
W	3.0	mm
H	0.254	mm

► Suggested Assembly Drawings

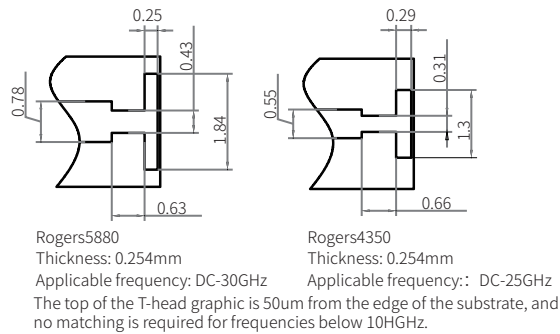


► Typical Curve



► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB14250-3500-6

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

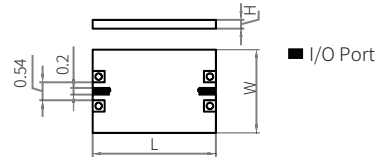
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

► Electrical Specifications

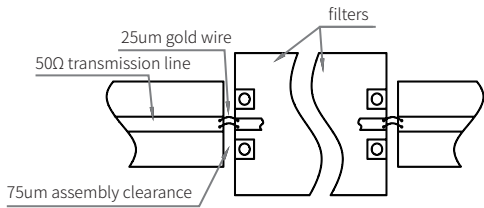
	Min	Typical	Max	
Center Freq	-	14.25	-	GHz
Band Freq	12.5	-	16	GHz
Fc IL	-	2.0	-	dB
Passband Ripple	-	-	1.0	dB
VSWR	-	1.8	-	-
Rejection	≥45dB@4.8 GHz			
	≥45dB@15.6 GHz			

► Overall Dimensions

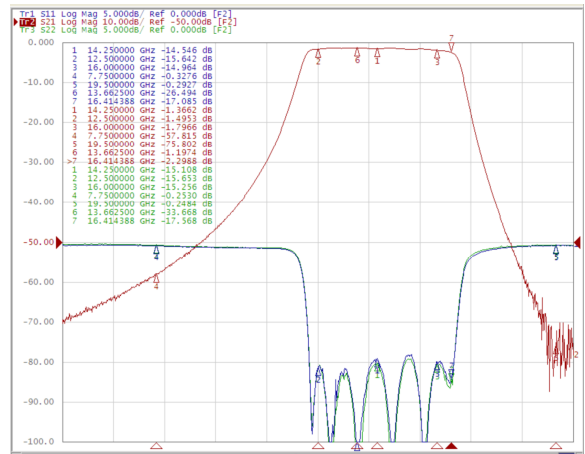


notation	value	unit
L	7.0	mm
W	2.9	mm
H	0.254	mm

► Suggested Assembly Drawings

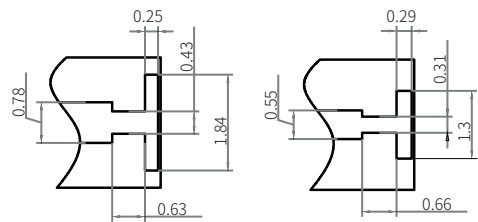


► Typical Curve



► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



Rogers5880 Thickness: 0.254mm Applicable frequency: DC-30GHz
Rogers4350 Thickness: 0.254mm Applicable frequency: DC-25GHz

The top of the T-head graphic is 50um from the edge of the substrate, and no matching is required for frequencies below 10GHz.

IYFTB14400-20-6

- Performance Characteristics
- 1、High precision micro-nanometer processing technology

2、High performance, low temperature drift, high power

3、Gold wire bonding, suitable for multi-chip integration module applications

4、50Ω coplanar waveguide output

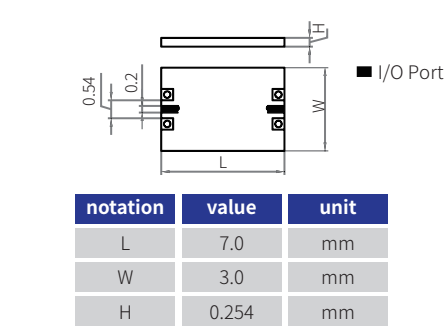
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

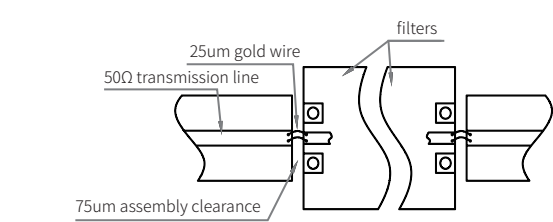
► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	14.4	-	GHz
Band Freq	14.39	-	14.41	GHz
Fc IL	-	2.0	-	dB
Passband Ripple	-	-	1.0	dB
VSWR	-	1.8	-	-
Rejection	≥50dB@10.8 GHz			
	≥40dB@18 GHz			

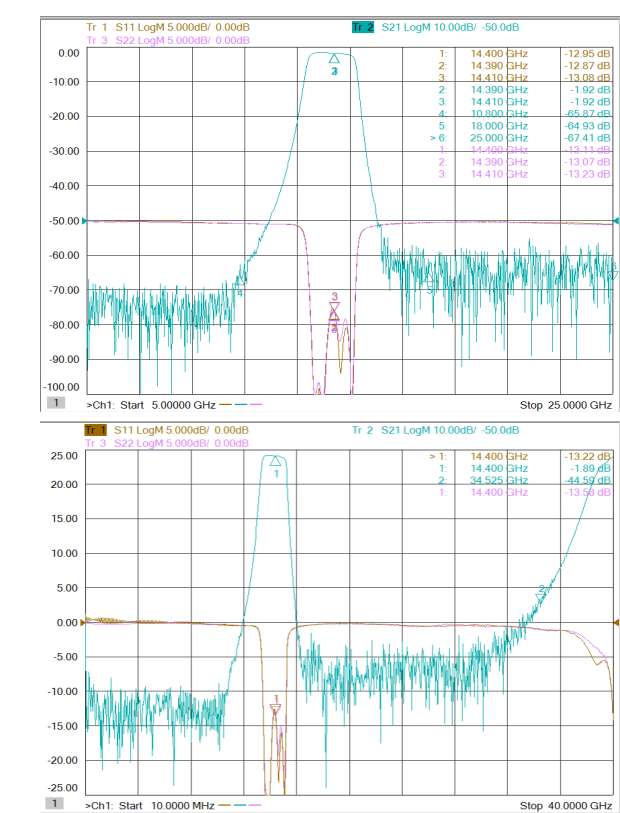
► Overall Dimensions



► Suggested Assembly Drawings



► Typical Curve



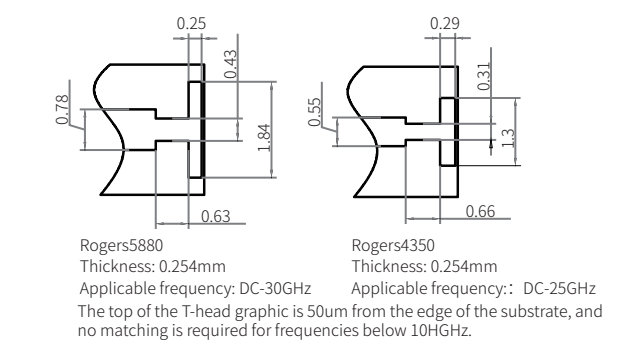
► Caveat

- 1、It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;

2、The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);

3、The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;

4、Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB14450-900-8

- Performance Characteristics
- 1、High precision micro-nanometer processing technology

2、High performance, low temperature drift, high power

3、Gold wire bonding, suitable for multi-chip integration module applications

4、50Ω coplanar waveguide output

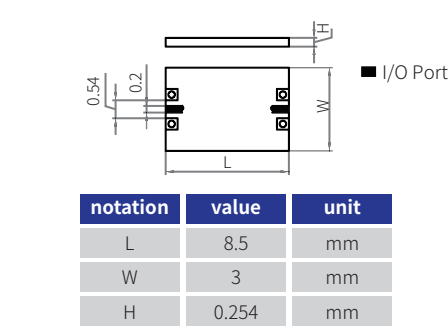
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

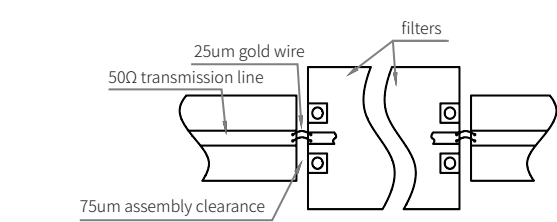
► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	14.45	-	GHz
Band Freq	14	-	14.9	GHz
Fc IL	-	3	-	dB
Passband Ripple	-	-	1.5	dB
VSWR	-	1.8	-	-
Rejection	≥50dB@12.6 GHz			
	≥50dB@15.4 GHz			

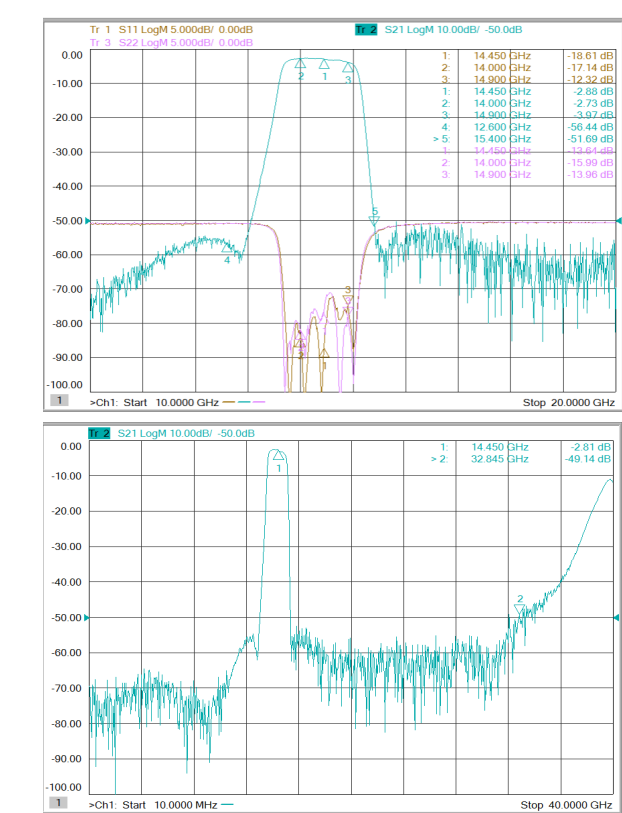
► Overall Dimensions



► Suggested Assembly Drawings



► Typical Curve



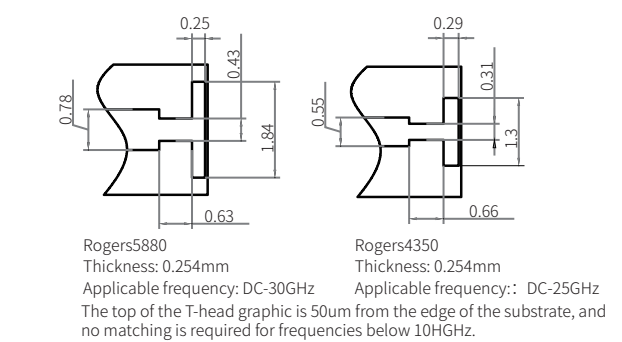
► Caveat

- 1、It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;

2、The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);

3、The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;

4、Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB14500-7000-9

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

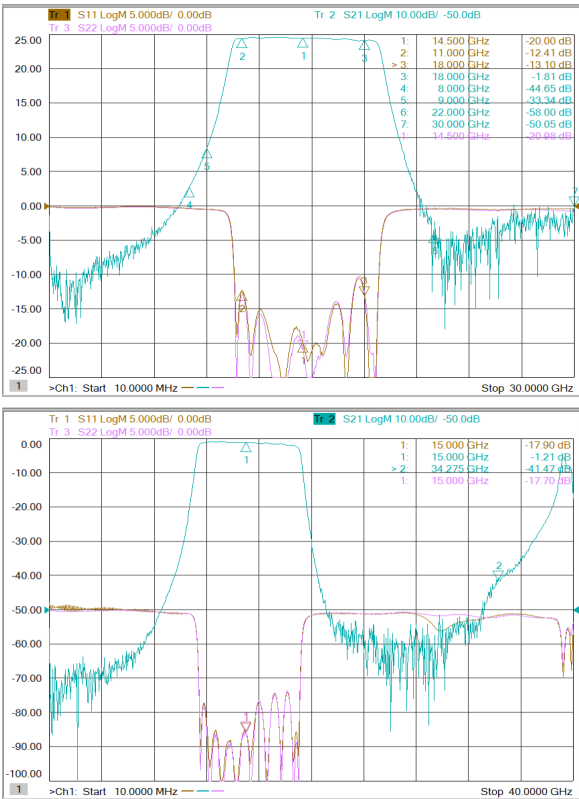
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

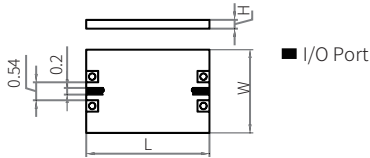
► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	14.5	-	GHz
Band Freq	11	-	18	GHz
Fc IL	-	2.0	-	dB
Passband Ripple	-	-	0.8	dB
VSWR	-	1.8	-	-
Rejection	≥30dB@8 GHz			
	≥35dB@22 GHz			

► Typical Curve

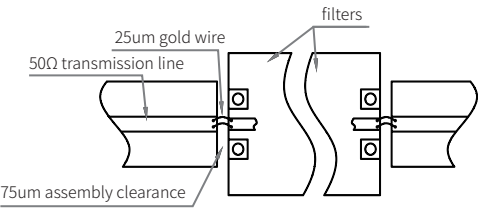


► Overall Dimensions



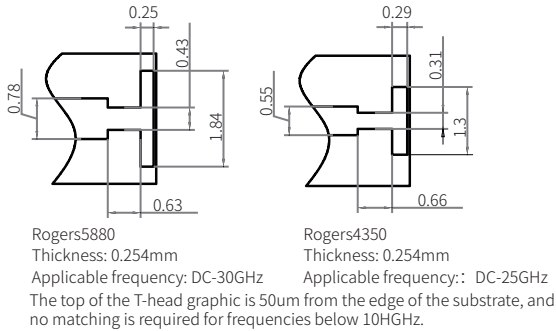
notation	value	unit
L	7.5	mm
W	2.5	mm
H	0.381	mm

► Suggested Assembly Drawings



► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB14700-1800-8

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

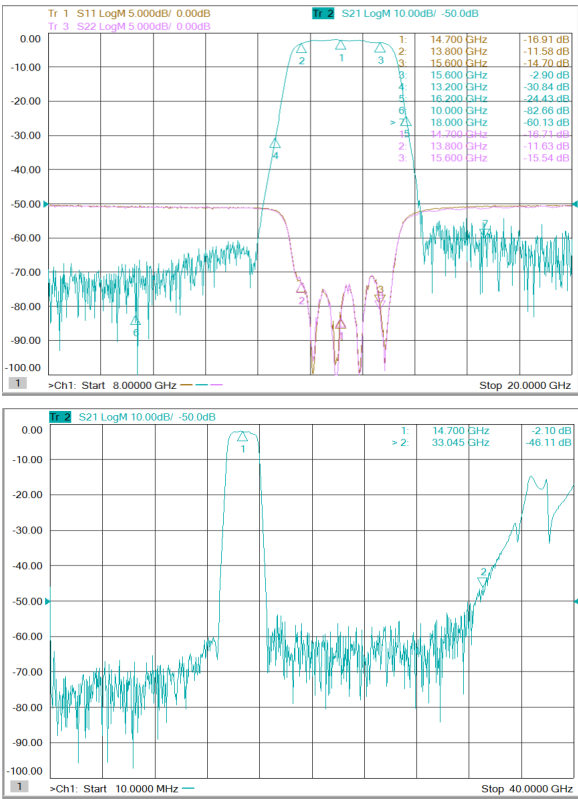
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

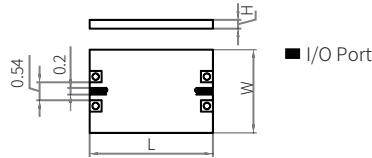
► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	14.7	-	GHz
Band Freq	13.8	-	15.6	GHz
Fc IL	-	2.5	-	dB
Passband Ripple	-	-	1.7	dB
VSWR	-	1.8	-	-
Rejection	≥20dB@13.2 GHz			
	≥20dB@16.2 GHz			

► Typical Curve

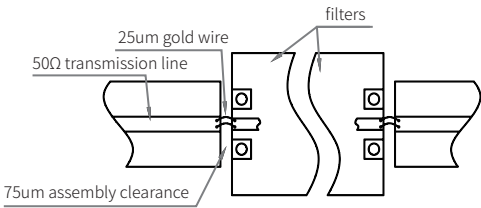


► Overall Dimensions



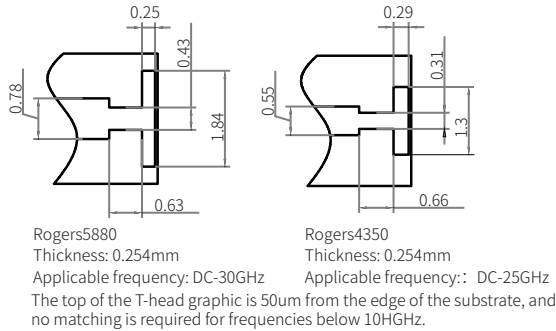
notation	value	unit
L	7.5	mm
W	3	mm
H	0.381	mm

► Suggested Assembly Drawings



► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB14750-2500-8

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

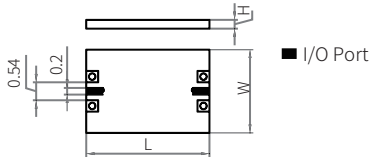
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

► Electrical Specifications

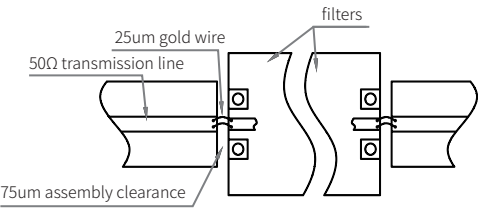
	Min	Typical	Max	
Center Freq	-	14.75	-	GHz
Band Freq	13.5	-	16	GHz
Fc IL	-	2.0	-	dB
Passband Ripple	-	-	1	dB
VSWR	-	1.8	-	-
Rejection	≥30dB@12.5 GHz			
	≥30dB@17 GHz			

► Overall Dimensions

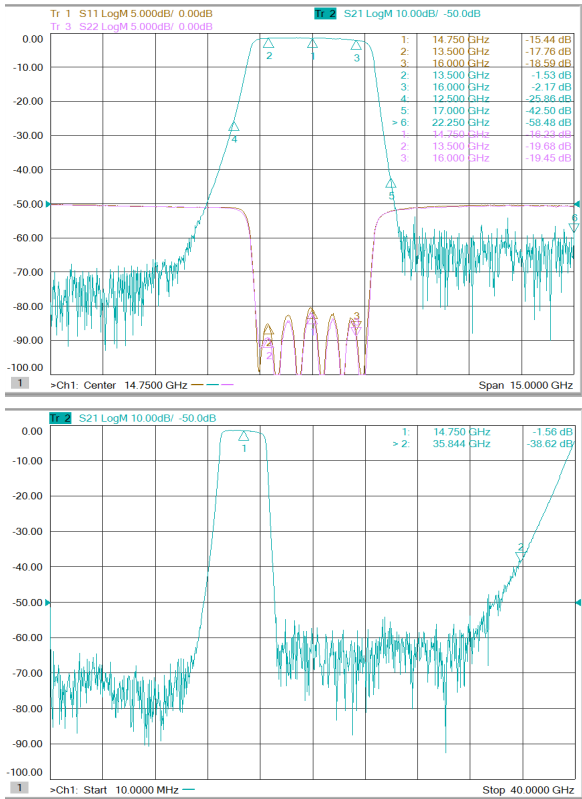


notation	value	unit
L	8.0	mm
W	3.0	mm
H	0.254	mm

► Suggested Assembly Drawings

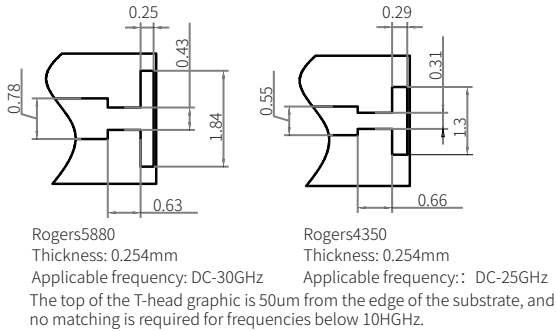


► Typical Curve



► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB14900-1050-6

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

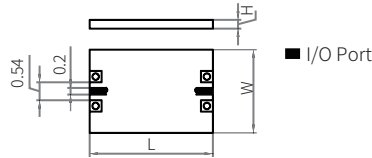
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

► Electrical Specifications

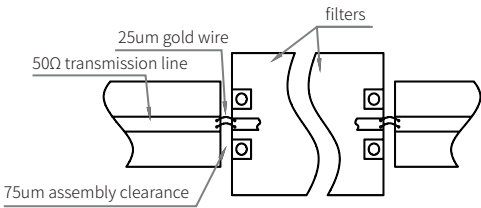
	Min	Typical	Max	
Center Freq	-	14.9	-	GHz
Band Freq	14.4	-	15.45	GHz
Fc IL	-	3.0	-	dB
Passband Ripple	-	-	1.0	dB
VSWR	-	1.8	-	-
Rejection	≥40dB@13.2 GHz			
	≥40dB@16.85 GHz			

► Overall Dimensions

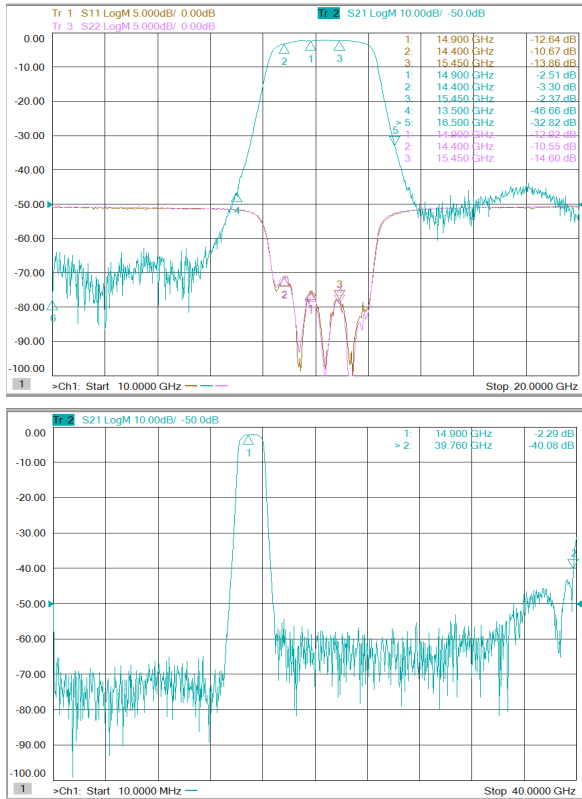


notation	value	unit
L	7	mm
W	3	mm
H	0.254	mm

► Suggested Assembly Drawings

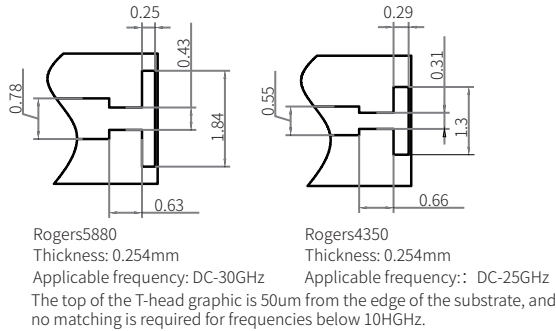


► Typical Curve



► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB15000-2000-6

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

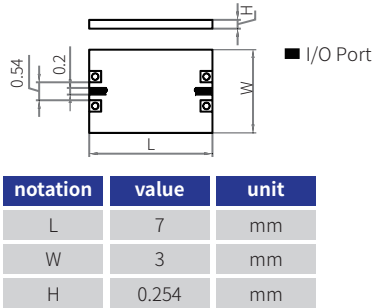
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

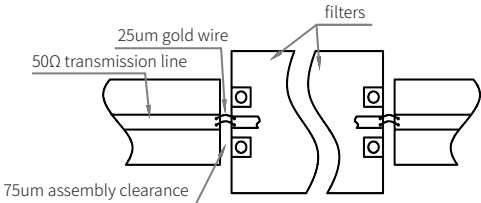
► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	15	-	GHz
Band Freq	14	-	16	GHz
Fc IL	-	2.5	-	dB
Passband Ripple	-	-	-	dB
VSWR	-	1.8	-	-
Rejection	≥60dB@7.5 GHz			
	≥50dB@22.5 GHz			

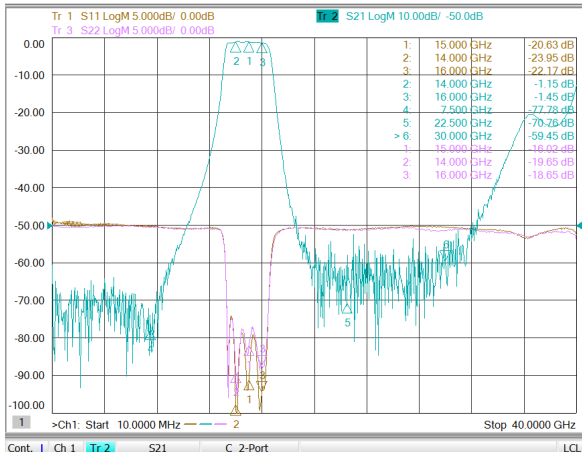
► Overall Dimensions



► Suggested Assembly Drawings

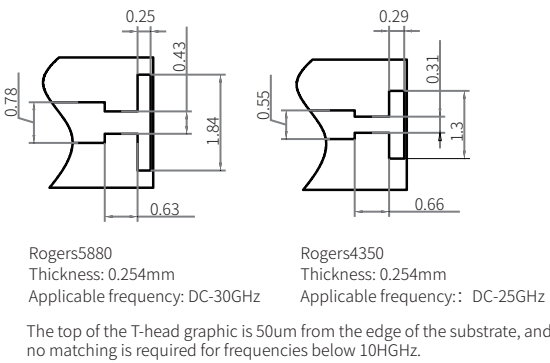


► Typical Curve



► Caveat

- 1、It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2、The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3、The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4、Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB15000-2500-7

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

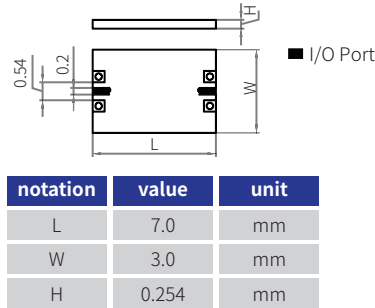
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

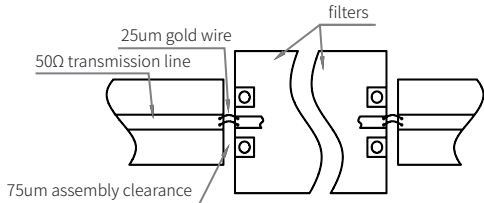
► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	15	-	GHz
Band Freq	13.75	-	16.25	GHz
Fc IL	-	2.0	-	dB
Passband Ripple	-	-	1.0	dB
VSWR	-	1.8	-	-
Rejection	≥50dB@11GHz			
	≥45dB@19 GHz			

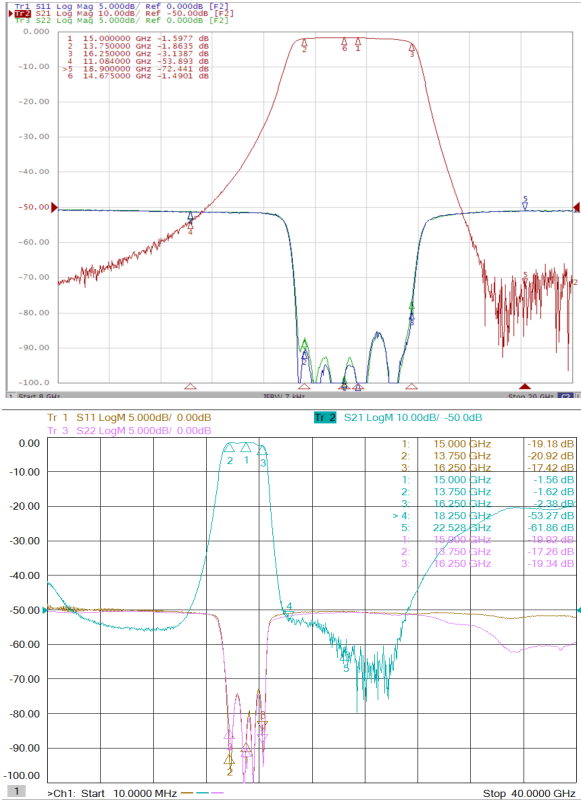
► Overall Dimensions



► Suggested Assembly Drawings

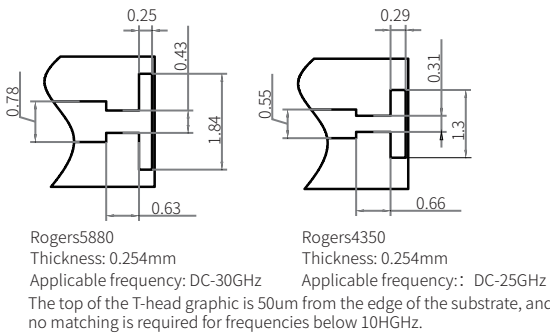


► Typical Curve



► Caveat

- 1、It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2、The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3、The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4、Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB15000-6500-9

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

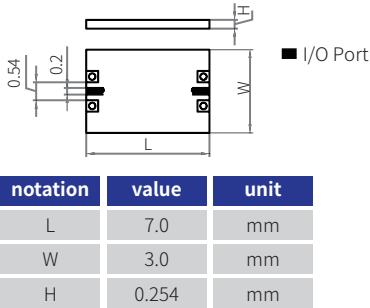
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

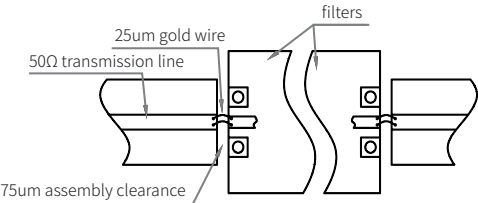
► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	15	-	GHz
Band Freq	11.75	-	18.25	GHz
Fc IL	-	1.5	-	dB
Passband Ripple	-	-	1.0	dB
VSWR	-	1.8	-	-
Rejection	≥45dB@DC~8.2 GHz			
	≥60dB@21.5~28 GHz			

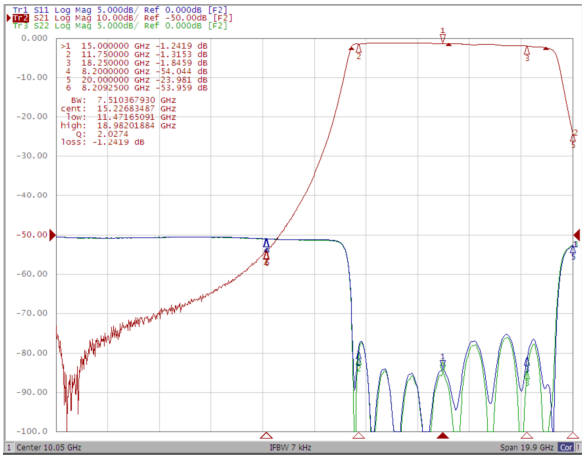
► Overall Dimensions



► Suggested Assembly Drawings

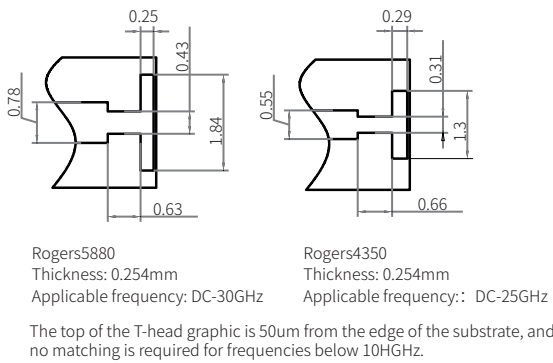


► Typical Curve



► Caveat

- 1、It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2、The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3、The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4、Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB15500-3400-8

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

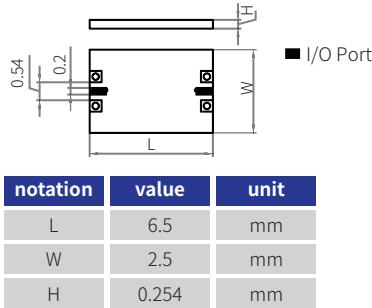
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

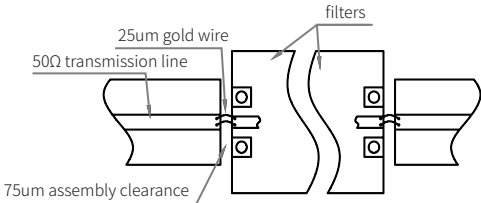
► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	15.5	-	GHz
Band Freq	13.8	-	17.2	GHz
Fc IL	-	2.5	-	dB
Passband Ripple	-	-	1	dB
VSWR	-	1.8	-	-
Rejection	≥60dB@9 GHz			
	≥60dB@21 GHz			

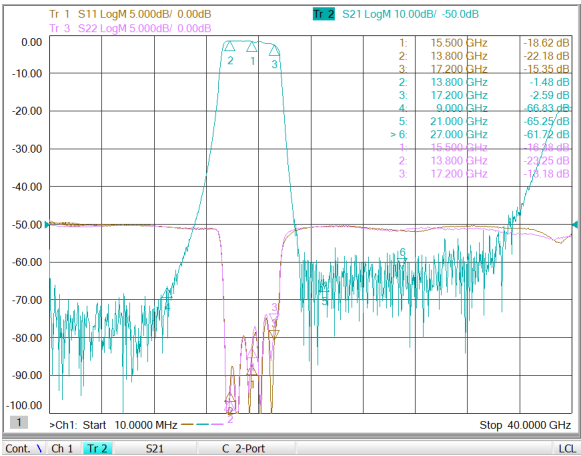
► Overall Dimensions



► Suggested Assembly Drawings

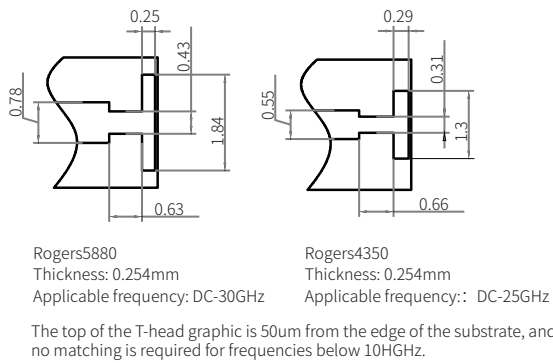


► Typical Curve



► Caveat

- 1、It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2、The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3、The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4、Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB15750-4500-10

- Performance Characteristics
- 1、High precision micro-nanometer processing technology
 - 2、High performance, low temperature drift, high power
 - 3、Gold wire bonding, suitable for multi-chip integration module applications
 - 4、50Ω coplanar waveguide output

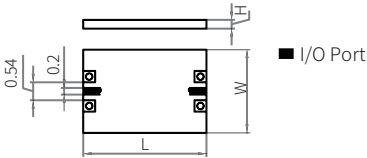
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

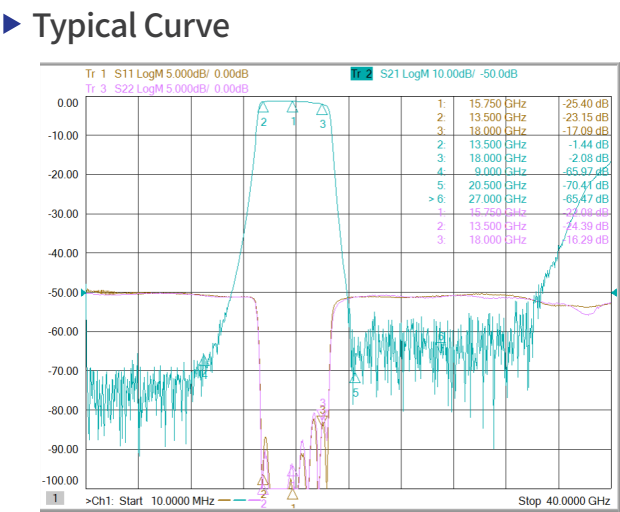
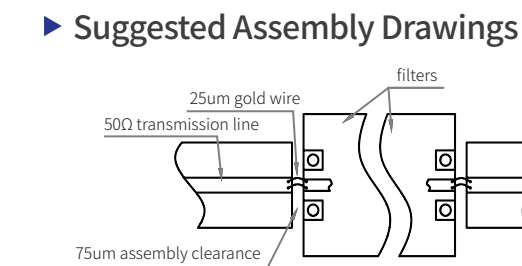
► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	15.75	-	GHz
Band Freq	13.5	-	18	GHz
Fc IL	-	2.0	-	dB
Passband Ripple	-	-	1.0	dB
VSWR	-	1.8	-	-
Rejection	≥55dB@9GHz			
	≥50dB@20.5 GHz			

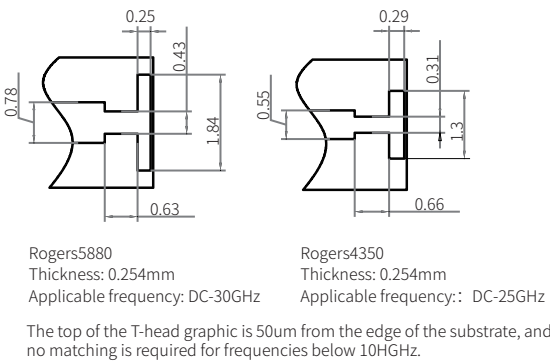
► Overall Dimensions



notation	value	unit
L	7.0	mm
W	3.0	mm
H	0.254	mm



- Caveat
- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
 - 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
 - 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
 - 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB16000-4000-10

- Performance Characteristics
- 1、High precision micro-nanometer processing technology
 - 2、High performance, low temperature drift, high power
 - 3、Gold wire bonding, suitable for multi-chip integration module applications
 - 4、50Ω coplanar waveguide output

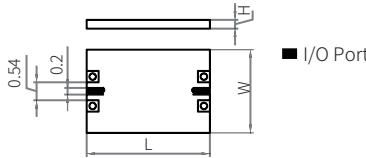
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

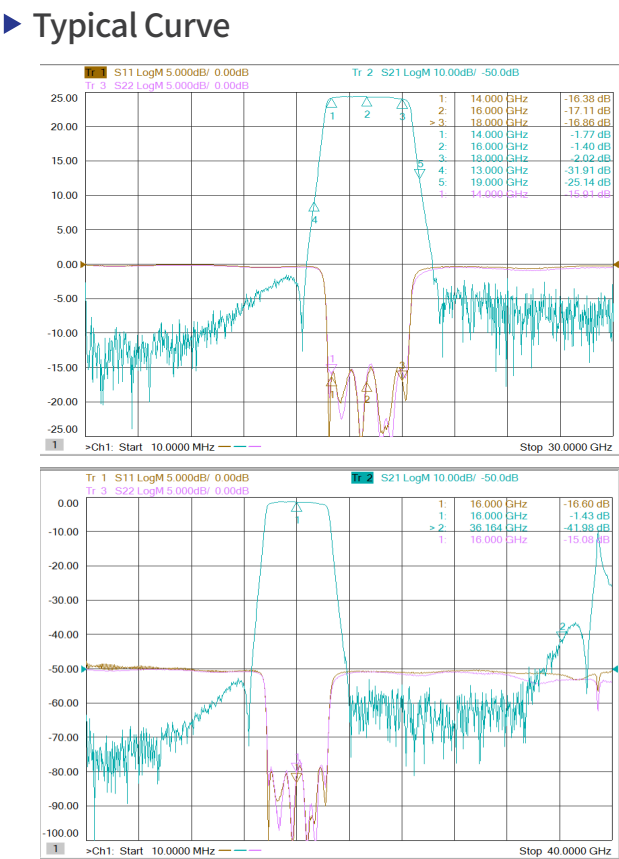
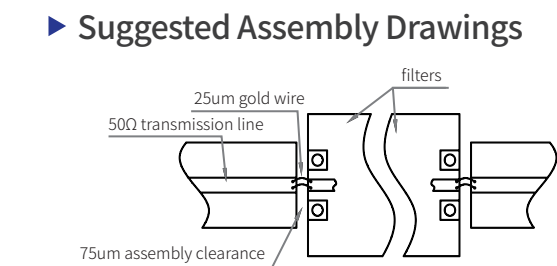
► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	16.0	-	GHz
Band Freq	14	-	18	GHz
Fc IL	-	2.0	-	dB
Passband Ripple	-	-	1.0	dB
VSWR	-	1.8	-	-
Rejection	≥20dB@13 GHz			
	≥20dB@19 GHz			

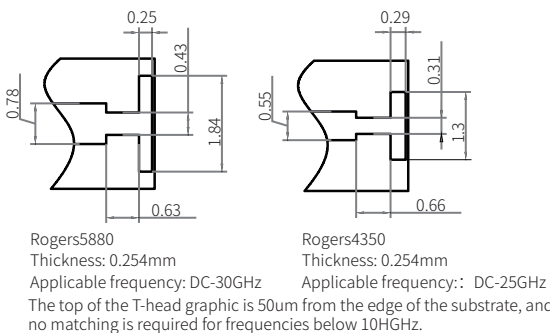
► Overall Dimensions



notation	value	unit
L	8.0	mm
W	2.5	mm
H	0.254	mm



- Caveat
- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
 - 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
 - 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
 - 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB16155-980-8

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

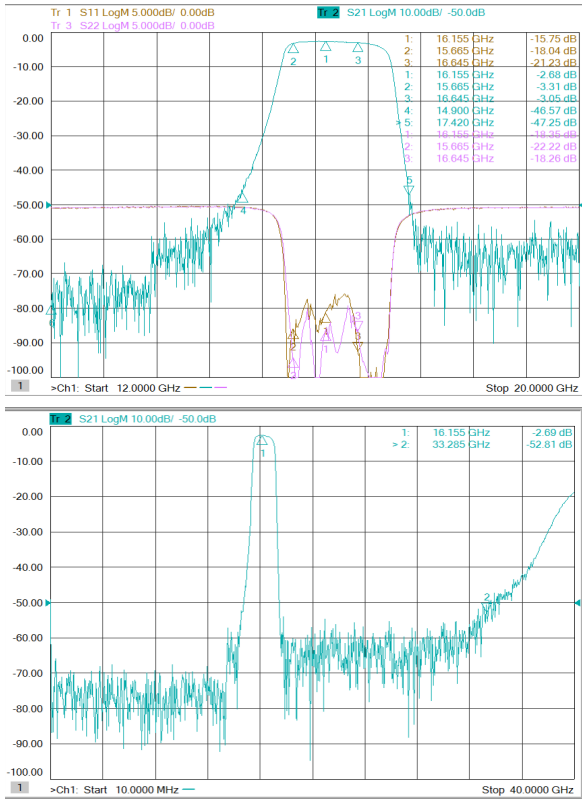
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

► Electrical Specifications

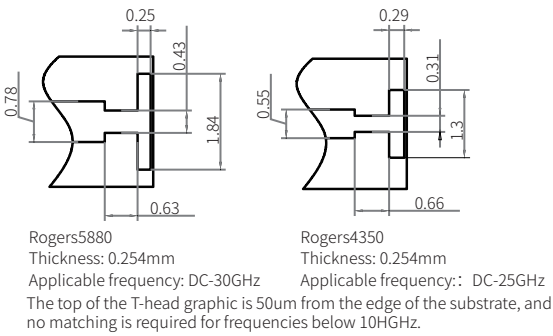
	Min	Typical	Max	
Center Freq	-	16.155	-	GHz
Band Freq	15.71	-	16.69	GHz
Fc IL	-	3.0	-	dB
Passband Ripple	-	-	1.5	dB
VSWR	-	1.8	-	-
Rejection	≥40dB@14.9 GHz			
	≥40dB@17.4 GHz			

► Typical Curve

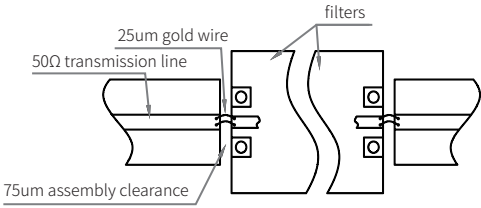


► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



► Suggested Assembly Drawings



IYFTB16500-3500-8

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

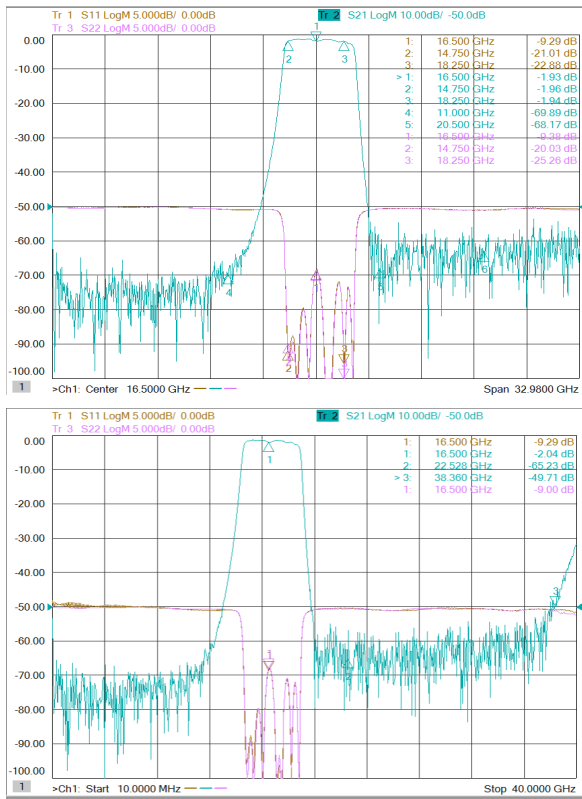
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

► Electrical Specifications

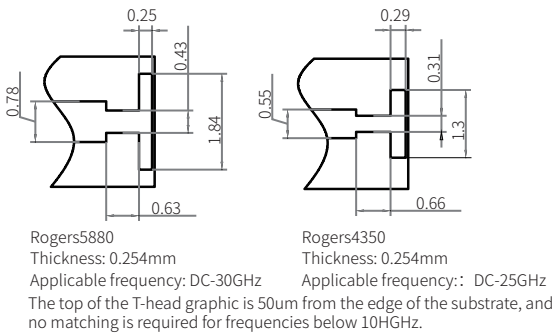
	Min	Typical	Max	
Center Freq	-	16.5	-	GHz
Band Freq	14.75	-	18.25	GHz
Fc IL	-	2.0	-	dB
Passband Ripple	-	-	1.0	dB
VSWR	-	1.8	-	-
Rejection	≥50dB@11GHz			
	≥50dB@20.5 GHz			

► Typical Curve

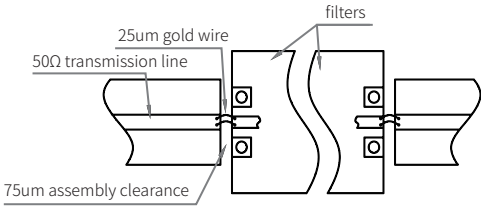


► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



► Suggested Assembly Drawings



IYFTB16500-7000-12

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

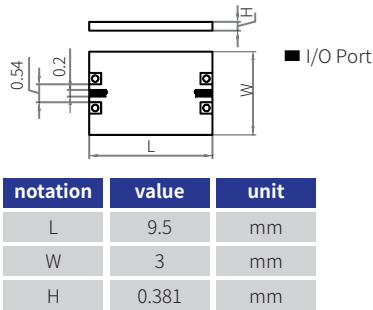
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

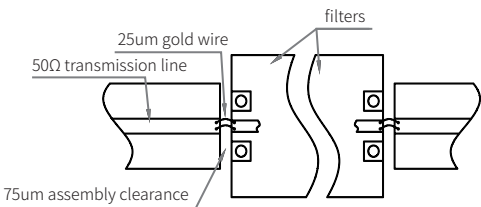
► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	16.5	-	GHz
Band Freq	13	-	20	GHz
Fc IL	-	2.0	-	dB
Passband Ripple	-	-	1.0	dB
VSWR	-	1.8	-	-
Rejection	≥50dB@10GHz			
	≥50dB@22.3 GHz			

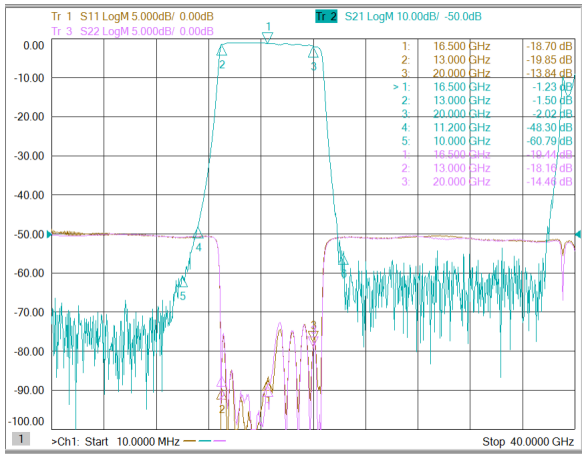
► Overall Dimensions



► Suggested Assembly Drawings

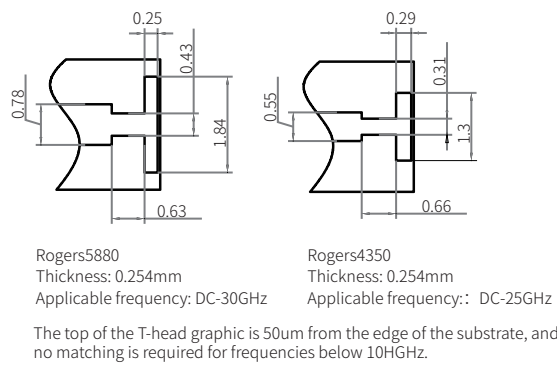


► Typical Curve



► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB16650-4800-8

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

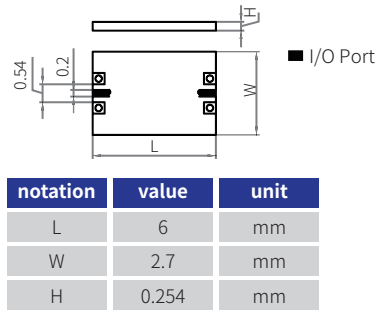
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

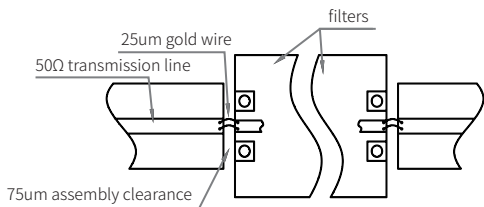
► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	16.65	-	GHz
Band Freq	14.3	-	19.1	GHz
Fc IL	-	2.0	-	dB
Passband Ripple	-	-	1.0	dB
VSWR	-	1.8	-	-
Rejection	≥40dB@11GHz			
	≥40dB@20.5 GHz			

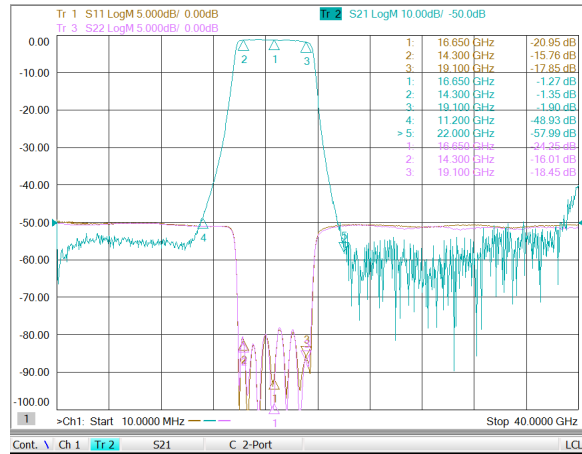
► Overall Dimensions



► Suggested Assembly Drawings

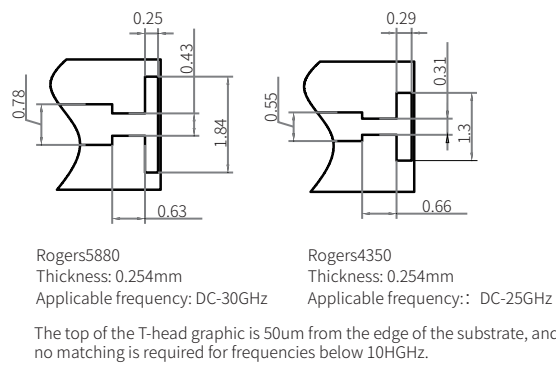


► Typical Curve



► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB16975-2450-9

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

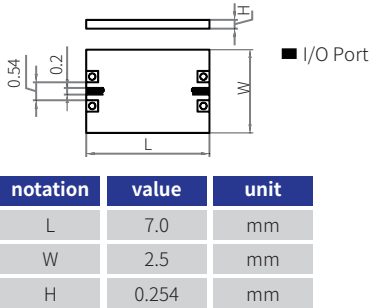
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

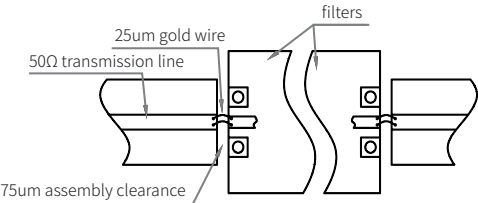
► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	16.975	-	GHz
Band Freq	15.75	-	18.2	GHz
Fc IL	-	2.0	-	dB
Passband Ripple	-	-	1.0	dB
VSWR	-	1.8	-	-
Rejection	≥40dB@13GHz			
	≥50dB@20 GHz			

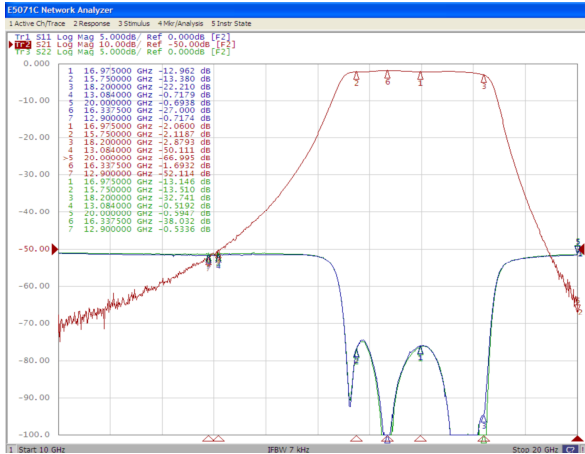
► Overall Dimensions



► Suggested Assembly Drawings

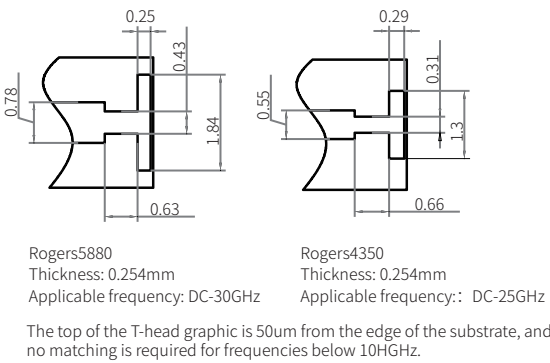


► Typical Curve



► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB17250-4500-8

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

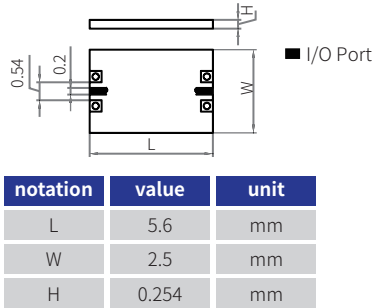
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

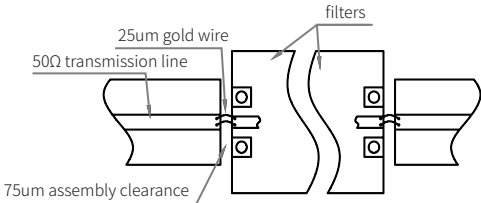
► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	17.25	-	GHz
Band Freq	15	-	19.5	GHz
Fc IL	-	2.0	-	dB
Passband Ripple	-	-	1.0	dB
VSWR	-	1.8	-	-
Rejection	≥40dB@12GHz			
	≥40dB@23GHz			

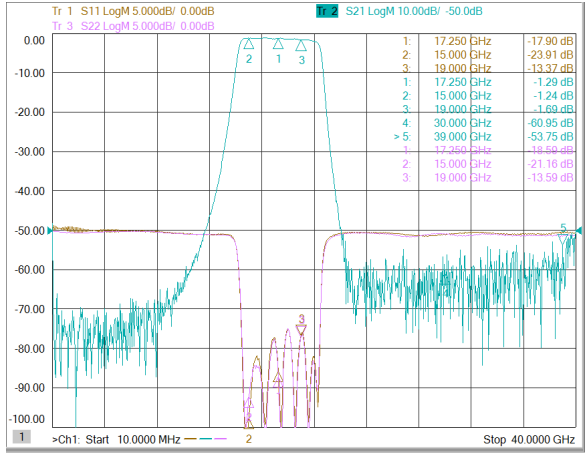
► Overall Dimensions



► Suggested Assembly Drawings

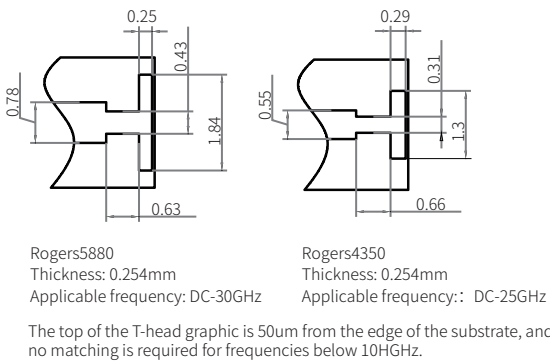


► Typical Curve



► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB17350-2700-8

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

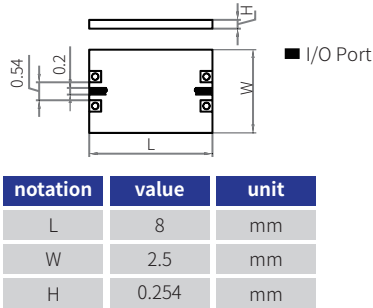
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

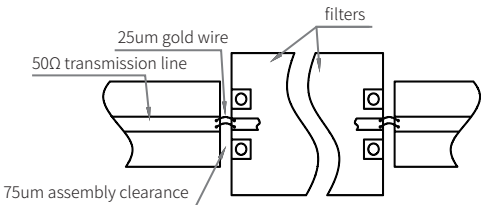
► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	17.35	-	GHz
Band Freq	16	-	18.7	GHz
Fc IL	-	2.5	-	dB
Passband Ripple	-	-	1.0	dB
VSWR	-	1.8	-	-
Rejection	≥35dB@15GHz			
	≥35dB@19.5GHz			

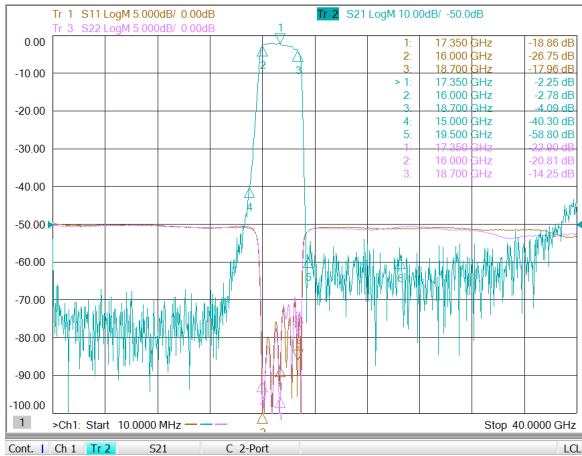
► Overall Dimensions



► Suggested Assembly Drawings

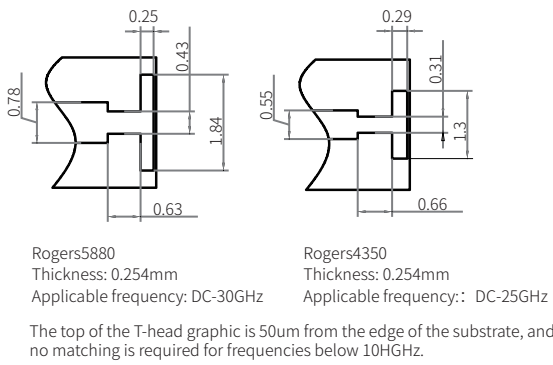


► Typical Curve



► Caveat

- 1、It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2、The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3、The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4、Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB17875-4250-8

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

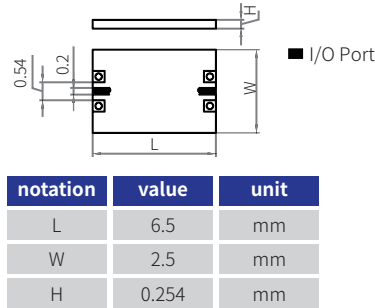
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

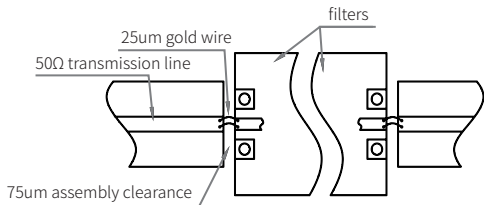
► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	17.875	-	GHz
Band Freq	15.75	-	20	GHz
Fc IL	-	2.0	-	dB
Passband Ripple	-	-	1.0	dB
VSWR	-	1.8	-	-
Rejection	≥40dB@12.5GHz			
	≥40dB@23.5GHz			

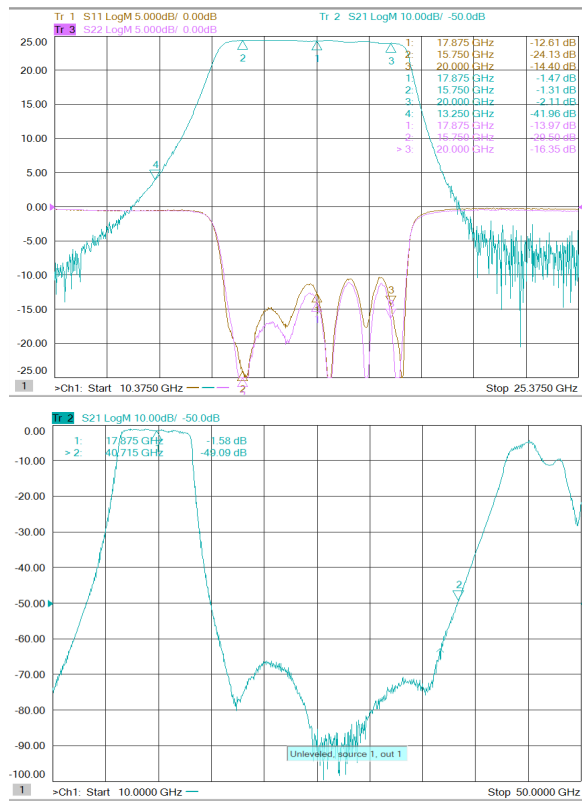
► Overall Dimensions



► Suggested Assembly Drawings

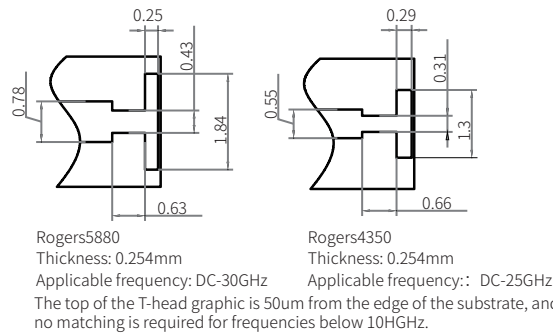


► Typical Curve



► Caveat

- 1、It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2、The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3、The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4、Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB18000-4000-8

► Performance Characteristics

1. High precision micro-nanometer processing technology
2. High performance, low temperature drift, high power
3. Gold wire bonding, suitable for multi-chip integration module applications
4. 50Ω coplanar waveguide output

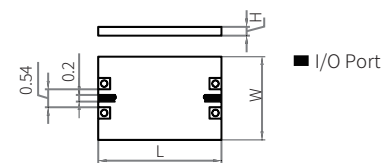
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

► Electrical Specifications

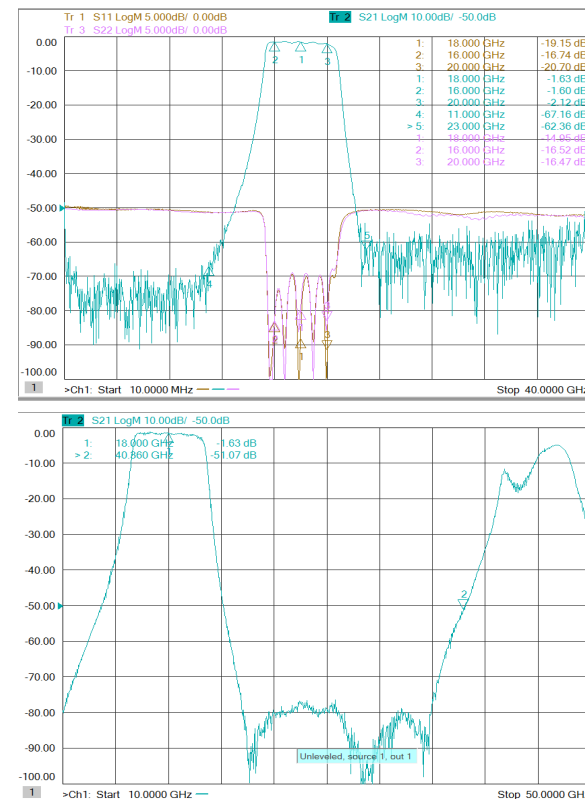
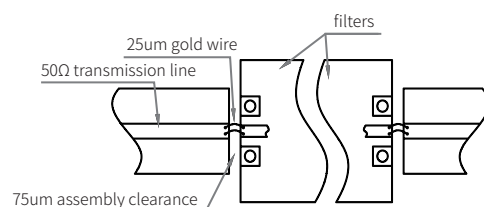
	Min	Typical	Max	
Center Freq	-	18	-	GHz
Band Freq	16		20	GHz
Fc IL	-	2	-	dB
Passband Ripple	-	-	1.5	dB
VSWR	-	1.8		-
Rejection	≥45dB@11 GHz			
	≥45dB@23 GHz			

► Overall Dimensions



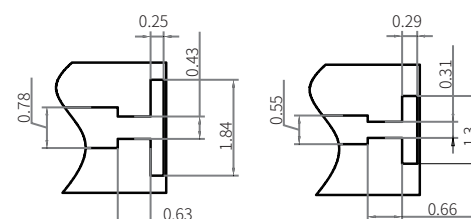
notation	value	unit
L	6	mm
W	2.5	mm
H	0.254	mm

► Suggested Assembly Drawings



► **Caveat**

1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion ($6.7\text{ppm}/^{\circ}\text{C}$) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier $\geq 0.2\text{mm}$;
4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



Rogers5880	Rogers4350
Thickness: 0.254mm	Thickness: 0.254mm
Applicable frequency: DC-30GHz	Applicable frequency: DC-25GHz
The top of the T-head graphic is 50um from the edge of the substrate, and no matching is required for frequencies below 10GHz.	

IYFTB18000-4400-9

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

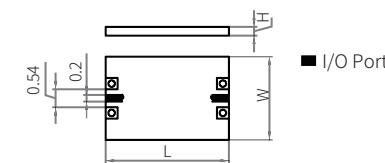
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

► Electrical Specifications

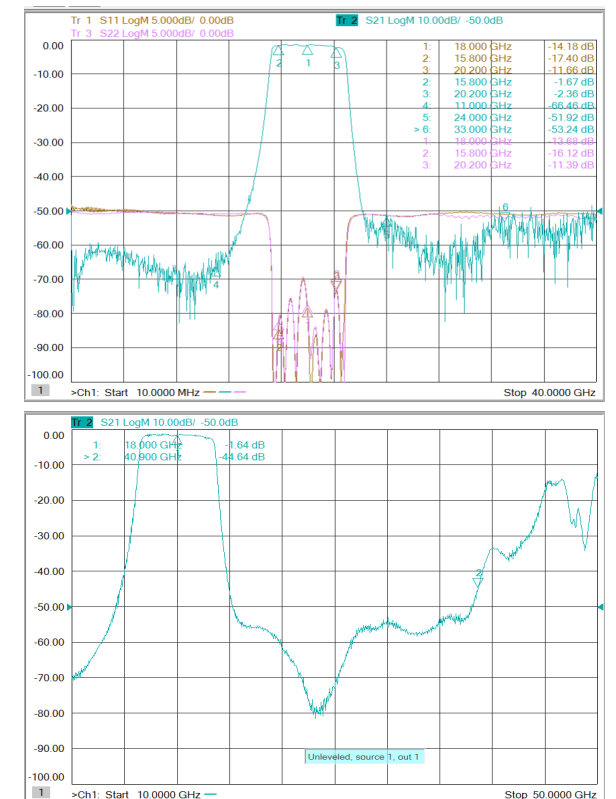
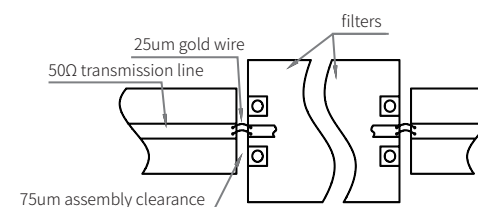
	Min	Typical	Max	
Center Freq	-	18	-	GHz
Band Freq	15.8	-	20.2	GHz
Fc IL	-	2.0	-	dB
Passband Ripple	-	-	1.2	dB
VSWR	-	1.8	-	-
Rejection	≥50dB@11 GHz			
	≥50dB@24 GHz			

► Overall Dimensions



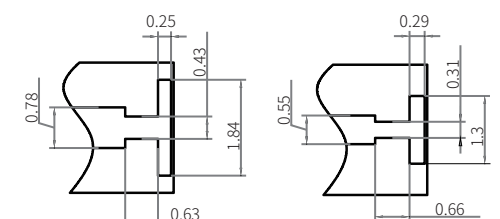
notation	value	unit
L	8.0	mm
W	2.5	mm
H	0.254	mm

► Suggested Assembly Drawings



► **Caveat**

1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier $\geq 0.2\text{mm}$;
4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



Rogers5880	Rogers4350
Thickness: 0.254mm	Thickness: 0.254mm
Applicable frequency: DC-30GHz	Applicable frequency: DC-25GHz
The top of the T-head graphic is 50um from the edge of the substrate, and no matching is required for frequencies below 10GHz.	

IYFTB18500-3400-8

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

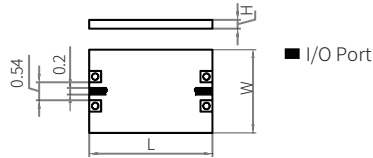
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

► Electrical Specifications

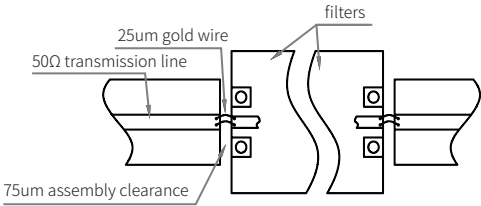
	Min	Typical	Max	
Center Freq	-	18.5	-	GHz
Band Freq	16.8	-	20.2	GHz
Fc IL	-	2.0	-	dB
Passband Ripple	-	-	1	dB
VSWR	-	1.8	-	-
Rejection	≥60dB@12 GHz			
	≥60dB@25 GHz			

► Overall Dimensions

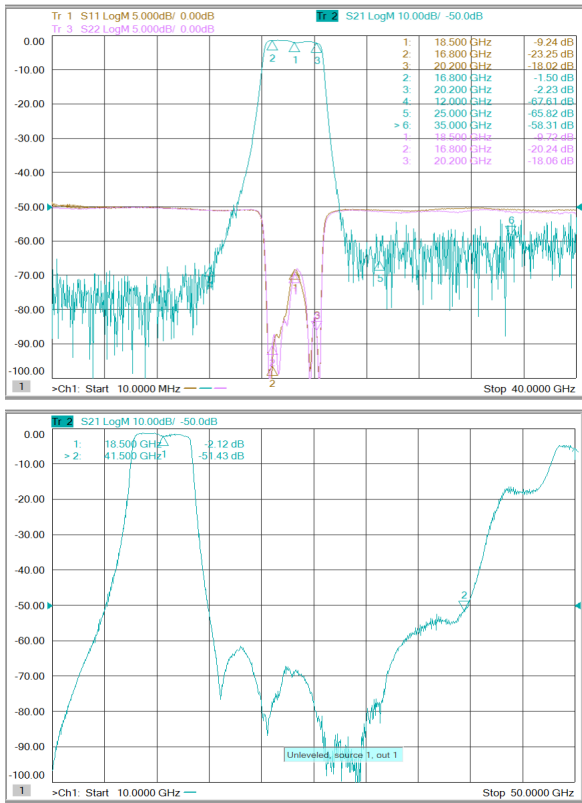


notation	value	unit
L	6.5	mm
W	2.2	mm
H	0.254	mm

► Suggested Assembly Drawings

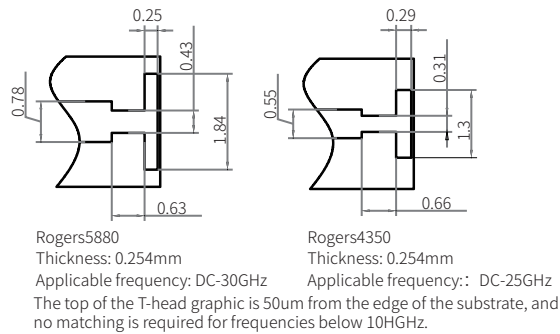


► Typical Curve



► Caveat

- 1、It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2、The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3、The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4、Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB19000-2300-8

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

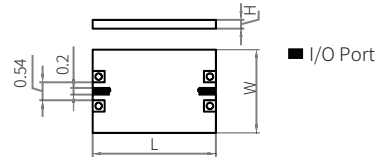
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

► Electrical Specifications

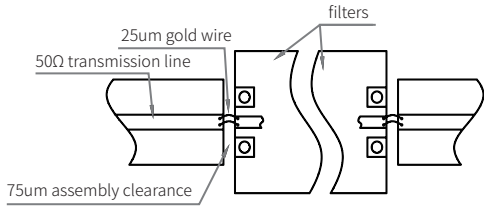
	Min	Typical	Max	
Center Freq	-	19	-	GHz
Band Freq	17.85	-	20.15	GHz
Fc IL	-	3	-	dB
Passband Ripple	-	-	1.5	dB
VSWR	-	1.8	-	-
Rejection	≥46dB@15 GHz			
	≥46dB@23 GHz			

► Overall Dimensions

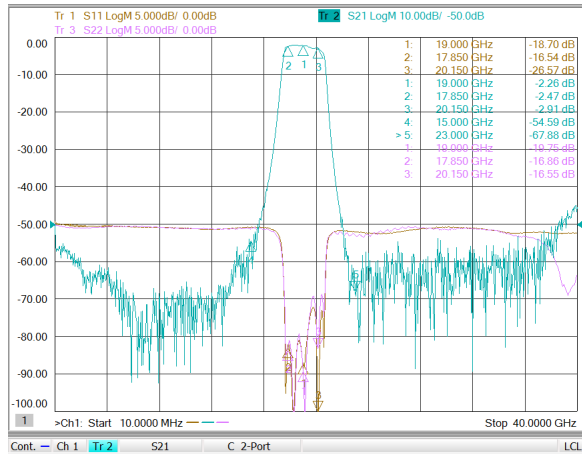


notation	value	unit
L	7	mm
W	2.5	mm
H	0.254	mm

► Suggested Assembly Drawings

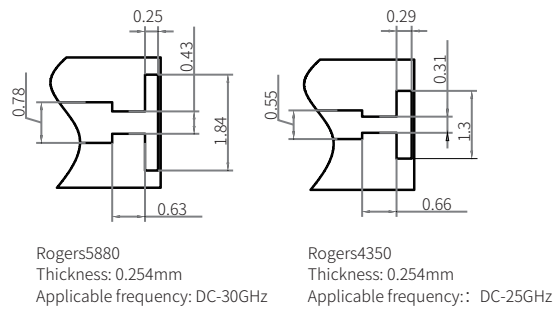


► Typical Curve



► Caveat

- 1、It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2、The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3、The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4、Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



The top of the T-head graphic is 50um from the edge of the substrate, and no matching is required for frequencies below 10HGHZ.

IYFTB20328.4-20-4

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

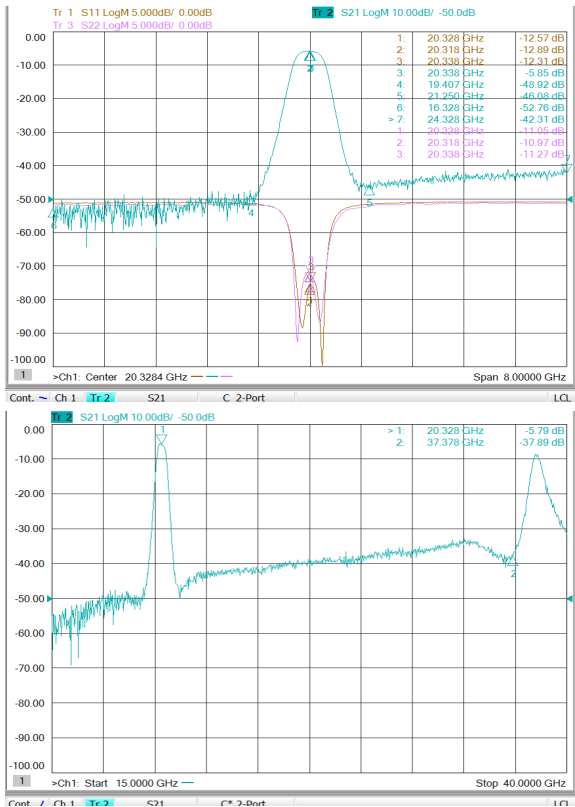
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

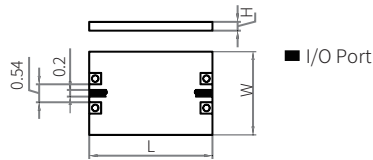
► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	20.3284	-	GHz
Band Freq	20.3184	-	20.3384	GHz
Fc IL	-	6	-	dB
Passband Ripple	-	-	0.5	dB
VSWR	-	1.8	-	-
Rejection	≥40dB@19.4068 GHz			
	≥40dB@21.25 GHz			

► Typical Curve



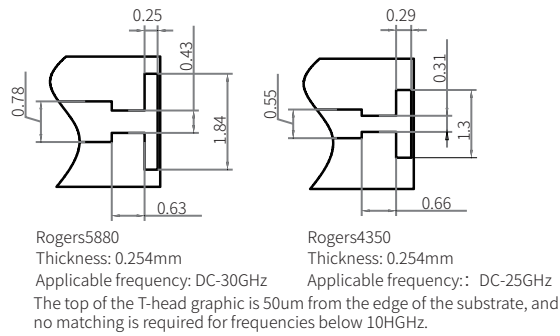
► Overall Dimensions



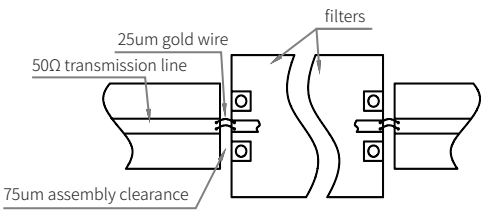
notation	value	unit
L	3.8	mm
W	3	mm
H	0.254	mm

► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



► Suggested Assembly Drawings



IYFTB20500-7000-11

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

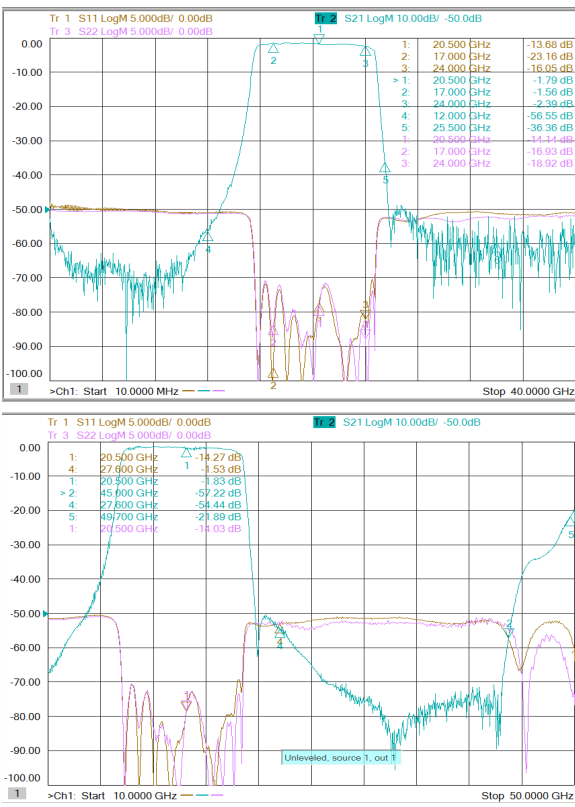
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

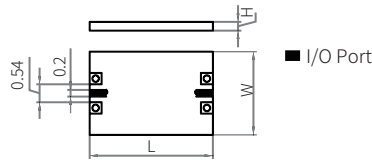
► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	20.5	-	GHz
Band Freq	17	-	24	GHz
Fc IL	-	2.0	-	dB
Passband Ripple	-	-	1.5	dB
VSWR	-	1.8	-	-
Rejection	≥45dB@12GHz			
	≥35dB@25.5GHz			

► Typical Curve



► Overall Dimensions

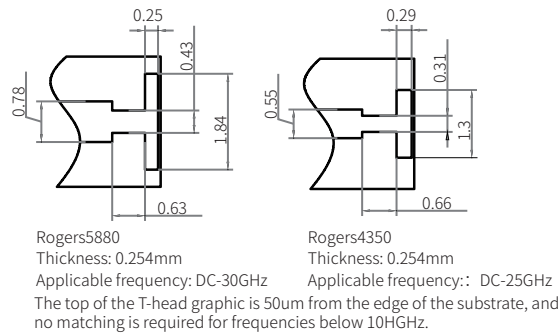
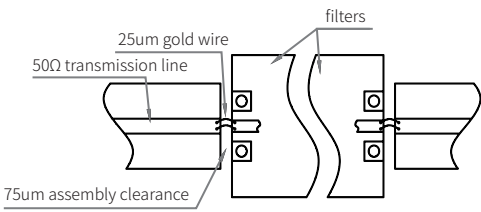


notation	value	unit
L	7.0	mm
W	2.0	mm
H	0.254	mm

► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:

► Suggested Assembly Drawings



IYFTB20750-6500-9

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

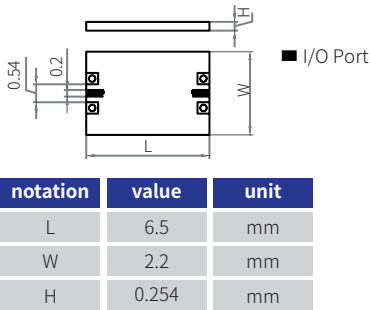
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

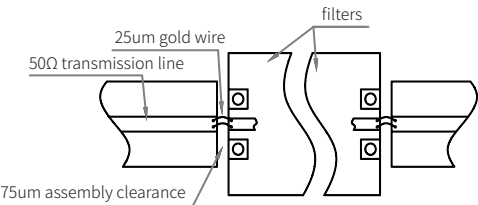
► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	20.75	-	GHz
Band Freq	17.5	-	24	GHz
Fc IL	-	2.0	-	dB
Passband Ripple	-	-	1.5	dB
VSWR	-	1.8	-	-
Rejection	≥40dB@12GHz			
	≥40dB@27GHz			

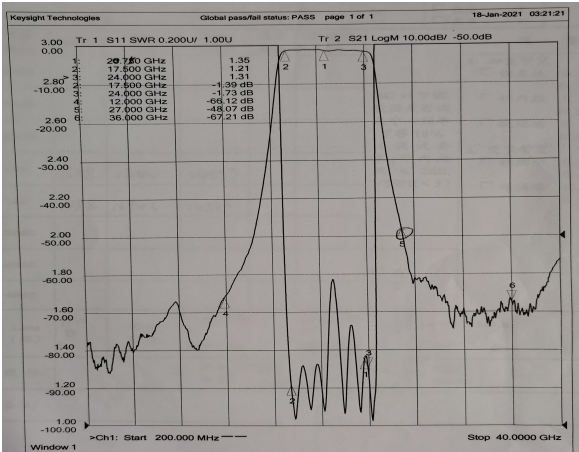
► Overall Dimensions



► Suggested Assembly Drawings

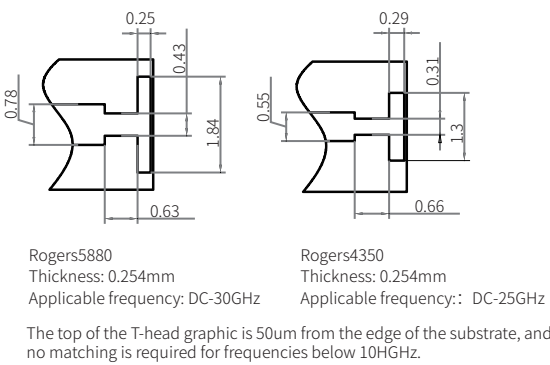


► Typical Curve



► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB20828.4-20-4

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

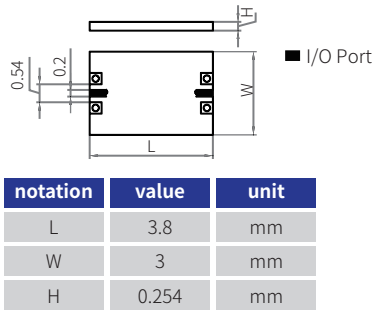
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

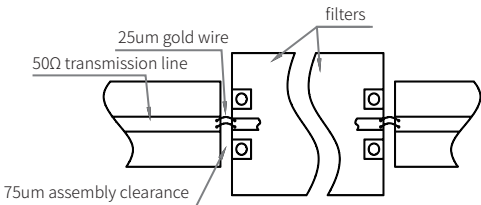
► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	20.8284	-	GHz
Band Freq	20.8184	-	20.8384	GHz
Fc IL	-	7.0	-	dB
Passband Ripple	-	-	0.5	dB
VSWR	-	1.8	-	-
Rejection	≥40dB@19.9068 GHz			
	≥40dB@21.75 GHz			

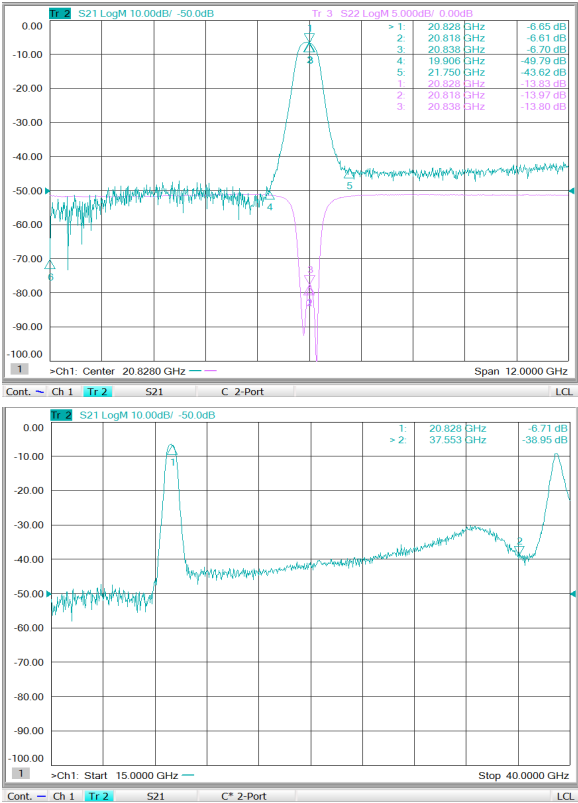
► Overall Dimensions



► Suggested Assembly Drawings

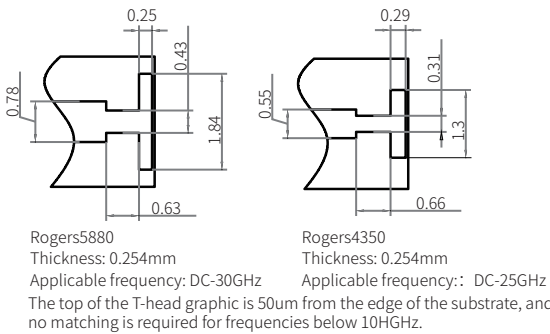


► Typical Curve



► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB21900-1600-6

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

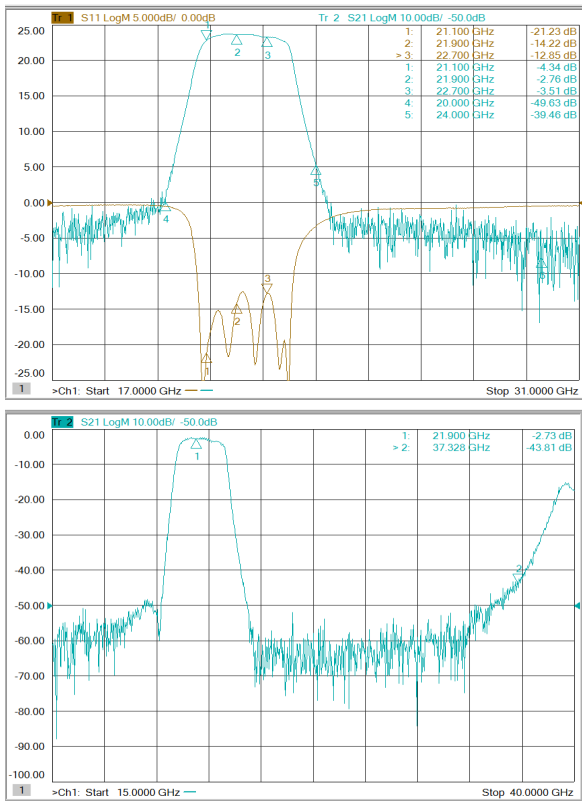
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

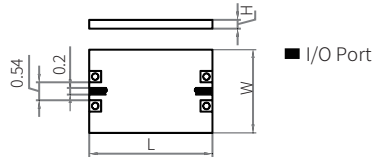
► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	21.9	-	GHz
Band Freq	21.1	-	22.7	GHz
Fc IL	-	3.0	-	dB
Passband Ripple	-	-	1.0	dB
VSWR	-	1.8	-	-
Rejection	≥35dB@20GHz			
	≥35dB@24GHz			

► Typical Curve



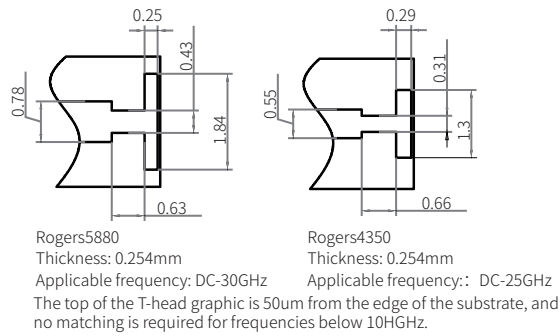
► Overall Dimensions



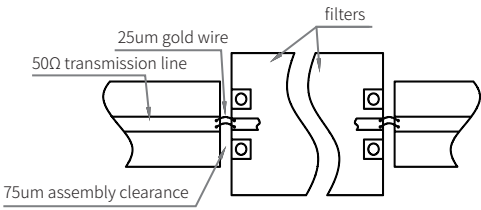
notation	value	unit
L	9.5	mm
W	3.2	mm
H	0.254	mm

► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



► Suggested Assembly Drawings



IYFTB22000-4400-9

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

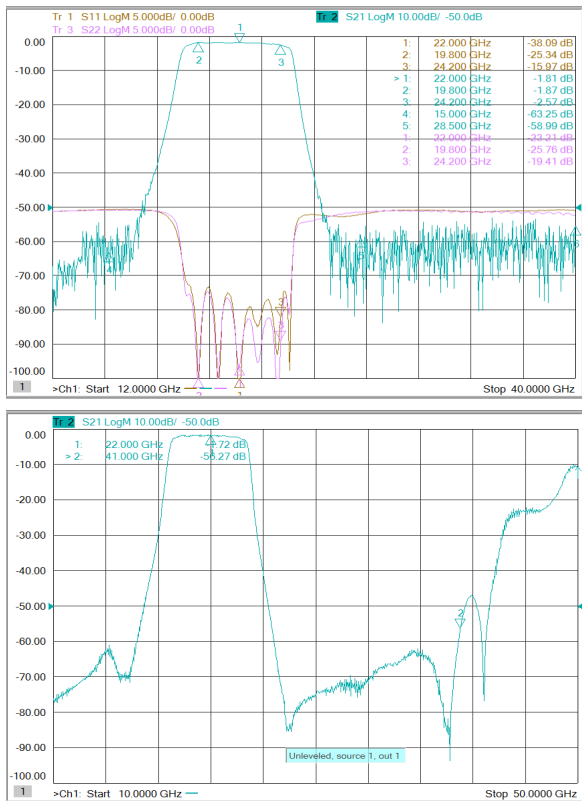
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

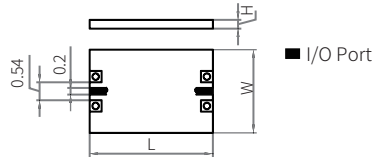
► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	22	-	GHz
Band Freq	19.8	-	24.2	GHz
Fc IL	-	2.0	-	dB
Passband Ripple	-	-	1.2	dB
VSWR	-	1.8	-	-
Rejection	≥50dB@15GHz			
	≥50dB@28.5GHz			

► Typical Curve



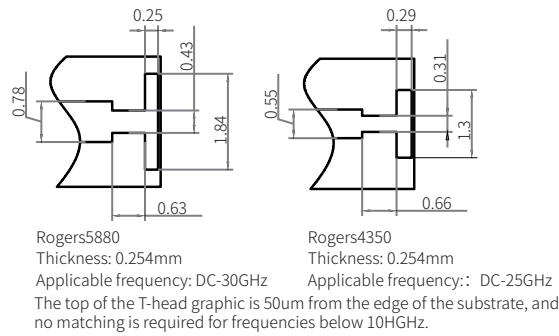
► Overall Dimensions



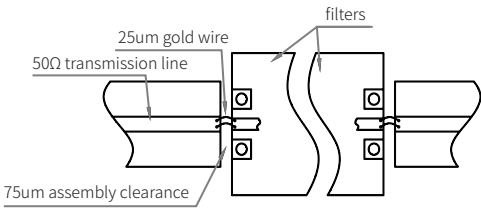
notation	value	unit
L	7.5	mm
W	2.0	mm
H	0.254	mm

► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



► Suggested Assembly Drawings



IYFTB20750-6500-10

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

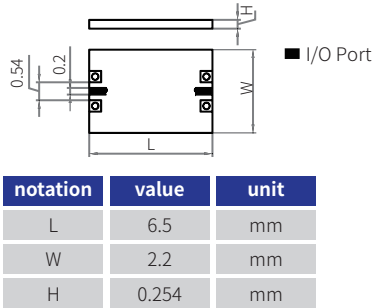
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

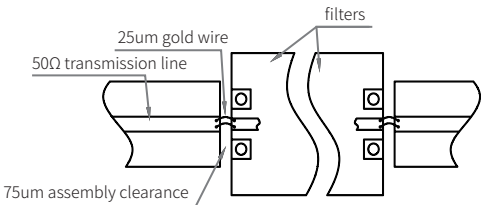
► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	20.75	-	GHz
Band Freq	17.5	-	24	GHz
Fc IL	-	2.0	-	dB
Passband Ripple	-	-	1.5	dB
VSWR	-	1.8	-	-
Rejection	≥40dB@12GHz			
	≥40dB@27GHz			

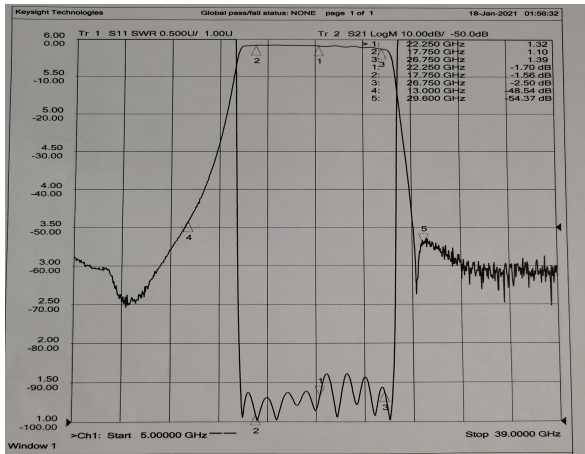
► Overall Dimensions



► Suggested Assembly Drawings

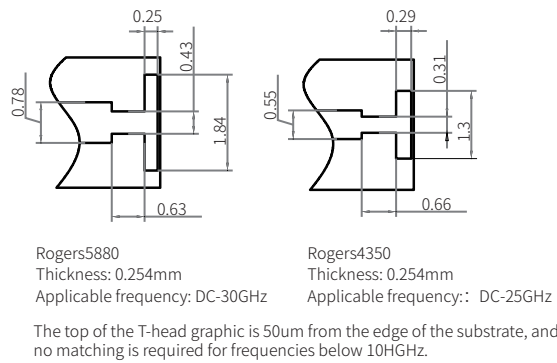


► Typical Curve



► Caveat

- 1、It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2、The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3、The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4、Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB22250-9000-8

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

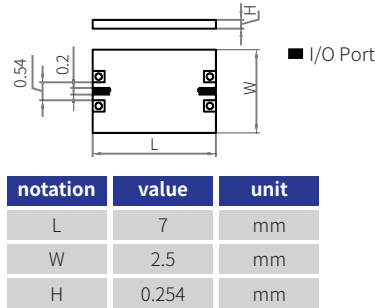
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

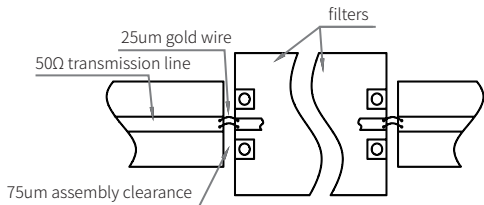
► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	22.25	-	GHz
Band Freq	17.75	-	26.75	GHz
Fc IL	-	2.0	-	dB
Passband Ripple	-	-	1.5	dB
VSWR	-	1.8	-	-
Rejection	≥50dB@13GHz			
	≥27dB@29.6GHz			

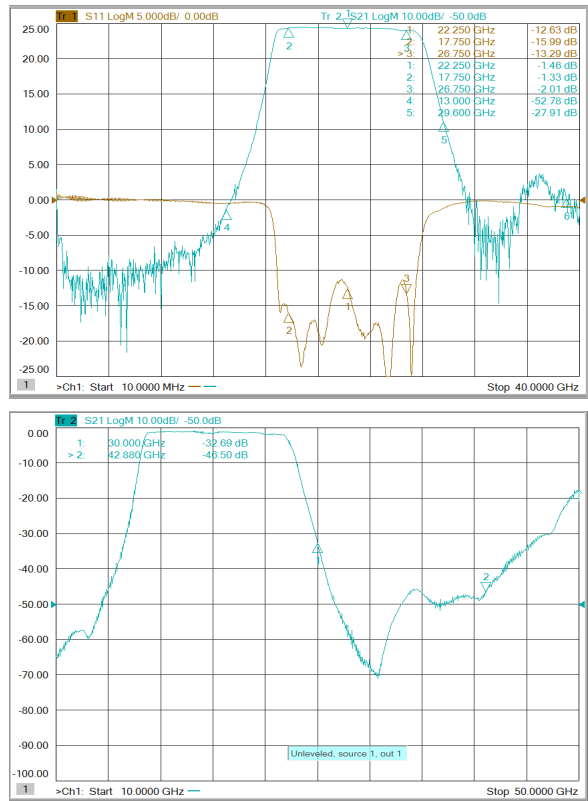
► Overall Dimensions



► Suggested Assembly Drawings

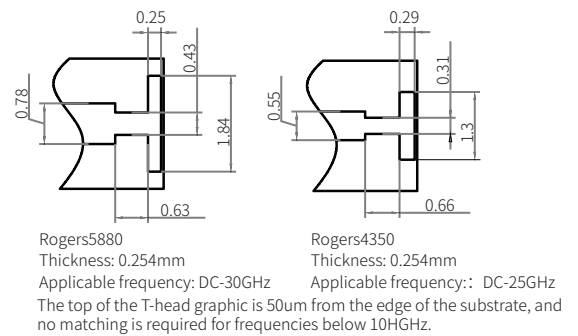


► Typical Curve



► Caveat

- 1、It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2、The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3、The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4、Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB23171.5-20-4

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

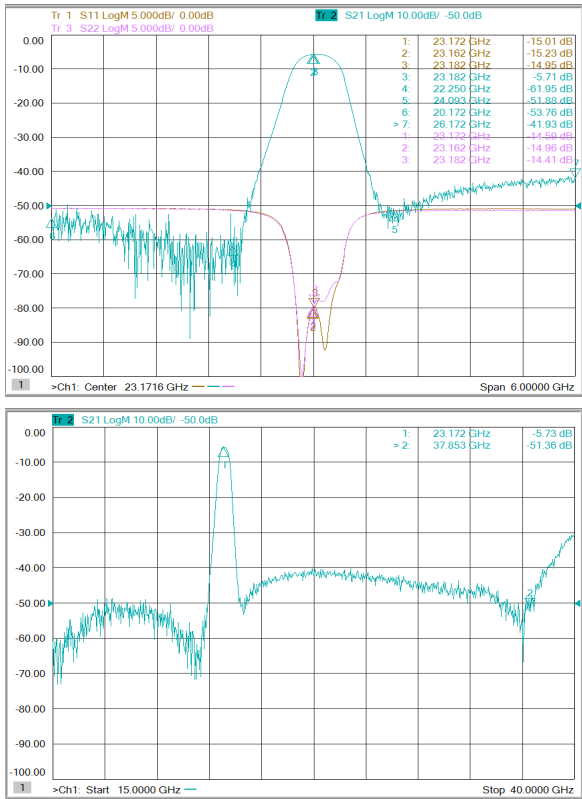
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

► Electrical Specifications

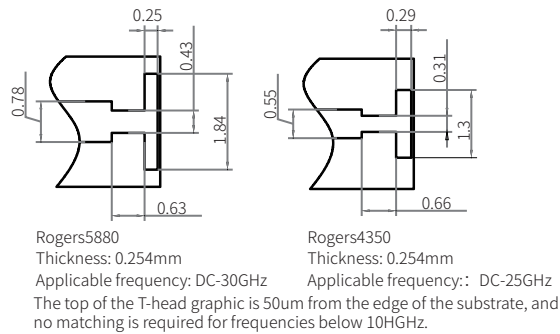
	Min	Typical	Max	
Center Freq	-	23.1715	-	GHz
Band Freq	23.1615	-	23.1815	GHz
Fc IL	-	6	-	dB
Passband Ripple	-	-	0.5	dB
VSWR	-	1.8	-	-
Rejection	≥40dB@22.2499 GHz			
	≥40dB@24.0931 GHz			

► Typical Curve

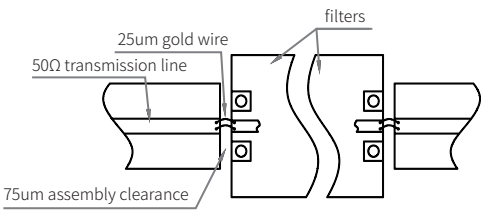


► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



► Suggested Assembly Drawings



IYFTB23200-100-4

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

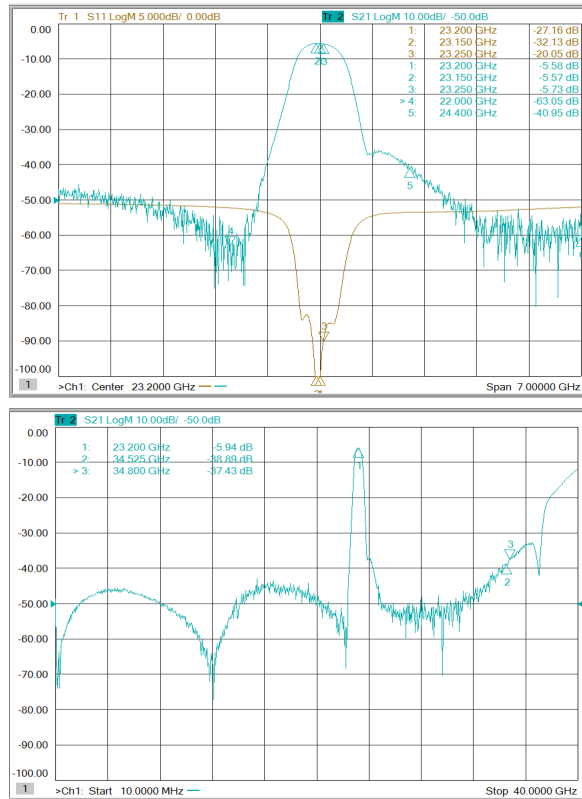
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

► Electrical Specifications

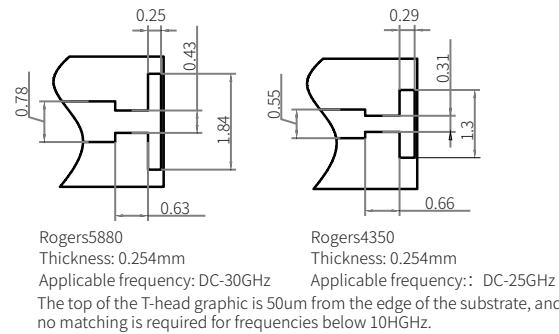
	Min	Typical	Max	
Center Freq	-	23.2	-	GHz
Band Freq	23.15	-	23.25	GHz
Fc IL	-	6.5	-	dB
Passband Ripple	-	-	1.0	dB
VSWR	-	1.8	-	-
Rejection	≥40dB@22GHz			
	≥40dB@24.4GHz			

► Typical Curve

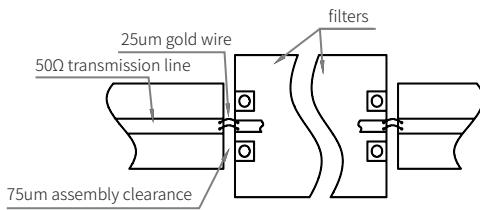


► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



► Suggested Assembly Drawings



IYFTB23671.6-20-4

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

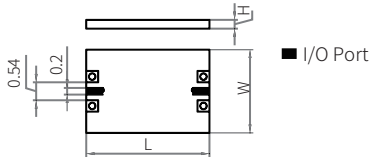
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

► Electrical Specifications

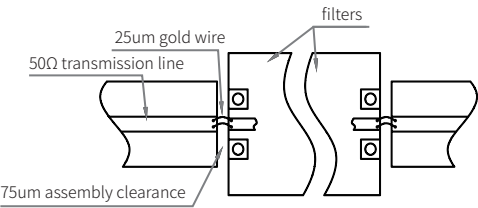
	Min	Typical	Max	
Center Freq	-	23.6716	-	GHz
Band Freq	23.6616	-	23.6816	GHz
Fc IL	-	6.2	-	dB
Passband Ripple	-	-	0.5	dB
VSWR	-	1.8	-	-
Rejection	≥40dB@22.75GHz			
	≥40dB@24.5932 GHz			

► Overall Dimensions

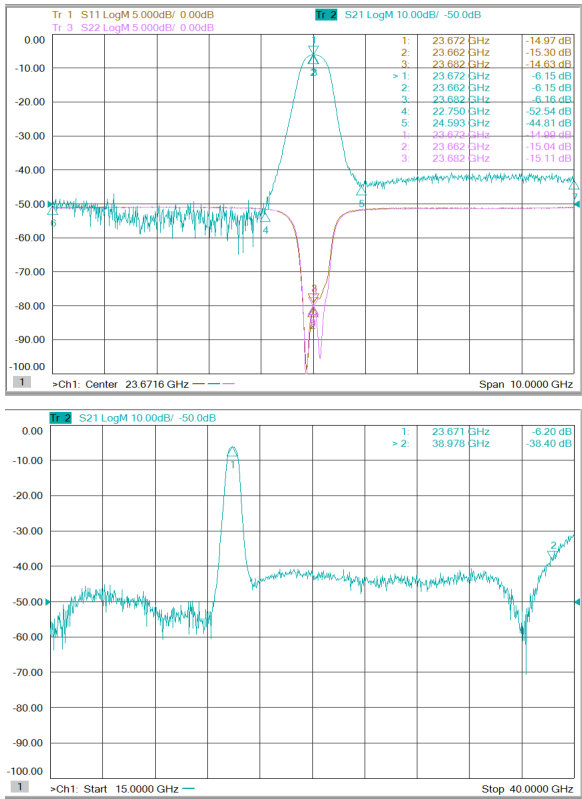


notation	value	unit
L	3.8	mm
W	3	mm
H	0.254	mm

► Suggested Assembly Drawings

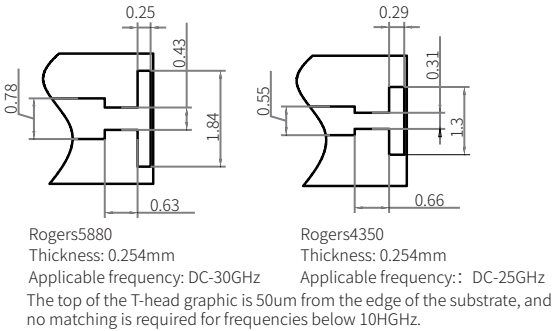


► Typical Curve



► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB24000-1000-5

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

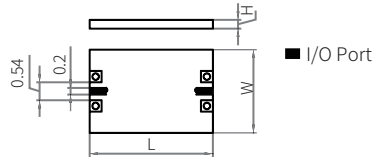
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

► Electrical Specifications

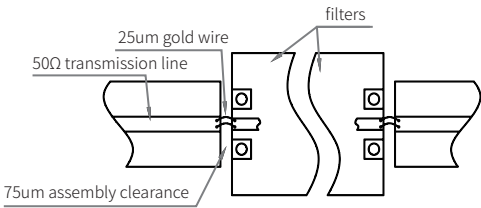
	Min	Typical	Max	
Center Freq	-	24	-	GHz
Band Freq	23.5	-	24.5	GHz
Fc IL	-	3.0	-	dB
Passband Ripple	-	-	1.0	dB
VSWR	-	1.8	-	-
Rejection	≥40dB@22GHz			
	≥40dB@25.5GHz			

► Overall Dimensions

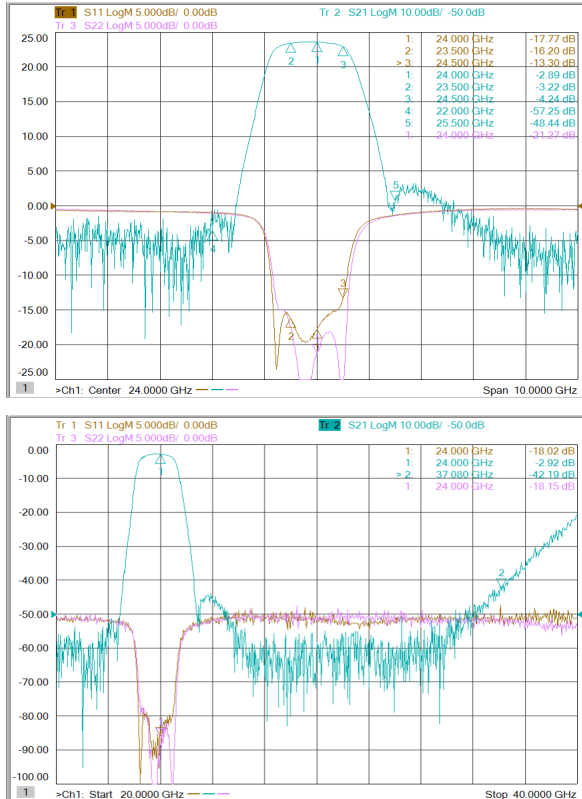


notation	value	unit
L	6.0	mm
W	3.0	mm
H	0.254	mm

► Suggested Assembly Drawings

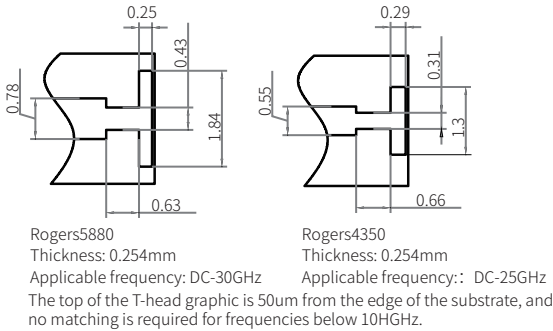


► Typical Curve



► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB25000-2900-8

- Performance Characteristics
- 1、High precision micro-nanometer processing technology
 - 2、High performance, low temperature drift, high power
 - 3、Gold wire bonding, suitable for multi-chip integration module applications
 - 4、50Ω coplanar waveguide output

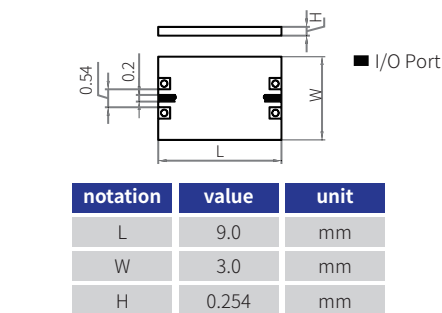
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

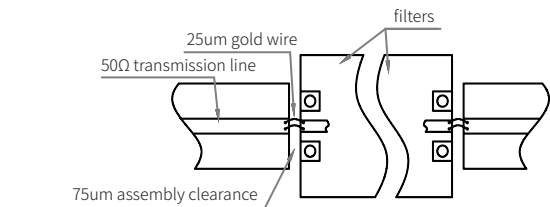
► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	25	-	GHz
Band Freq	23.5	-	26.4	GHz
Fc IL	-	2.8	-	dB
Passband Ripple	-	-	1	dB
VSWR	-	1.8	-	-
Rejection	≥40dB@21.6GHz			
	≥40dB@28.5GHz			

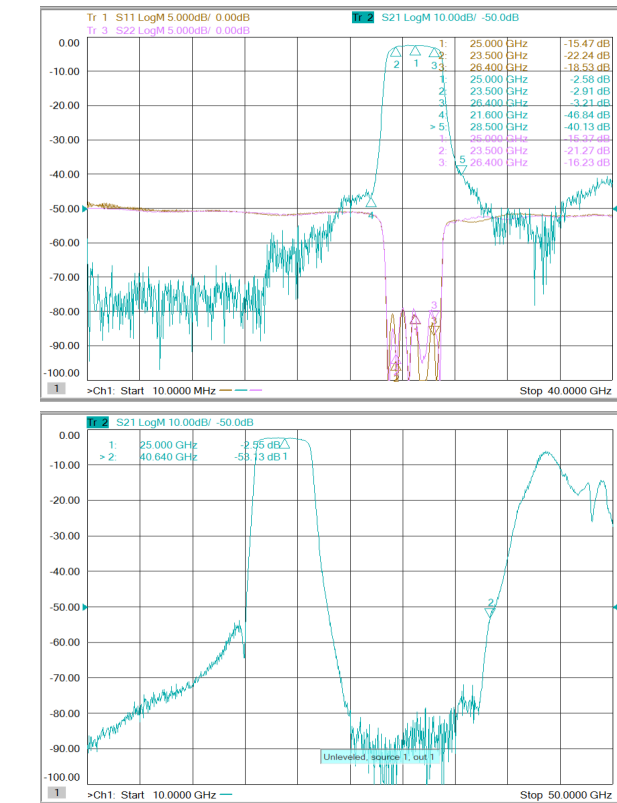
► Overall Dimensions



► Suggested Assembly Drawings

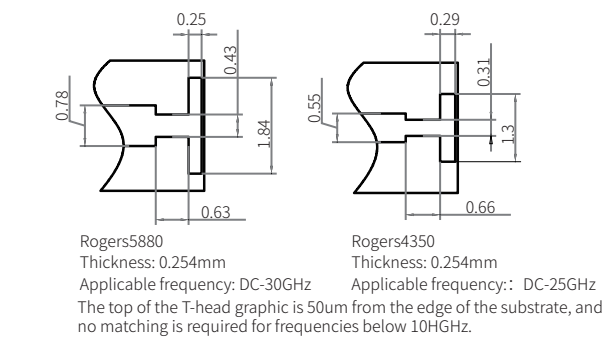


► Typical Curve



► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB26000-4400-8

- Performance Characteristics
- 1、High precision micro-nanometer processing technology
 - 2、High performance, low temperature drift, high power
 - 3、Gold wire bonding, suitable for multi-chip integration module applications
 - 4、50Ω coplanar waveguide output

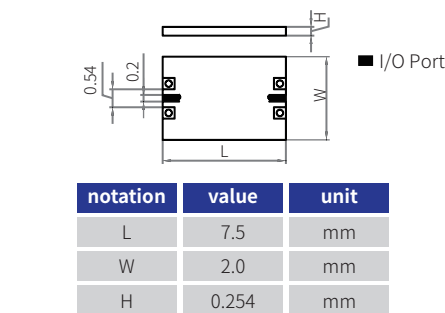
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

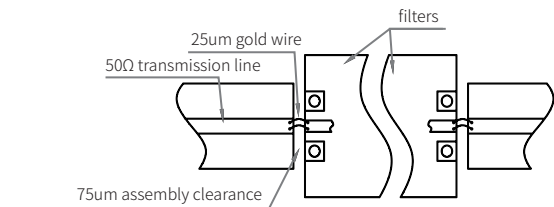
► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	26	-	GHz
Band Freq	23.8	-	28.2	GHz
Fc IL	-	2.0	-	dB
Passband Ripple	-	-	1.0	dB
VSWR	-	1.8	-	-
Rejection	≥60dB@18GHz			
	≥60dB@32.5GHz			

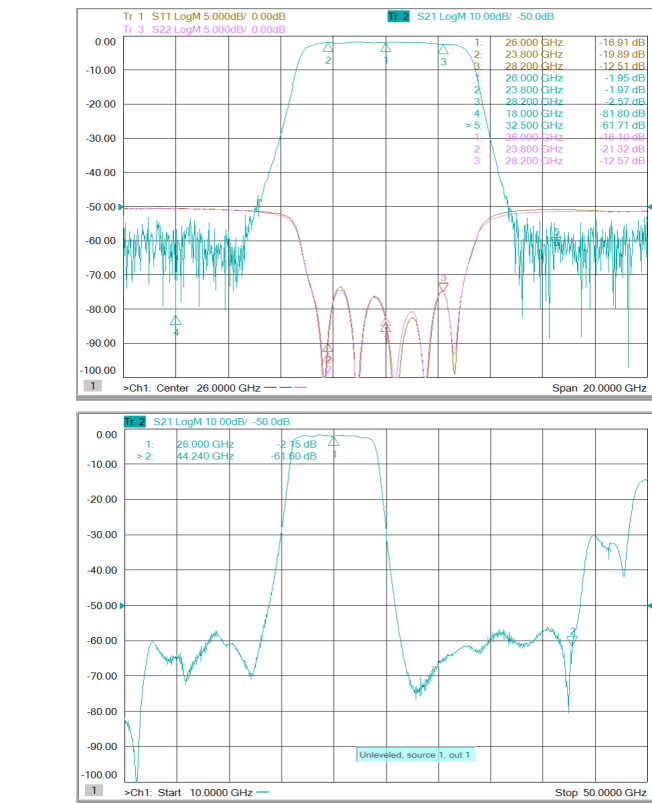
► Overall Dimensions



► Suggested Assembly Drawings

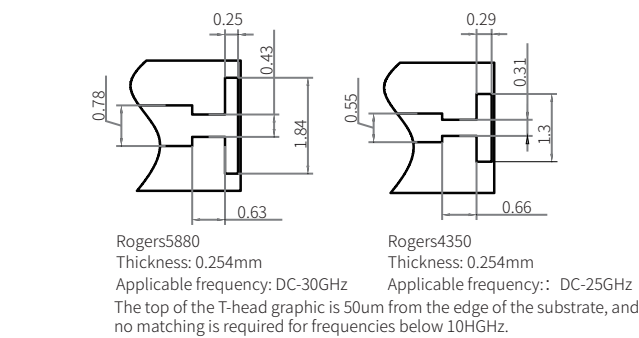


► Typical Curve



► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB28050-8700-9

- Performance Characteristics
- 1、High precision micro-nanometer processing technology

2、High performance, low temperature drift, high power

3、Gold wire bonding, suitable for multi-chip integration module applications

4、50Ω coplanar waveguide output

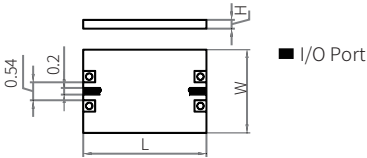
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

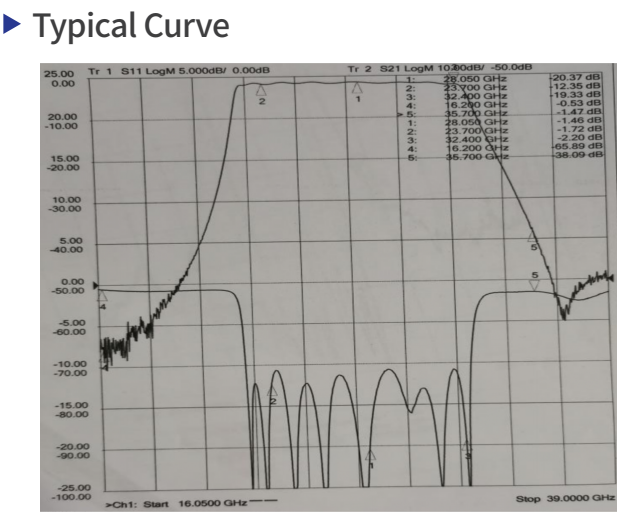
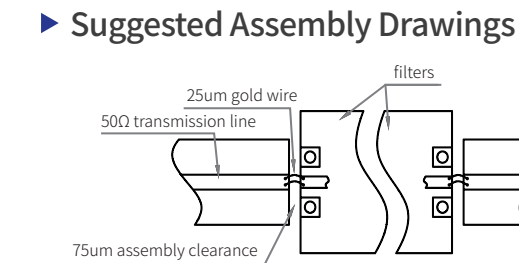
► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	28.05	-	GHz
Band Freq	23.7	-	32.4	GHz
Fc IL	-	2.0	-	dB
Passband Ripple	-	-	1.5	dB
VSWR	-	1.8	-	-
Rejection	≥50dB@DC~16.2GHz			
	≥35dB@35.7~45GHz			

► Overall Dimensions



notation	value	unit
L	9.0	mm
W	2.8	mm
H	0.254	mm

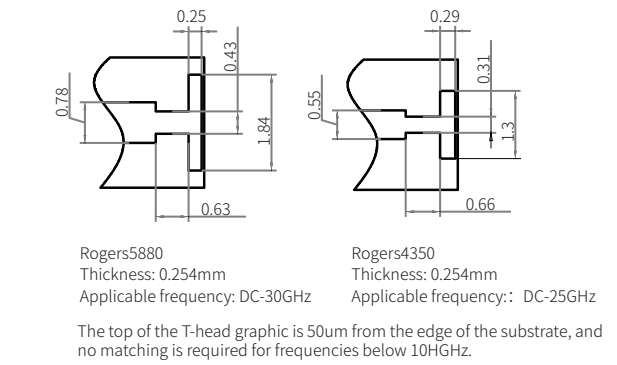


- Caveat
- 1、It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;

2、The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);

3、The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;

4、Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB28500-8500-10

- Performance Characteristics
- 1、High precision micro-nanometer processing technology

2、High performance, low temperature drift, high power

3、Gold wire bonding, suitable for multi-chip integration module applications

4、50Ω coplanar waveguide output

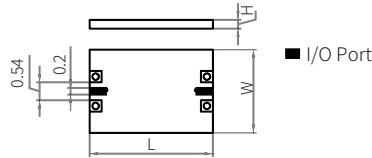
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

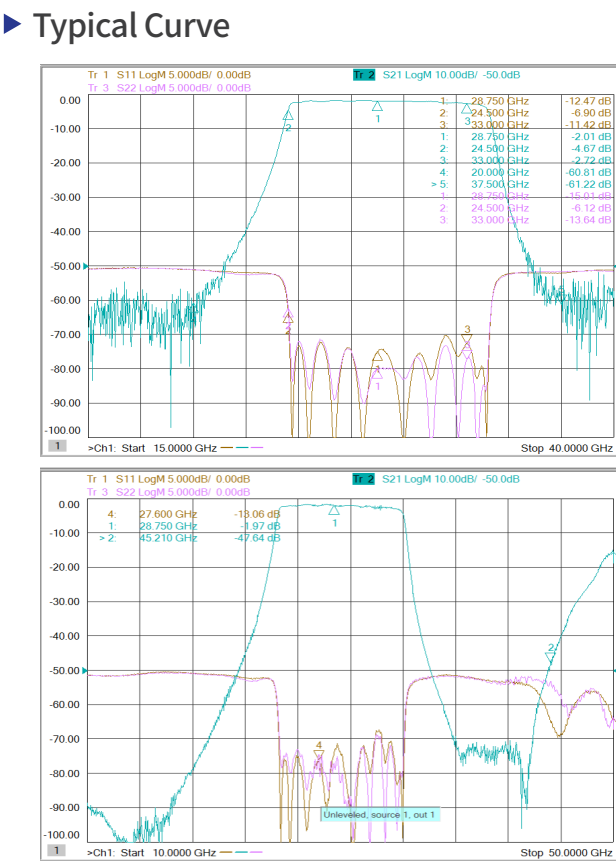
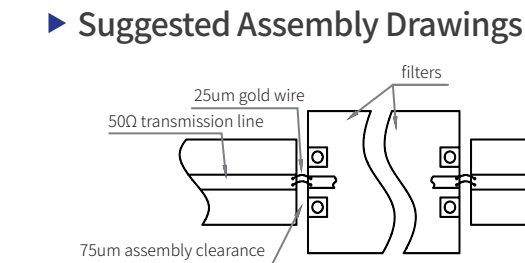
► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	28.5	-	GHz
Band Freq	24.25	-	32.75	GHz
Fc IL	-	2.5	-	dB
Passband Ripple	-	-	1.5	dB
VSWR	-	1.8	-	-
Rejection	≥55dB@20GHz			
	≥50dB@37.5GHz			

► Overall Dimensions



notation	value	unit
L	7.0	mm
W	2.0	mm
H	0.254	mm

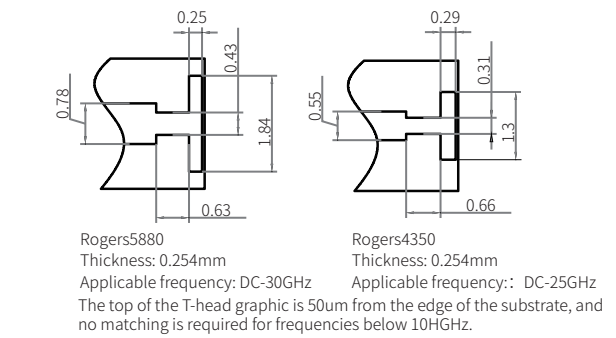


- Caveat
- 1、It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;

2、The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);

3、The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;

4、Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB29000-2000-8

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

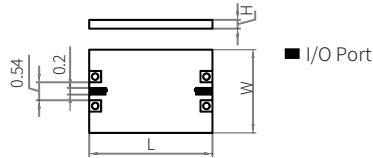
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

► Electrical Specifications

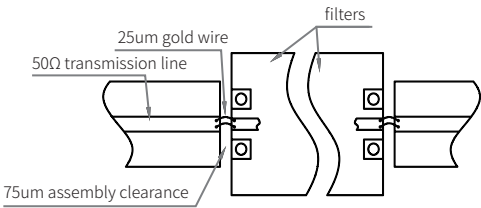
	Min	Typical	Max	
Center Freq	-	29	-	GHz
Band Freq	28	-	30	GHz
Fc IL	-	2.5	-	dB
Passband Ripple	-	-	1.0	dB
VSWR	-	1.8	-	-
Rejection	≥50dB@23GHz			
	≥50dB@35GHz			

► Overall Dimensions

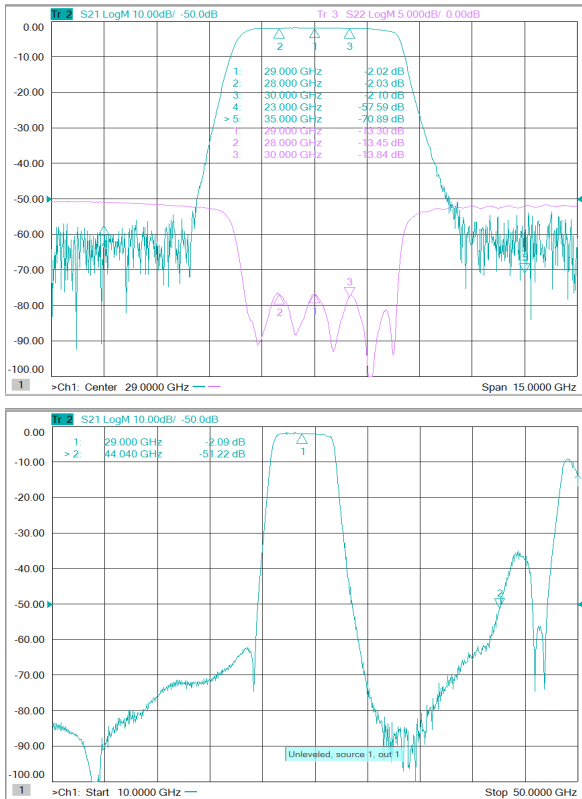


notation	value	unit
L	9.0	mm
W	2.4	mm
H	0.254	mm

► Suggested Assembly Drawings

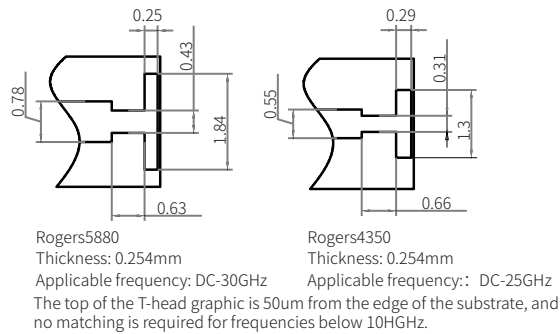


► Typical Curve



► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB29000-6500-8

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

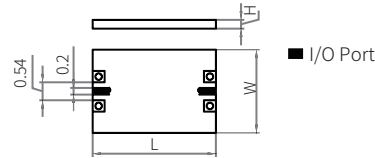
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

► Electrical Specifications

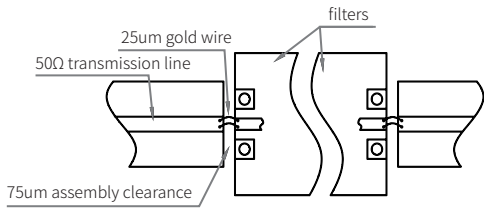
	Min	Typical	Max	
Center Freq	-	29	-	GHz
Band Freq	25.75	-	32.25	GHz
Fc IL	-	2	-	dB
Passband Ripple	-	-	1.0	dB
VSWR	-	1.8	-	-
Rejection	≥50dB@20GHz			
	≥45dB@38GHz			

► Overall Dimensions

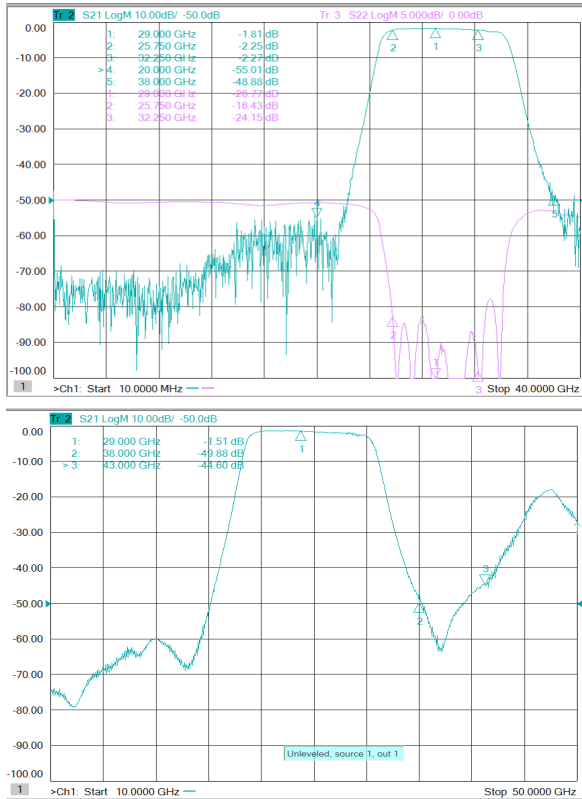


notation	value	unit
L	8.0	mm
W	2.4	mm
H	0.254	mm

► Suggested Assembly Drawings

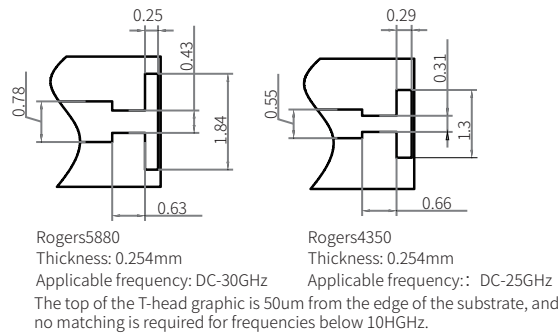


► Typical Curve



► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB29500-7200-8

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

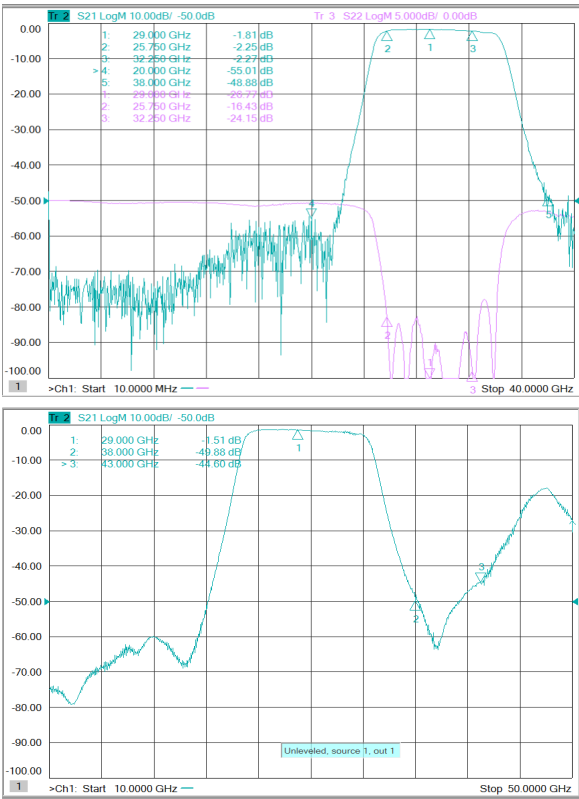
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

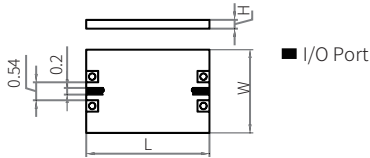
► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	29.5	-	GHz
Band Freq	25.9	-	33.1	GHz
Fc IL	-	2.0	-	dB
Passband Ripple	-	-	1.0	dB
VSWR	-	1.8	-	-
Rejection	≥50dB@19.5GHz			
	≥40dB@37.5GHz			

► Typical Curve

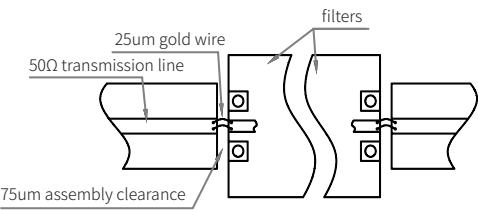


► Overall Dimensions



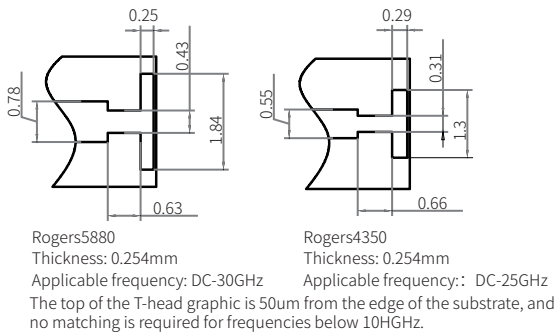
notation	value	unit
L	7.0	mm
W	2.0	mm
H	0.254	mm

► Suggested Assembly Drawings



► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB33000-1000-6

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

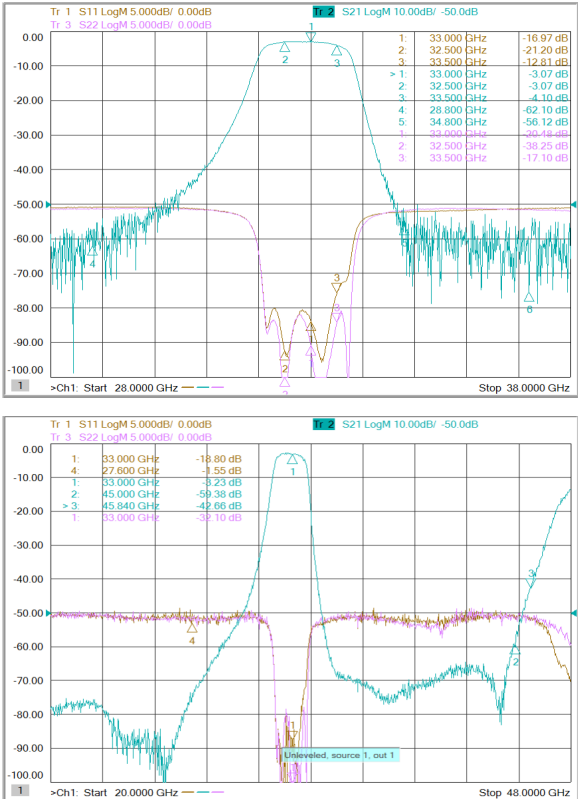
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

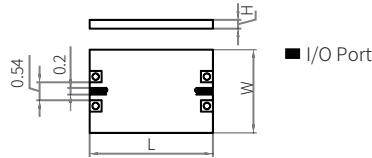
► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	33	-	GHz
Band Freq	32.5	-	33.5	GHz
Fc IL	-	3.5	-	dB
Passband Ripple	-	-	1.2	dB
VSWR	-	1.8	-	-
Rejection	≥50dB@28.8GHz			
	≥40dB@37.5GHz			

► Typical Curve

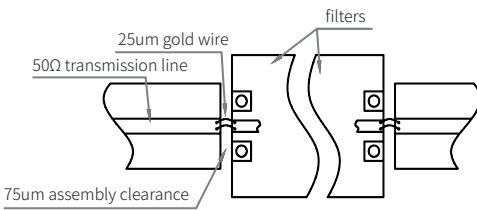


► Overall Dimensions



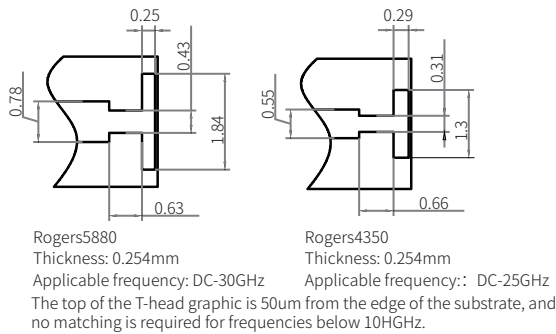
notation	value	unit
L	7.0	mm
W	2.0	mm
H	0.254	mm

► Suggested Assembly Drawings



► Caveat

- 1. It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2. The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3. The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4. Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB34000-4000-6

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

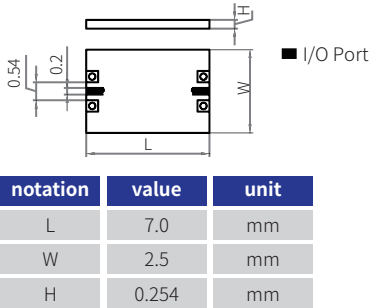
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

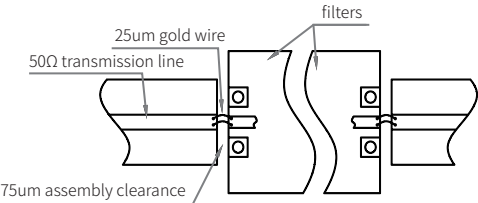
► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	34	-	GHz
Band Freq	32	-	36	GHz
Fc IL	-	2.0	-	dB
Passband Ripple	-	-	1.0	dB
VSWR	-	1.8	-	-
Rejection	≥40dB@28 GHz			
	≥40dB@40 GHz			

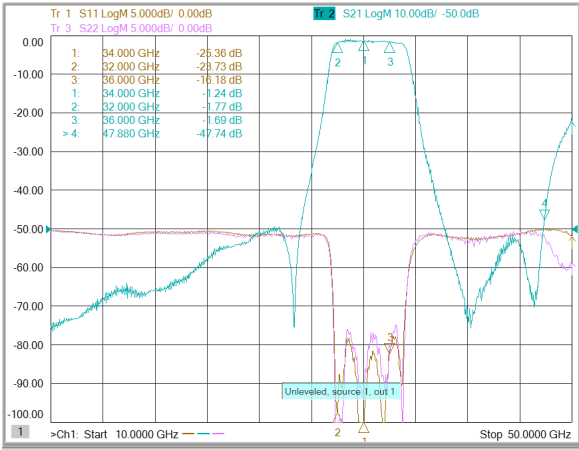
► Overall Dimensions



► Suggested Assembly Drawings

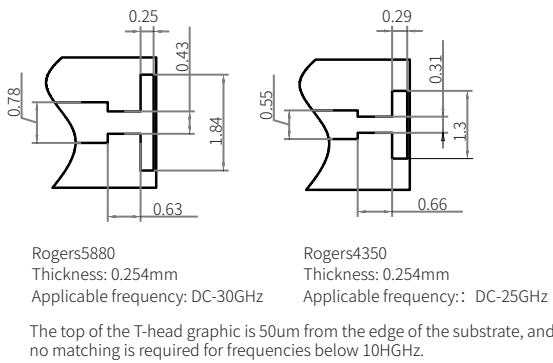


► Typical Curve



► Caveat

- 1、It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2、The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3、The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4、Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB34150-700-6

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

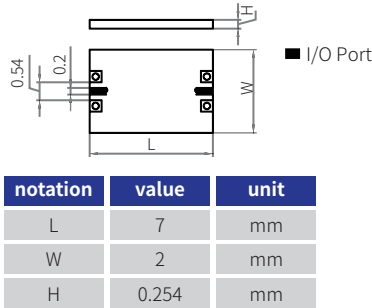
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

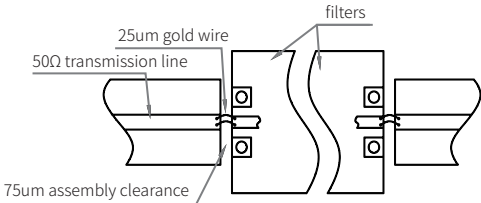
► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	34.15	-	GHz
Band Freq	33.8	-	34.5	GHz
Fc IL	-	2.5	-	dB
Passband Ripple	-	-	1.2	dB
VSWR	-	1.8	-	-
Rejection	≥50dB@28 GHz			
	≥50dB@40 GHz			

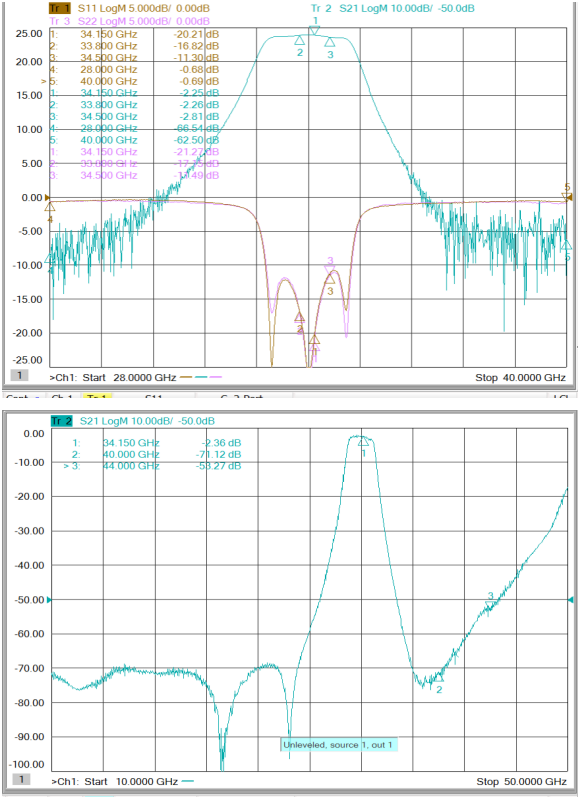
► Overall Dimensions



► Suggested Assembly Drawings

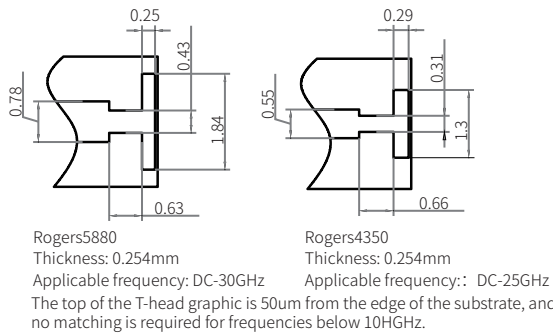


► Typical Curve



► Caveat

- 1、It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2、The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3、The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4、Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB34500-3000-8

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

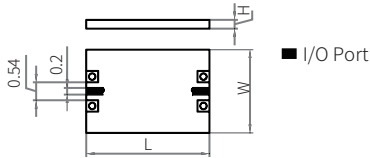
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

► Electrical Specifications

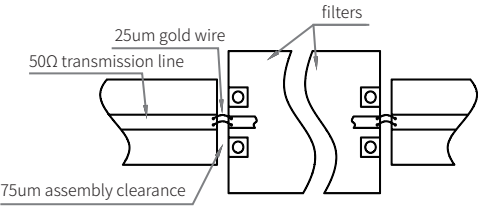
	Min	Typical	Max	
Center Freq	-	34.5	-	GHz
Band Freq	33	-	36	GHz
Fc IL	-	2.5	-	dB
Passband Ripple	-	-	-	dB
VSWR	-	1.8	-	-
Rejection	≥50dB@30 GHz			
	≥50dB@38 GHz			

► Overall Dimensions

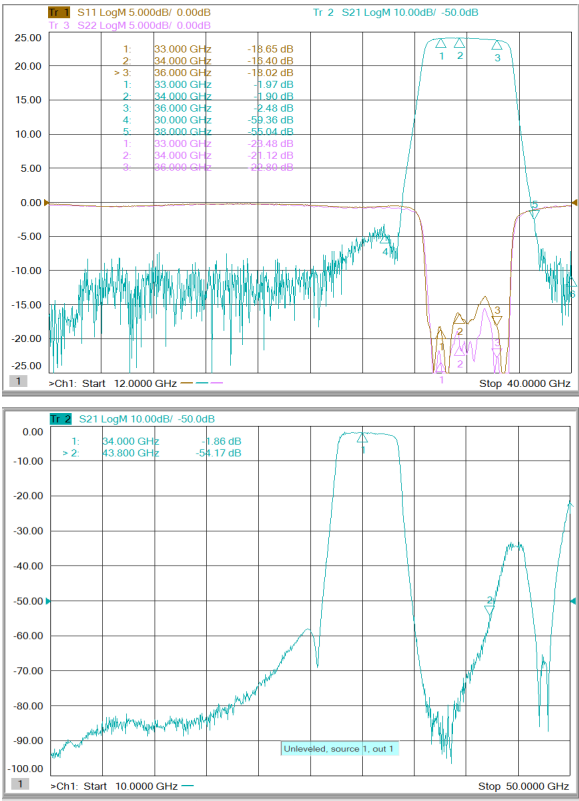


notation	value	unit
L	8.5	mm
W	2.4	mm
H	0.254	mm

► Suggested Assembly Drawings

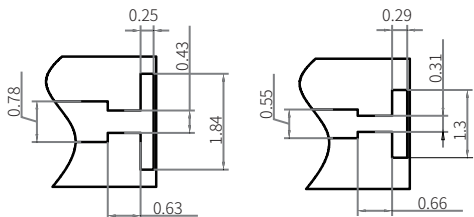


► Typical Curve



► Caveat

- 1、It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2、The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3、The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4、Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



Rogers5880
Thickness: 0.254mm
Applicable frequency: DC-30GHz
The top of the T-head graphic is 50um from the edge of the substrate, and no matching is required for frequencies below 10HGHZ.

Rogers4350
Thickness: 0.254mm
Applicable frequency: DC-25GHz
The top of the T-head graphic is 50um from the edge of the substrate, and no matching is required for frequencies below 10HGHZ.

IYFTB34500-3400-6

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

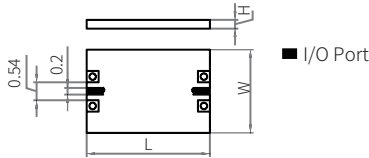
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

► Electrical Specifications

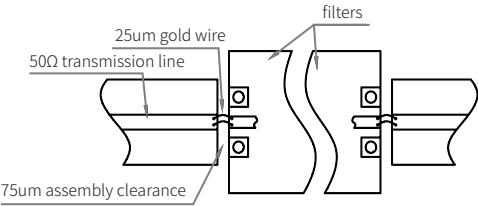
	Min	Typical	Max	
Center Freq	-	34.5	-	GHz
Band Freq	32.8	-	36.2	GHz
Fc IL	-	2	-	dB
Passband Ripple	-	-	1.0	dB
VSWR	-	1.8	-	-
Rejection	≥40dB@29.6 GHz			
	≥35dB@39.1 GHz			

► Overall Dimensions

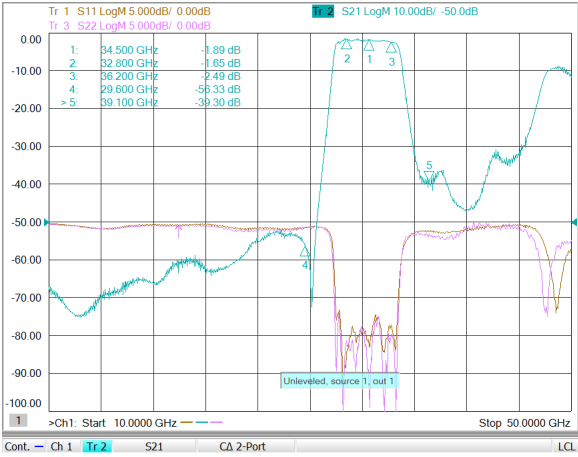


notation	value	unit
L	8	mm
W	3	mm
H	0.254	mm

► Suggested Assembly Drawings

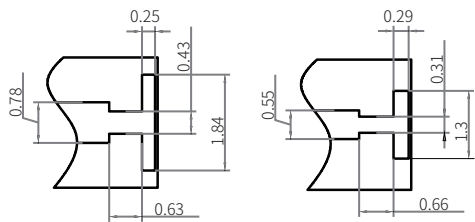


► Typical Curve



► Caveat

- 1、It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2、The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3、The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4、Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



Rogers5880
Thickness: 0.254mm
Applicable frequency: DC-30GHz

Rogers4350
Thickness: 0.254mm
Applicable frequency: DC-25GHz

The top of the T-head graphic is 50um from the edge of the substrate, and no matching is required for frequencies below 10HGHZ.

IYFTB36000-8000-8

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

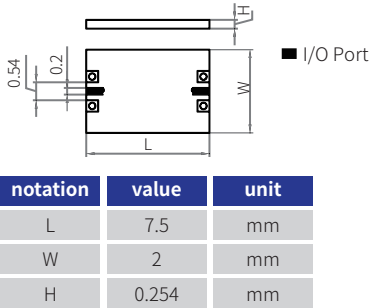
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

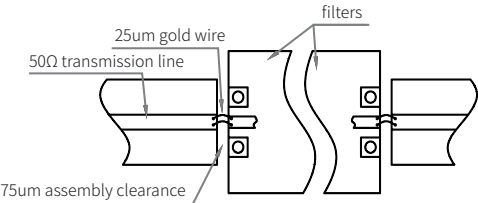
► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	36	-	GHz
Band Freq	32	-	40	GHz
Fc IL	-	2.5	-	dB
Passband Ripple	-	-	1.5	dB
VSWR	-	1.8	-	-
Rejection	≥45dB@21 GHz			
	≥30dB@42 GHz			

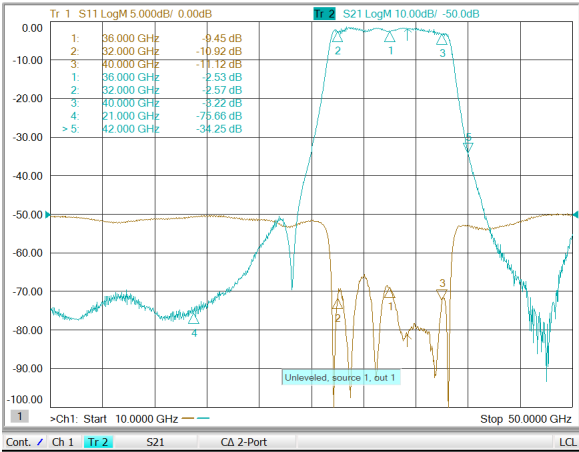
► Overall Dimensions



► Suggested Assembly Drawings

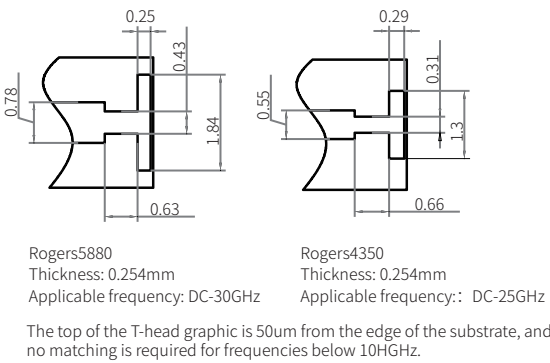


► Typical Curve



► Caveat

- 1、It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2、The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3、The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4、Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:



IYFTB40500-600-5

► Performance Characteristics

- 1、High precision micro-nanometer processing technology
- 2、High performance, low temperature drift, high power
- 3、Gold wire bonding, suitable for multi-chip integration module applications
- 4、50Ω coplanar waveguide output

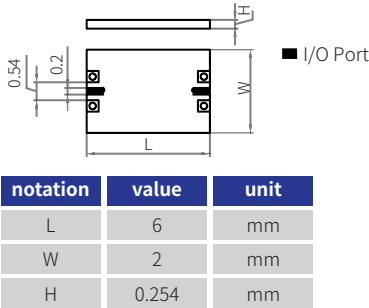
► Environmental Parameters

Working Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Maximum Input Power	35dBm

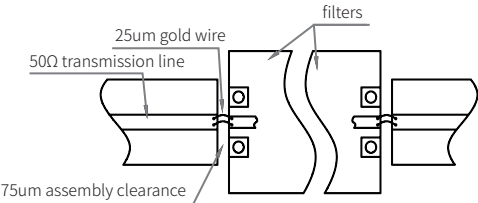
► Electrical Specifications

	Min	Typical	Max	
Center Freq	-	40.5	-	GHz
Band Freq	40.2	-	40.8	GHz
Fc IL	-	3	-	dB
Passband Ripple	-	-	1.2	dB
VSWR	-	1.8	-	-
Rejection	≥50dB@31 GHz			
	≥15dB@51 GHz			

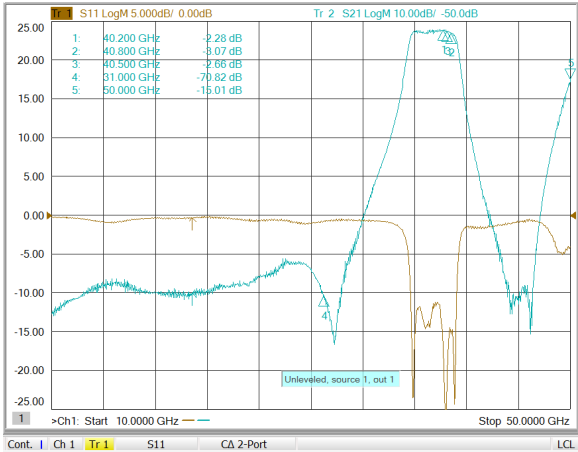
► Overall Dimensions



► Suggested Assembly Drawings



► Typical Curve



► Caveat

- 1、It is recommended that the filter be used in separate chambers, with both sides of the filter on the upper line about 0.2mm from the wall. The upper surface of the filter is about 3mm away from the upper cover plate;
- 2、The filter is recommended to be bonded with low-stress conductive adhesive (such as ME8456);
- 3、The filter should be mounted on a carrier with a comparable coefficient of thermal expansion (6.7ppm / °C) of the substrate such as Kovar (recommended) or molybdenum-copper, and the thickness of the carrier ≥ 0.2mm;
- 4、Circuit microstrip line and filter chip bonding connection, it is recommended that the microstrip line bonding to match the T-shaped structure, T-head size is as follows:

